

RL78/G1F

RENESAS MCU

R01DS0246EJ0110 Rev. 1.10

Aug 12, 2016

True Low Power Platform (as low as 66 μ A/MHz, and 0.57 μ A for RTC + LVD), 1.6 V to 5.5 V operation, 32/64 Kbyte Flash, Max.32 MHz CPU operation, Enhanced analog functions, for General Purpose Applications

1. OUTLINE

1.1 Features

Ultra-low power consumption technology

- V_{DD} = single power supply voltage of 1.6 to 5.5 V which can operate a 1.8 V device at a low voltage
- HALT mode
- STOP mode
- SNOOZE mode

RL78 CPU core

- · CISC architecture with 3-stage pipeline
- Minimum instruction execution time: Can be changed from high speed (0.03125 μs: @ 32 MHz operation with high-speed on-chip oscillator) to ultra-low speed (30.5 μs: @ 32.768 kHz operation with subsystem clock)
- Multiply/divide/multiply & accumulate instructions are supported.
- · Address space: 1 MB
- General-purpose registers: (8-bit register × 8) × 4 banks
- On-chip RAM: 5.5 KB

Code flash memory

- · Code flash memory: 32/64 KB
- · Block size: 1 KB
- Prohibition of block erase and rewriting (security function)
- · On-chip debug function
- Self-programming (with boot swap function/flash shield window function)

Data flash memory

- Data flash memory: 4 KB
- Back ground operation (BGO): Instructions can be executed from the program memory while rewriting the data flash memory.
- Number of rewrites: 1,000,000 times (TYP.)
- Voltage of rewrites: V_{DD} = 1.8 to 5.5 V

High-speed on-chip oscillator

- Select from 64 MHz, 48 MHz, 32 MHz, 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz, and 1 MHz
- High accuracy: $\pm 1.0\%$ (V_{DD} = 1.8 to 5.5 V, T_A = -20 to +85°C)

Operating ambient temperature

- $T_A = -40$ to +85°C (A: Consumer applications)
- $T_A = -40 \text{ to } +105^{\circ}\text{C}$ (G: Industrial applications)

Power management and reset function

- On-chip power-on-reset (POR) circuit
- On-chip voltage detector (LVD) (Select interrupt and reset from 14 levels)

Data transfer controller (DTC)

- Transfer modes: Normal transfer mode, repeat transfer mode, block transfer mode
- Activation sources: Activated by interrupt sources.
- Chain transfer function

Event link controller (ELC)

 Event signals of 22 types can be linked to the specified peripheral function.

Serial interfaces

- CSI: 3 to 6 channels
- UART/UART (LIN-bus supported): 3 channels
- I2C/simplified I2C: 3 to 6 channels
- · IrDA: 1 channel

Timer

- 16-bit timer: 9 channels (Timer Array Unit (TAU): 4 channels, Timer RJ: 1 channel, Timer RD: 2 channels (with PWMOPA), Timer RG: 1 channel, Timer RX: 1 channel)
- · 12-bit interval timer: 1 channel
- Real-time clock: 1 channel (calendar for 99 years, alarm function, and clock correction function)
- Watchdog timer: 1 channel (operable with the dedicated low-speed on-chip oscillator)

A/D converter

- 8/10-bit resolution A/D converter (V_{DD} = 1.6 to 5.5 V)
- · Analog input: 8 to 17 channels
- Internal reference voltage (1.45 V) and temperature sensor

D/A converter

- 8-bit resolution D/A converter (VDD = 1.6 to 5.5 V)
- · Analog output: 1 or 2 channels
- Output voltage: 0 V to VDD
- · Real-time output function

Comparator

- 2 channels (pin selector is provided for 1 channel)
- Incorporates a function for the output of a timer window in combination with the timer array unit.
- The external reference voltage or internal reference voltage can be selected as the reference voltage.

Programmable gain amplifier (PGA)

• 1 channel

I/O port

- I/O port: 20 to 58 (N-ch open drain I/O [withstand voltage of 6 V]: 2 to 4, N-ch open drain I/O [VDD withstand voltage/EVDD withstand voltage]: 10 to 16)
- Can be set to N-ch open drain, TTL input buffer, and onchip pull-up resistor
- Different potential interface: Can connect to a 1.8/2.5/3
 V device
- · On-chip key interrupt function
- · On-chip clock output/buzzer output controller

Others

On-chip BCD (binary-coded decimal) correction circuit

Remark The functions mounted depend on the product. See 1.6 Outline of Functions.

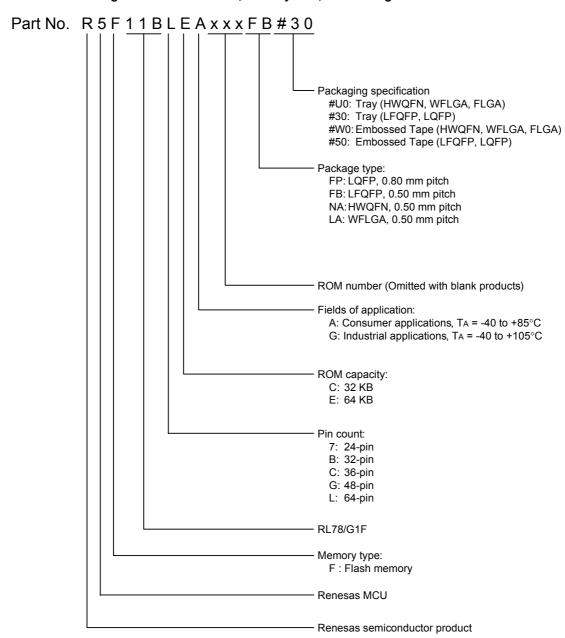
O ROM, RAM capacities

Flash ROM	Data flash	RAM			RL78/G1F		
T IdSIT IXOIVI	Data ilasii	IVAIVI	24 pins	32 pins	36 pins	48 pins	64 pins
64 KB	4 KB	5.5 KB Note	R5F11B7E	R5F11BBE	R5F11BCE	R5F11BGE	R5F11BLE
32 KB	4 KB	5.5 KB Note	R5F11B7C	R5F11BBC	R5F11BCC	R5F11BGC	R5F11BLC

Note This is about 4.5 KB when performing self-programming and rewriting the data flash memory (For details, see CHAPTER 3 CPU ARCHITECTURE in the RL78/G1F User's Manual).

1.2 Ordering Information

Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G1F



Pin count	Package	Fields of Application ^{Note}	Ordering Part Number
24 pins	24-pin plastic HWQFN	А	R5F11B7CANA#U0, R5F11B7EANA#U0, R5F11B7CANA#W0, R5F11B7EANA#W0
	(4 × 4, 0.5 mm pitch)	G	R5F11B7CGNA#U0, R5F11B7EGNA#U0, R5F11B7CGNA#W0, R5F11B7EGNA#W0
32 pins	32-pin plastic LQFP	А	R5F11BBCAFP#30, R5F11BBEAFP#30, R5F11BBCAFP#50, R5F11BBEAFP#50
	(7 × 7, 0.8 mm pitch)	G	R5F11BBCGFP#30, R5F11BBEGFP#30, R5F11BBCGFP#50, R5F11BBEGFP#50
36 pins	36-pin plastic WFLGA	А	R5F11BCCALA#U0, R5F11BCEALA#U0, R5F11BCCALA#W0, R5F11BCEALA#W0
	(4 × 4 mm, 0.5 mm pitch)	G	R5F11BCCGLA#U0, R5F11BCEGLA#U0, R5F11BCCGLA#W0, R5F11BCEGLA#W0
48 pins	48-pin plastic LFQFP	А	R5F11BGCAFB#30, R5F11BGEAFB#30, R5F11BGCAFB#50, R5F11BGEAFB#50
	(7 × 7 mm, 0.5 mm pitch)	G	R5F11BGCGFB#30, R5F11BGEGFB#30, R5F11BGCGFB#50, R5F11BGEGFB#50
64 pins	64-pin plastic LFQFP	А	R5F11BLCAFB#30, R5F11BLEAFB#30, R5F11BLCAFB#50, R5F11BLEAFB#50
	(10 × 10 mm, 0.5 mm pitch)	G	R5F11BLCGFB#30, R5F11BLEGFB#30, R5F11BLCGFB#50, R5F11BLEGFB#50

Note For the fields of application, refer to Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G1F.

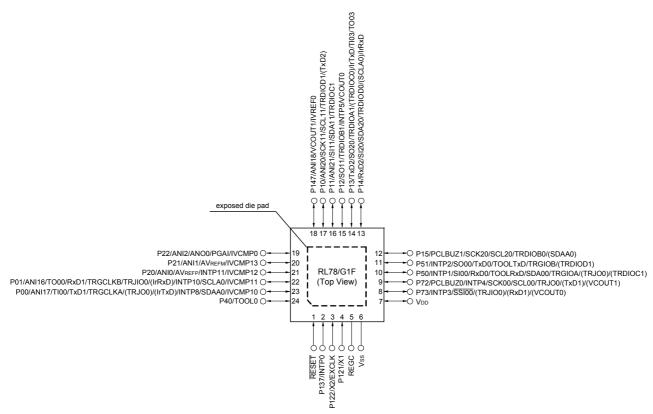
Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3 Pin Configuration (Top View)

1.3.1 24-pin products

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• 24-pin plastic HWQFN (4 × 4 mm, 0.5 mm pitch)



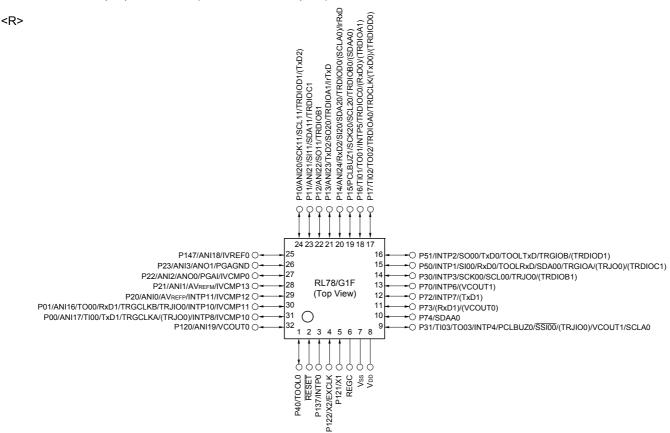
Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection registers 0 to 3 (PIOR0 to PIOR3).

1.3.2 **32-pin products**

• 32-pin plastic LQFP (7 × 7 mm, 0.8 mm pitch)



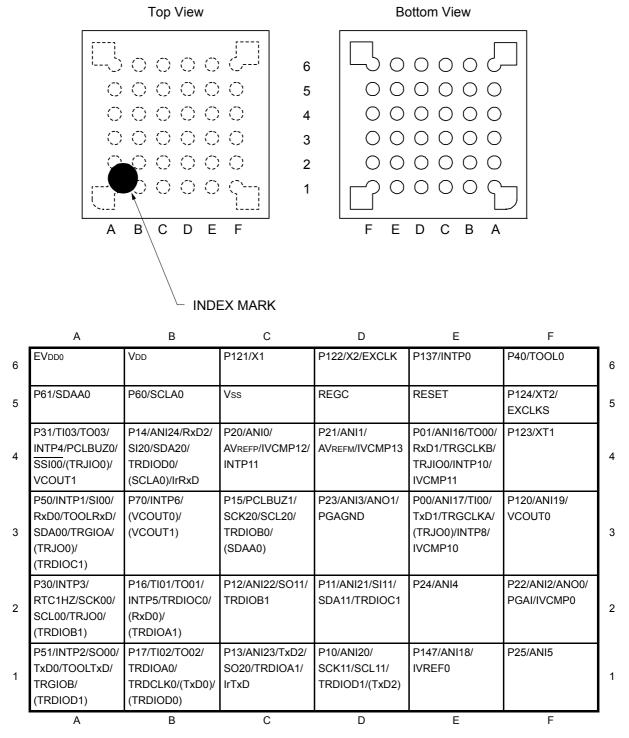
Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection registers 0 to 3 (PIOR0 to PIOR3).

1.3.3 36-pin products

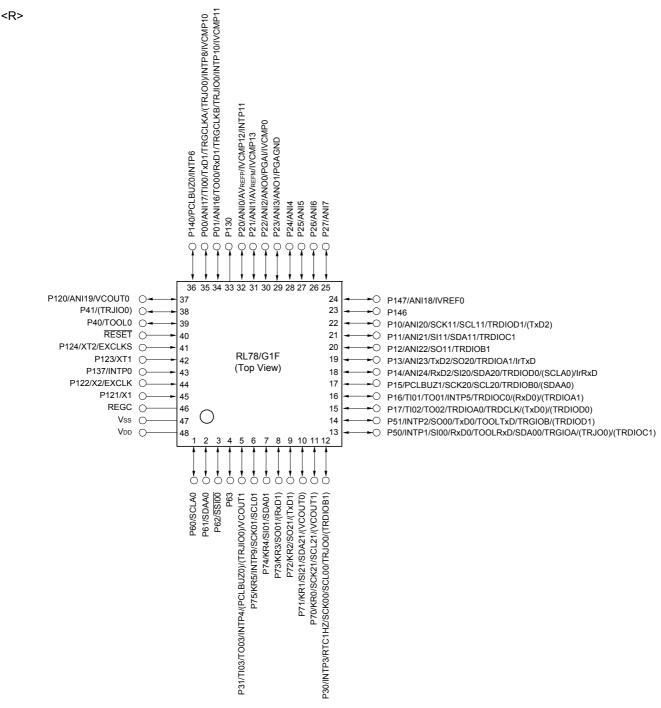
• 36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)



- Caution 1. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).
- Caution 2. Make VDD pin the potential that is higher than EVDD0 pin.
- Remark 1. For pin identification, see 1.4 Pin Identification.
- **Remark 2.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection registers 0 to 3 (PIOR0 to PIOR3).
- **Remark 3.** When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD and EVDDD pins.

1.3.4 48-pin products

• 48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch)



Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

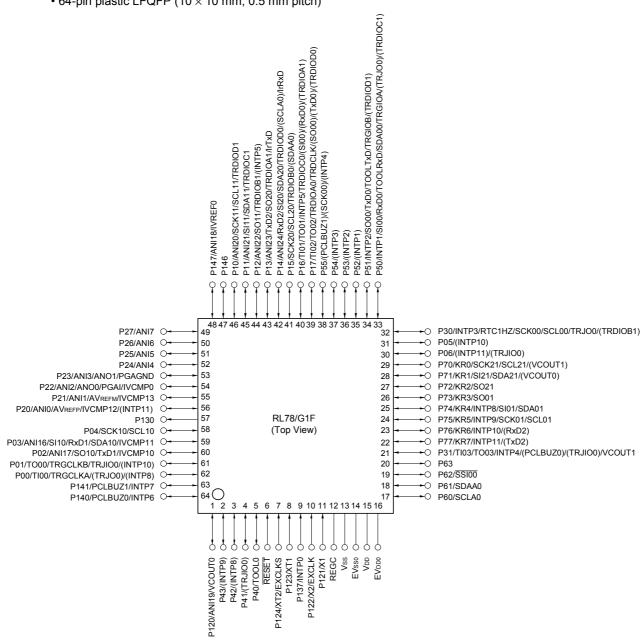
Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection registers 0 to 3 (PIOR0 to PIOR3).

1.3.5 64-pin products

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• 64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)



- Caution 1. Make EVsso pin the same potential as Vss pin.
- Caution 2. Make VDD pin the potential that is higher than EVDD0 pin.
- Caution 3. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).
- Remark 1. For pin identification, see 1.4 Pin Identification.
- Remark 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD and EVDD0 pins and connect the Vss and EVss0 pins to separate ground lines.
- Remark 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection registers 0 to 3 (PIOR0 to PIOR3).

1.4 Pin Identification

EXCLKS:

KR0 to KR7:

ANI0 to ANI7: Analog input PGAI: PGA input ANI16 to ANI24: Analog input PGAGND: PGA input

ANO0, ANO1: Analog output RTC1HZ: Real-time clock correction

AVREFM: Analog reference voltage

minus RxD0 to RxD2: Receive data

AVREFP: Analog reference voltage SCK00, SCK01, SCK10: Serial clock input/output

plus SCK11, SCK20, SCK21: Serial clock input/output

clock (1 Hz) output

Data input/output for tool

EVDD0: Power supply for port SCLA0: Serial clock input/output

EVSs0: Ground for port SCL00, SCL01, SCL10, SCL11: Serial clock output

EXCLK: External clock input SCL20, SCL21: Serial clock output

(main system clock)SDAA0:Serial data input/outputExternal clock inputSDA00, SDA01, SDA10:Serial data input/output

(subsystem clock) SDA11, SDA20, SDA21: Serial data input/output

INTP0 to INTP11: External interrupt input SI00, SI01, SI10, SI11: Serial data input IrRxD: Receive Data for IrDA SI20, SI21: Serial data input IrTxD: Transmit Data for IrDA SO00, SO01, SO10: Serial data output IVCMP0: Comparator 0 input SO11, SO20, SO21: Serial data output

IVCMP10 to IVCMP13: Comparator 1 input / SSI00: Serial interface chip select input

reference input TI00 to TI03: Timer input

IVREF0: Comparator 0 reference TO00 to TO03: Timer output

input TRJO0: Timer output

P00 to P06: Port 0 TOOLRxD, TOOLTxD: Data input/output for external device

TOOL0:

P10 to P17: Port 1 TRDCLK, TRGCLKA: Timer external input clock
P20 to P27: Port 2 TRGCLKB: Timer external Input clock

P30, P31: Port 3 TRDIOA0, TRDIOB0: Timer input/output

P40 to P43: Port 4 TRDIOC0, TRDIOD0: Timer input/output P50 to P55: Port 5 TRDIOA1, TRDIOB1: Timer input/output P60 to P63: Port 6 TRDIOC1, TRDIOD1: Timer input/output P70 to P77: Port 7 TRGIOA, TRGIOB, TRJIO0: Timer input/output P120 to P124: Port 12 TxD0 to TxD2: Transmit data P130, P137 Port 13 VCOUT0, VCOUT1: Comparator output

P140, P141, P146, Port 14 VDD: Power supply
P147: Vss: Ground

PCLBUZ0, PCLBUZ1: Programmable clock output/ X1, X2: Crystal oscillator (main system clock)

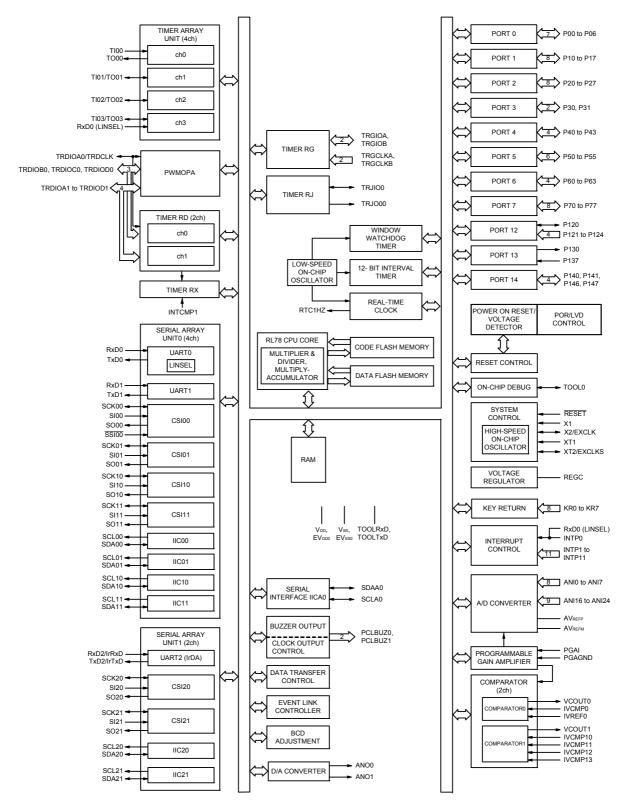
buzzer output XT1, XT2: Crystal oscillator (subsystem clock)

REGC: Regulator capacitance

Key return

RESET: Reset

1.5 Block Diagram



Remark Block diagram of 64-pin products is shown as an example. For difference of the block diagram other than 64-pin products, refer to **1.6 Outline of Functions**.

1.6 Outline of Functions

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

(1/2)

						•			
		24-pin	32-pin	36-pin	48-pin	64-pin			
	Item	R5F11B7x (x = C, E)	R5F11BBx (x = C, E)	R5F11BCx (x = C, E)	R5F11BGx (x = C, E)	R5F11BLx (x = C, E)			
Code flash mer	mory (KB)	32, 64	32, 64	32, 64	32, 64	32, 64			
Data flash men	nory (KB)	4	4	4	4	4			
RAM (KB)		5.5 Note	5.5 Note	5.5 Note	5.5 Note	5.5 Note			
Address space		1 MB							
Main system clock	High-speed system clock High-speed on-chip oscillator clock (fiн)	HS (high-speed r HS (high-speed r LS (low-speed m LV (low-voltage n HS (high-speed mai HS (high-speed main LS (low-speed main	(1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz (VDD = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (VDD = 1.8 to 2.7 V), LV (low-voltage main) mode: 1 to 4 MHz (VDD = 1.6 to 1.8 V) HS (high-speed main) mode: 1 to 32 MHz (VDD = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V), S (low-speed main) mode: 1 to 8 MHz (VDD = 1.8 to 5.5 V), V (low-voltage main) mode: 1 to 4 MHz (VDD = 1.6 to 5.5 V)						
Subsystem cloo	ck	_	_	XT1 (crystal) oscilla (EXCLKS) 32.768 k	tion, external subsyst Hz	em clock input			
Low-speed on-	chip oscillator clock	15 kHz (TYP.): V _{DD} = 1.6 to 5.5 V							
General-purpos	se register	8 bits × 32 registers (8 bits × 8 registers × 4 banks)							
Minimum instru	ction execution time	0.03125 μs (High-speed on-chip oscillator clock: fiн = 32 MHz operation)							
		0.05 μs (High-speed	d system clock: fmx =	20 MHz operation)					
		_	_	30.5 μs (Subsystem	clock: fsuB = 32.768	kHz operation)			
Instruction set		Multiplication (8 biMultiplication and	ctor/logical operation ts \times 8 bits, 16 bits \times 1 Accumulation (16 bits	6 bits), Division (16 b		,			
I/O port	Total	20	28	31	44	58			
	CMOS I/O	17 (N-ch O.D. output [VDD withstand voltage]: 10)	25 (N-ch O.D. output [Vpp withstand voltage]: 12)	24 (N-ch O.D. output [VDD withstand voltage]: 10)	34 (N-ch O.D. output [VDD withstand voltage]: 12)	48 (N-ch O.D. output [Vpp withstand voltage]: 12)			
	CMOS input	3	3	5	5	5			
	CMOS output	_	_	_	1	1			
	N-ch open-drain I/O (6 V tolerance)	_	_	2	4	4			
Timer	16-bit timer	9 channels (TAU: 4 channels, T Timer RG: 1 channel		imer RD: 2 channels	(with PWMOPA), Tim	ner RX: 1 channel,			
	Watchdog timer	1 channel							
	Real-time clock (RTC)	1 channel							
	12-bit interval timer	1 channel							
	Timer output	Timer outputs: 13 channels PWM outputs: 8 channels	Timer outputs: 16 channels PWM outputs: 9 channels						
	RTC output	-	_	1 • 1 Hz (subsystem of	clock: fsuB = 32.768 k	Hz)			

Note This is about 4.5 KB when the self-programming function and data flash function are used (For details, see CHAPTER 3 in the RL78/G1F User's Manual).

(2/2)

		_				(2/2	
		24-pin	32-pin	36-pin	48-pin	64-pin	
Ite	em	R5F11B7x (x = C, E)	R5F11BBx (x = C, E)	R5F11BCx (x = C, E)	R5F11BGx (x = C, E)	R5F11BLx (x = C, E)	
Clock output/buzzer	output	2	2	2	2	2	
		,	z, 9.76 kHz, 1.25 MH; k: fmain = 20 MHz ope	z, 2.5 MHz, 5 MHz, 1 eration)	0 MHz	l	
8/10-bit resolution A/	D converter	8 channels	13 channels	15 channels	17 channels	17 channels	
8-bit D/A converter		1 channel		2 cha	nnels	ı	
Comparator				2 channels			
Programmable gain a	amplifier (PGA)			1 channel			
Serial interface		[24-pin, 32-pin, 36-pin products] • CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I ² C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I ² C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I ² C: 1 channel [48-pin products] • CSI: 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified I ² C: 2 channels • CSI: 1 channel/UART: 1 channel/simplified I ² C: 1 channel • CSI: 2 channels/UART: 1 channel/simplified I ² C: 2 channels • CSI: 2 channels/UART: 1 channel/simplified I ² C: 2 channels • CSI: 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified I ² C: 2 channels • CSI: 2 channels/UART: 1 channel/simplified I ² C: 2 channels					
	<u> </u>		ART: 1 channel/simpl				
	I ² C bus	1 channel	1 channel	1 channel	1 channel	1 channel	
Data transfer controller (DTC)		30 sources	32 sources	31 sources	32 sources	33 sources	
(ELC)	Event input	21	21	21	22	22	
(ELC)	Event trigger output	9	10	10	10	10	
Vectored interrupt	Internal	25	25	25	25	25	
sources	External	9	11	10	12	13	
Key interrupt		_	_	_	6	8	
Reset		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Note Internal reset by RAM parity error Internal reset by illegal-memory access					
Power-on-reset circu	it	Power-on-reset: Power-down-reset	1.51 ±0.04 V (TA = 1.51 ±0.06 V (TA = 1.50 ±0.04 V (TA = 1.50 ±0.06 V (TA =	= -40 to +105°C) = -40 to +85°C)			
Voltage detector		[TA = -40 to +85°C] • Rising edge: 1.67 ±0.03 V to 4.00 ±0.08 V (14 stages) • Falling edge: 1.63 ±0.03 V to 3.98 ±0.08 V (14 stages) [TA = -40 to +105°C (G: Industrial applications)] • Rising edge: 2.61 ±0.1 V to 4.06 ±0.16 V (8 stages) • Falling edge: 2.55 ±0.1 V to 3.98 ±0.15 V (8 stages)					
On-chip debug functi	on	Provided					
Power supply voltage	•	V _{DD} = 1.6 to 5.5 V (⁻¹ V _{DD} = 2.4 to 5.5 V (⁻¹	•				
Operating ambient te	mperature	$T_A = -40 \text{ to } +85^{\circ}\text{C}$ (A	A: Consumer applicat	ions), T _A = -40 to +10	05°C (Industrial appli	cations),	

The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not is issued by emulation with the in-circuit emulator or on-chip debug emulator.

2. ELECTRICAL SPECIFICATIONS (TA = -40 to +85°C)

This chapter describes the following electrical specifications.

Target products A: Consumer applications TA = -40 to +85°C

R5F11BxxAxx

- G: Industrial applications when TA = -40 to +105°C products is used in the range of TA = -40 to +85°C R5F11BxxGxx
- Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
- Caution 2. With products not provided with an EVDD0, EVsso pin, replace EVDD0 with VDD, or replace EVsso with Vss.
- Caution 3. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G1F User's Manual.

2.1 Absolute Maximum Ratings

Absolute Maximum Ratings

(1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	VDD		-0.5 to +6.5	V
	EV _{DD0}		-0.5 to +6.5	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8	V
			and -0.3 to V _{DD} +0.3 Note 1	
Input voltage	VI1	P00 to P06, P10 to P17, P30, P31,	-0.3 to EVDD0 +0.3	V
		P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	and -0.3 to V _{DD} +0.3 Note 2	
	Vı2	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	VI3	P20 to P27, P121 to P124, P137, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 Note 2	V
Output voltage	Vo1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P60 to P63, P70 to P77, P120, P130, P140, P141, P146, P147	-0.3 to EVDD0 +0.3 and -0.3 to VDD +0.3 Note 2	V
	VO2	P20 to P27	-0.3 to V _{DD} +0.3 Note 2	V
Analog input voltage	VAI1	ANI16 to ANI24	-0.3 to EVDD0 +0.3 and -0.3 to AVREF(+) +0.3 Notes 2, 3	V
	VAI2	ANI0 to ANI7	-0.3 to VDD +0.3 and -0.3 to AVREF(+) +0.3 Notes 2, 3	V

- Note 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
- Note 2. Must be 6.5 V or lower.
- Note 3. Do not exceed AVREF (+) + 0.3 V in case of A/D conversion target pin.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter.

 That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
- Remark 2. AVREF (+): + side reference voltage of the A/D converter.
- Remark 3. Vss: Reference voltage

Absolute Maximum Ratings

(2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P130, P140, P141, P146, P147	-40	mA
		Total of all	P00 to P04, P40 to P43,P120, P130, P140, P141	-70	mA
		pins -170 mA	P05, P06, P10 to P17, P30, P31, P50 to P55, P70 to P77, P146, P147	-100	mA
	Іон2	Per pin	P20 to P27	-0.5	mA
		Total of all pins		-2	mA
Output current, low	loL1	Per pin	P00 to P06, P10 to P17, P30, P31, P40-P43, P50 to P55, P60 to P63, P70 to P77, P120, P130, P140, P141, P146, P147	0 40	mA
		Total of all	P00 to P04, P40 to P47, P120, P130, P140, P141	70	mA
		pins 170 mA	P05, P06, P10 to P17, P30, P31, P50 to P55, P70 to P77, P146, P147	100	mA
	IOL2	Per pin	P20 to P27	1	mA
		Total of all pins		5	mA
Operating ambient tem-	TA	In normal o	pperation mode	-40 to +85	°C
perature		In flash me	mory programming mode		
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter.

That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

2.2 Oscillator Characteristics

2.2.1 X1, XT1 characteristics

 $(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le EV_{DD0} = V_{DD} \le 5.5 \text{ V}, Vss = 0 \text{ V})$

Resonator	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) Note	Ceramic resonator/	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	1.0		20.0	MHz
	crystal resonator	2.4 V ≤ V _{DD} < 2.7 V	1.0		16.0	
		1.8 V ≤ V _{DD} < 2.4 V	1.0		8.0	
		1.6 V ≤ V _{DD} < 1.8 V	1.0		4.0	
XT1 clock oscillation frequency (fxT) Note	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time.

Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to 5.4 System Clock Oscillator in the RL78/G1F User's Manual.

2.2.2 On-chip oscillator characteristics

 $(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le EV_{DD0} = V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

Oscillators	Parameters	Cor	nditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency	fıн	2.7 V ≤ VDD ≤ 5.5 V		1		32	MHz
Notes 1, 2		2.4 V ≤ V _{DD} < 2.7 V	V	1		16	MHz
		1.8 V ≤ V _{DD} < 2.4 V	V	1		32	MHz
		1.6 V ≤ V _{DD} < 1.8 V	V	1		4	MHz
High-speed on-chip oscillator clock frequency		T _A = -20 to +85°C	1.8 V ≤ VDD ≤ 5.5 V	-1		1	%
accuracy		1	1.6 V ≤ VDD < 1.8 V	-5		5	%
		Ta = -40 to -20°C	1.8 V ≤ V _{DD} < 5.5 V	-1.5		1.5	%
			1.6 V ≤ V _{DD} < 1.8 V	-5.5		5.5	%
Low-speed on-chip oscillator clock frequency	fıL				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 4 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.

2.3 DC Characteristics

2.3.1 Pin characteristics

 $(TA = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EVDD0} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	Іон1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P55, P70 to P77, P120, P130, P140, P141, P146, P147				-10.0 Note 2	mA
		, , , , , , , , , , , , , , , , , , , ,	4.0 V ≤ EVDD0 ≤ 5.5 V			-55.0	mA
		P120, P130, P140, P141	2.7 V ≤ EV _{DD0} < 4.0 V			-10.0	mA
		(When duty ≤ 70% Note 3)	1.8 V ≤ EV _{DD0} < 2.7 V			-5.0	mA
		1	1.6 V ≤ EV _{DD0} < 1.8 V			-2.5	mA
		Total of P05, P06, P10 to P17,	$4.0 \text{ V} \leq \text{EVDD0} \leq 5.5 \text{ V}$			-80.0	mA
		P30, P31, P50 to P53, P70 to P77, P146, P147	2.7 V ≤ EV _{DD0} < 4.0 V			-19.0	mA
		(When duty $\leq 70\%$ Note 3)	1.8 V ≤ EV _{DD0} < 2.7 V			-10.0	mA
		(Wilding and)	1.6 V ≤ EV _{DD0} < 1.8 V			-5.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})				-135.0 Note 4	mA
	Іон2	Per pin for P20 to P27				-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	1.6 V ≤ VDD ≤ 5.5 V			-1.5	mA

- Note 1. Value of current at which the device operation is guaranteed even if the current flows from the EVDDO, VDD pins to an output pin.
- Note 2. Do not exceed the total current value.
- **Note 3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (IOH × 0.7)/(n × 0.01)

<Example> Where n = 80% and IOH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

Note 4. The applied current for the products for industrial application (R5F11BxxGxx) is -100 mA.

Caution P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43, P50 to P55, P71, P74 do not output high level in N-ch open-drain mode.

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

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Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	lo _{L1}	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77,P120, P130, P140, P141, P146, P147				20.0 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		Total of P00 to P04, P40 to P43,	4.0 V ≤ EVDD0 ≤ 5.5 V			70.0	mA
		P120, P130, P140, P141	2.7 V ≤ EV _{DD0} < 4.0 V			15.0	mA
		(When duty ≤ 70% Note 3)	1.8 V ≤ EVDD0 < 2.7 V			9.0	mA
			1.6 V ≤ EV _{DD0} < 1.8 V			4.5	mA
		Total of P05, P06, P10 to P17,	4.0 V ≤ EVDD0 ≤ 5.5 V			80.0	mA
		P30, P31, P50 to P55, P60 to	2.7 V ≤ EV _{DD0} < 4.0 V			35.0	mA
		P63, P70 to P77, P146, P147	1.8 V ≤ EV _{DD0} < 2.7 V			20.0	mA
		(When duty ≤ 70% Note 3)	1.6 V ≤ EVDD0 < 1.8 V			10.0	mA
		Total of all pins (When duty ≤ 70% Note 3)				150.0	mA
	lol2	Per pin for P20 to P27				0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	1.6 V ≤ VDD ≤ 5.5 V			5.0	mA

- Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso and Vss pins.
- Note 2. Do not exceed the total current value.
- **Note 3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(IoL \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and IoL = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

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Items	Symbol	Conditions	3	MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	Normal input buffer	0.8 EVDD0		YP. MAX. EVDDO EVDDO EVDDO O.2 EVDDO O.8 O.5 O.32 O.3 VDD	V
	VIH2	P01, P03, P04, P10, P14 to P17, P30, P43, P50, P53 to P55,	TTL input buffer 4.0 V ≤ EVDD0 ≤ 5.5 V	2.2			V
			TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	2.0	EVDD0 EVDD0 EVDD0 O.2 EVDD0 O.32 O.3 VDD	V	
			TTL input buffer 1.6 V ≤ EVDD0 < 3.3 V	1.5		EV _{DD0}	V
	VIH3	P20 to P27 (when P20 is used as	a port pin)	0.7 Vdd		VDD	V
	VIH4	P60 to P63		0.7 EVDD0		6.0	V
	VIH5	P121 to P123, P137, EXCLK, EX P20 is used as INTP11 pin)	CLKS, RESET (when	0.8 VDD		VDD	V
Input voltage, low	VIL1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	Normal input buffer	0		EVDD0 EVDD0 VDD 6.0 VDD 0.2 EVDD0 0.8 0.5 0.32	V
	VIL2	P01, P03, P04, P10, P14 to P17, P30, P43, P50, P53 to P55,	TTL input buffer 4.0 V ≤ EVDD0 ≤ 5.5 V	0			V
			TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	0		0.5	V
			TTL input buffer 1.6 V ≤ EVDD0 < 3.3 V	0		0.32	٧
	VIL3	P20 to P27 (when P20 is used as	a port pin)	0		0.3 VDD	V
	VIL2 P01, P03, P04 P30, P43, P50 VIL3 P20 to P27 (w VIL4 P60 to P63 VIL5 P121 to P124	P60 to P63		0		0.3 EVDD0	V
	VIL5	P121 to P124, P137, EXCLK, EX P20 is used as INTP11 pin)	CLKS, RESET (when	0		0.2 VDD	V

Caution The maximum value of VIH of pins P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43, P50 to P55, P71, P74 is EVDD0, even in the N-ch open-drain mode.

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

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Items	Symbol	Condition	ns	MIN.	TYP.	MAX.	Unit
Output voltage, high	Vон1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55,	$4.0 \text{ V} \le \text{EVDD0} \le 5.5 \text{ V},$ IOH1 = -10.0 mA	EVDD0 - 1.5			V
		P70 to P77, P120, P130, P140, P141, P146, P147	4.0 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -3.0 mA	EVDD0 - 0.7			V
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOH1 = -2.0 mA	EVDD0 - 0.6			V
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOH1 = -1.5 mA	EVDD0 - 0.5			V
			1.6 V ≤ EV _{DD0} < 1.8 V, IOH1 = -1.0 mA	EVDD0 - 0.5			V
	VOH2	P20 to P27	1.6 V ≤ VDD ≤ 5.5 V, IOH2 = -100 μA	VDD - 0.5			V
Output voltage, low	VOL1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55,	4.0 V ≤ EVDD0 ≤ 5.5 V, IOL1 = 20.0 mA		1.3	V	
	P70 to P77, P120, P130, P140, P141, P146, P147 $4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ \text{IoL1} = 8.5 \text{ mA}$		0.7	V			
			$2.7 \text{ V} \le \text{EVDD0} \le 5.5 \text{ V},$ $\text{IOL1} = 3.0 \text{ mA}$			0.6	V
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $\text{IOL1} = 1.5 \text{ mA}$			0.4	V
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $\text{IoL1} = 0.6 \text{ mA}$			0.4	V
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $\text{IoL1} = 0.3 \text{ mA}$			0.4	V
	VOL2	P20 to P27	$1.6 \text{ V} \le \text{VDD} \le 5.5 \text{ V},$ $\text{IOL2} = 400 \mu\text{A}$			0.4	V
	VOL3	P60 to P63	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $\text{Iol3} = 15.0 \text{ mA}$			2.0	V
			$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $\text{Iol3} = 5.0 \text{ mA}$			0.4	V
			2.7 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 3.0 mA			0.4	V
			1.8 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 2.0 mA			0.4	V
			$1.6 \text{ V} \le \text{EVDD0} \le 5.5 \text{ V},$ $\text{IoL3} = 1.0 \text{ mA}$			0.4	V

Caution P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43, P50 to P55, P71, P74 do not output high level in N-ch opendrain mode.

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

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Items	Symbol	Conditi	MIN.	TYP.	MAX.	Unit		
Input leakage cur- rent, high	ILIH1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	VI = EVDD0			1	μА	
	ILIH2	P20 to P27, P137, RESET	VI = VDD				1	μΑ
	Ішн3	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VDD	In input port or external clock input			1	μА
				In resonator con- nection			10	μΑ
Input leakage current, low	ILIL1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	VI = EVsso				-1	μΑ
	ILIL2	P20 to P27, P137, RESET	Vı = Vss			-1	μΑ	
	ILIL3	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VSS	In input port or external clock input			-1	μА
				In resonator con- nection			-10	μΑ
On-chip pull-up resistance	Rυ	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	VI = EVsso	, In input port	10	20	100	kΩ

2.3.2 Supply current characteristics

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply IDD1	IDD1	Operat-	HS (high-speed main)	fHOCO = 64 MHz,	Basic	V _{DD} = 5.0 V		2.4		mA
current		ing mode	mode Note 5	fih = 32 MHz Note 3	operation	V _{DD} = 3.0 V		2.4		=
Note 1				fHOCO = 32 MHz,	Basic	V _{DD} = 5.0 V		2.1		
				fiH = 32 MHz Note 3	operation	V _{DD} = 3.0 V		2.1		
			HS (high-speed main)	fHOCO = 64 MHz,	Normal	V _{DD} = 5.0 V		5.2	8.7	mA
			mode Note 5	fih = 32 MHz Note 3	operation	V _{DD} = 3.0 V		5.2	8.7	
				fносо = 32 MHz,	Normal	V _{DD} = 5.0 V		4.8	8.1	
				fih = 32 MHz Note 3	operation	V _{DD} = 3.0 V		4.8	8.1	
				fносо = 48 MHz,	Normal	V _{DD} = 5.0 V		4.1	6.9	
				fih = 24 MHz Note 3	operation	V _{DD} = 3.0 V		4.1	6.9	
				fHOCO = 24 MHz,	Normal	V _{DD} = 5.0 V		3.8	6.3	
				fih = 24 MHz Note 3	operation	V _{DD} = 3.0 V		3.8	6.3	
		1		fHOCO = 16 MHz,	Normal	V _{DD} = 5.0 V		2.8	4.6	
				fih = 16 MHz Note 3	operation	V _{DD} = 3.0 V		2.8	4.6	
			LS (low-speed main) mode Note 5	fHOCO = 8 MHz, fIH = 8 MHz Note 3	Normal	V _{DD} = 3.0 V		1.3	2.1	mA
					operation	V _{DD} = 2.0 V		1.3	2.1	1
			LV (low-voltage main)		Normal operation	V _{DD} = 3.0 V		1.3	1.9	mA
			mode Note 5			V _{DD} = 2.0 V		1.3	1.9	
			HS (high-speed main)	f _{MX} = 20 MHz Note 2,	Normal	Square wave input		3.3	5.3	mA
		mode Note 5	V _{DD} = 5.0 V	operation	Resonator connection		3.5	5.5	1	
				f _{MX} = 20 MHz Note 2,	Normal	Square wave input		3.3	5.3	mA
				V _{DD} = 3.0 V	operation	Resonator connection		3.5	5.5	
				fmx = 10 MHz Note 2,	Normal	Square wave input		2	3.1	
				V _{DD} = 5.0 V f _{MX} = 10 MHz Note 2, V _{DD} = 3.0 V f _{MX} = 8 MHz Note 2,	operation Normal operation Normal	Resonator connection		2.1	3.2	
						Square wave input		2	3.1	
						Resonator connection		2.1	3.2	
			LS (low-speed main)			Square wave input		1.2	1.9	
			mode Note 5	V _{DD} = 3.0 V	operation	Resonator connection		1.2	2	
				f _{MX} = 8 MHz Note 2,	Normal	Square wave input		1.2	1.9	
				V _{DD} = 2.0 V	operation	Resonator connection		1.2	2	
			Subsystem clock	fsuB = 32.768 kHz Note 4	Normal	Square wave input		4.7	6.1	μА
			operation	TA = -40°C	operation	Resonator connection		4.7	6.1	
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		4.7	6.1	1
			T _A = +25°C	operation	Resonator connection		4.7	6.1		
			fsuB = 32.768 kHz Note 4	Normal	Square wave input		4.8	6.7		
			T _A = +50°C	operation	Resonator connection		4.8	6.7		
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		4.8	7.5	-
				T _A = +70°C	operation	Resonator connection		4.8	7.5	
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		5.4	8.9	
				T _A = +85°C	operation	Resonator connection		5.4	8.9	

(Notes and Remarks are listed on the next page.)

- Note 1. Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing data flash rewrite.
- Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 3. When high-speed system clock and subsystem clock are stopped.
- **Note 4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
- Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @1 \text{ MHz}$ to 32 MHz

 $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V@1 MHz}$ to 16 MHz

LS (low-speed main) mode: 1.8 V \leq VDD \leq 5.5 V@1 MHz to 8 MHz LV (low-voltage main) mode: 1.6 V \leq VDD \leq 5.5 V@1 MHz to 4 MHz

- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3. fin: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is Ta = 25°C

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

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Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply current Note 1	I _{DD2}	HALT mode	HS (high-speed main)	fHOCO = 64 MHz,	V _{DD} = 5.0 V		8.0	3.09	mA
	Note 2		mode Note 7	fiH = 32 MHz Note 4	V _{DD} = 3.0 V		0.8	3.09	
				fhoco = 32 MHz,	V _{DD} = 5.0 V		0.54	2.4	
				fiH = 32 MHz Note 4	V _{DD} = 3.0 V		0.54	2.4	1
				fносо = 48 MHz,	V _{DD} = 5.0 V		0.62	2.4	
				fiH = 24 MHz Note 4	V _{DD} = 3.0 V		0.62	2.4	1
				fhoco = 24 MHz,	V _{DD} = 5.0 V		0.44	1.83	
				fiH = 24 MHz Note 4	V _{DD} = 3.0 V		0.44	1.83	
				fHOCO = 16 MHz,	V _{DD} = 5.0 V		0.4	1.38	
				fiH = 16 MHz Note 4	V _{DD} = 3.0 V		0.4	1.38	
			LS (low-speed main)	fHOCO = 8 MHz,	V _{DD} = 3.0 V		260	790	μΑ
			mode Note 7	fiH = 8 MHz Note 4	V _{DD} = 2.0 V		260	790	
			LV (low-voltage main)	fHOCO = 4 MHz,	V _{DD} = 3.0 V		420	830	μΑ
			HS (high-speed main) mode Note 7	fiH = 4 MHz Note 4	V _{DD} = 2.0 V		420	830	
				f _{MX} = 20 MHz Note 3, V _{DD} = 5.0 V	Square wave input		0.28	1.55	mA
					Resonator connection		0.49	1.74	
				f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.28	1.55	
					Resonator connection		0.49	1.74	
			LS (low-speed main) mode Note 7	f _{MX} = 10 MHz Note 3, V _{DD} = 5.0 V	Square wave input		0.19	0.86	
					Resonator connection		0.3	0.93	
				f _{MX} = 10 MHz Note 3, V _{DD} = 3.0 V	Square wave input		0.19	0.86	
					Resonator connection		0.3	0.93	
				f _{MX} = 8 MHz Note 3, V _{DD} = 3.0 V f _{MX} = 8 MHz Note 3,	Square wave input		95	640	μΑ
					Resonator connection		145	680	
					Square wave input		95	640	
				V _{DD} = 2.0 V	Resonator connection		145	680	
			Subsystem clock	fsuB = 32.768 kHz Note 5,	Square wave input		0.25	0.57	μΑ
			operation	TA = -40°C	Resonator connection		0.44	0.76	
				fsuB = 32.768 kHz Note 5,	Square wave input		0.3	0.57	
				TA = 25°C	Resonator connection		0.49	0.76	
				fsuB = 32.768 kHz Note 5,	Square wave input		0.36	1.17	
				TA = 50°C	Resonator connection		0.59	1.36	
				fsuB = 32.768 kHz Note 5,	Square wave input		0.49	1.97	
				TA = 70°C	Resonator connection		0.72	2.16	
				fsuB = 32.768 kHz Note 5,	Square wave input		0.97	3.37	
-				TA = 85°C	Resonator connection		1.16	3.56	
	IDD3	STOP mode	T _A = -40°C	•	•		0.18	0.51	μА
	Note 6	Note 8	T _A = +25°C				0.24	0.51	
			T _A = +50°C				0.29	1.1	1
			T _A = +70°C				0.41	1.9	1
			T _A = +85°C				0.9	3.3	

(Notes and Remarks are listed on the next page.)

- Note 1. Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing data flash rewrite.
- Note 2. During HALT instruction execution by flash memory.
- Note 3. When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 4. When high-speed system clock and subsystem clock are stopped.
- Note 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
- Note 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz to } 32 \text{ MHz}$

 $2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V@1 MHz}$ to 16 MHz

LS (low-speed main) mode: 1.8 V \leq VDD \leq 5.5 V@1 MHz to 8 MHz LV (low-voltage main) mode: 1.6 V \leq VDD \leq 5.5 V@1 MHz to 4 MHz

- Note 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.)

 Remark 3. fH: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol	Conditi	MIN.	TYP.	MAX.	Unit	
Low-speed on-chip oscillator operating current	IFIL Note 1				0.2		μΑ
RTC operating current	IRTC Notes 1, 2, 3				0.02		μΑ
12-bit interval timer operat- ing current	I _{IT} Notes 1, 2, 4				0.02		μА
Watchdog timer operating current	I _{WDT} Notes 1, 2, 5	fı∟ = 15 kHz			0.22		μА
A/D converter operating current	IADC Notes 1, 6	When conversion at maximum speed	Normal mode, AVREFP = VDD = 5.0 V		1.3	1.7	mA
			Low voltage mode, AVREFP = VDD = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	IADREF Note 1				75		μА
Temperature sensor operating current	ITMPS Note 1				75		μА
D/A converter operating current	IDAC Notes 1, 11	Per D/A converter channel			1.5	mA	
PGA operating current		Operation			480	700	μА
Comparator operating cur- rent	ICMP Notes 1, 12	Operation (per comparator chan- nel, constant current for compara-	When the internal reference voltage is not in use		50	100	μΑ
		tor included)	When the internal reference voltage is in use		60	110	μА
LVD operating current	I _{LVD} Notes 1, 7				0.08		μΑ
Self-programming operating current	IFSP Notes 1, 9				2.5	12.2	mA
BGO operating current	I _{BGO} Notes 1, 8				2.5	12.2	mA
SNOOZE operating current	I _{SNOZ} Note 1	ADC operation	The mode is performed Note 10		0.5	0.6	mA
			The A/D conversion operations are performed, Low voltage mode, AVREFP = VDD = 3.0 V		1.2	1.44	
		CSI/UART operation		0.7	0.84		
		DTC operation		3.1			

- Note 1. Current flowing to VDD.
- Note 2. When high speed on-chip oscillator and high-speed system clock are stopped.
- Note 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
- Note 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator).

 The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
- Note 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- Note 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- Note 8. Current flowing during programming of the data flash.
- Note 9. Current flowing during self-programming.
- Note 10. For shift time to the SNOOZE mode, see 26.3.3 SNOOZE mode in the RL78/G1F User's Manual.



- **Note 11.** Current flowing only to the D/A converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IDAC when the D/A converter operates in an operation mode or the HALT mode.
- Note 12. Current flowing only to the comparator circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2, or IDD3 and ICMP when the comparator circuit is in operation.
- Remark 1. fil: Low-speed on-chip oscillator clock frequency
- Remark 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 3. fclk: CPU/peripheral hardware clock frequency
- Remark 4. Temperature condition of the TYP. value is TA = 25°C

2.4 AC Characteristics

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (min-	Tcy	Main system	HS (high-speed main)	$2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	0.03125		1	μs
imum instruction exe-		clock (fmain)	mode	2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
cution time)		operation	LS (low-speed main) mode	1.8 V ≤ VDD ≤ 5.5 V	0.125		1	μs
			LV (low-voltage main) mode	1.6 V ≤ VDD ≤ 5.5 V	0.25		1	μs
		Subsystem clo	ock (fsub) operation	1.8 V ≤ VDD ≤ 5.5 V	28.5	30.5	31.3	μs
		In the self-	HS (high-speed main)	$2.7 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$	0.03125		1	μs
		program-	mode	2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
		ming mode	LS (low-speed main) mode	1.8 V ≤ VDD ≤ 5.5 V	0.125		1	μs
			LV (low-voltage main) mode	1.8 V ≤ VDD ≤ 5.5 V	0.25		1	μs
External system clock	fEX	2.7 V ≤ V _{DD} ≤	5.5 V		1.0		20.0	MHz
frequency		$2.4 \text{ V} \leq \text{Vdd} \leq 2.7 \text{ V}$			1.0		16.0	MHz
		1.8 V ≤ V _{DD} < 2.4 V			1.0		8.0	MHz
		1.6 V ≤ V _{DD} <	1.8 V		1.0		4.0	MHz
	fexs				32		35	kHz
External system clock	texh, texl	2.7 V ≤ V _{DD} ≤	5.5 V		24			ns
input high-level width,		2.4 V ≤ V _{DD} ≤	2.7 V		30			ns
low-level width		1.8 V ≤ V _{DD} <	2.4 V		60			ns
		1.6 V ≤ V _{DD} <	1.8 V		120			ns
	texhs,				13.7			μs
TI00 to TI03 input high-level width, low- level width	tтін, tтіL				1/fMCK + 10 Note			ns
Timer RJ input cycle	fc	TRJIO		2.7 V ≤ EVDD0 ≤ 5.5 V	100			ns
				1.8 V ≤ EVDD0 < 2.7 V	300			ns
				1.6 V ≤ EVDD0 < 1.8 V	500			ns
Timer RJ input high-	tтлін,	TRJIO		2.7 V ≤ EVDD0 ≤ 5.5 V	40			ns
level width, low-level	ttjil			1.8 V ≤ EVDD0 < 2.7 V	120			ns
width				1.6 V ≤ EV _{DD0} < 1.8 V	200			ns

Note The following conditions are required for low voltage interface when EVDD0 < VDD

 $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V: MIN. } 125 \text{ ns}$ $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V: MIN. } 250 \text{ ns}$

Remark fmck: Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel

number (n = 0 to 3))

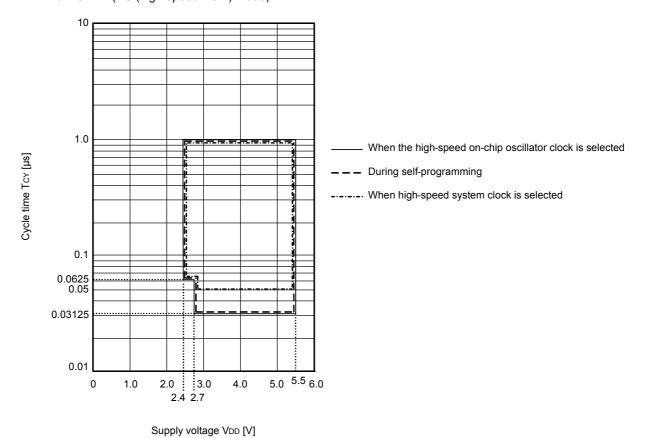
(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

(2/2)

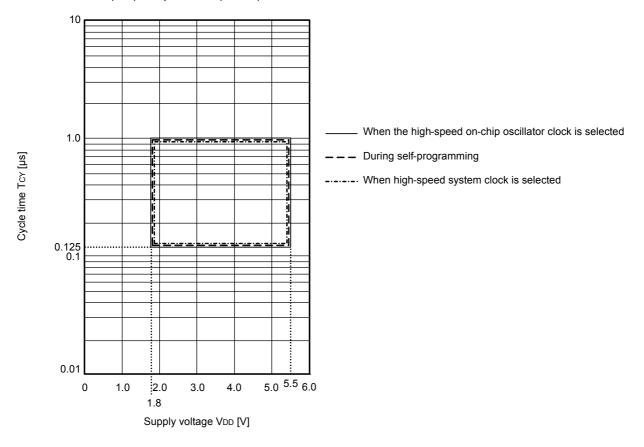
Items	Symbol	Condition	MIN.	TYP.	MAX.	Unit	
Timer RD input high-level width, low-level width	tтdiн, ttdil	TRDIOA0, TRDIOA1, TRDIOE TRDIOC0, TRDIOC1, TRDIO	3/fclk			ns	
Timer RD forced cutoff signal	ttdsil	P130/INTP0	2MHz < fclk ≤ 32 MHz	1			μs
input low-level width			fclk ≤ 2 MHz	1/fclk + 1			
Timer RG input high-level	tтgін,	TRGIOA, TRGIOB	1	2.5/fclk			ns
width, low-level width	ttgil						
TO00 to TO03,	fто	HS (high-speed main) mode	$4.0 \text{ V} \leq \text{EVDD0} \leq 5.5 \text{ V}$			16	MHz
TRJIO0, TRJO0,			2.7 V ≤ EVDD0 < 4.0 V			8	MHz
TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1,			1.8 V ≤ EVDD0 < 2.7 V			4	MHz
TRDIOCO, TRDIOC1,			1.6 V ≤ EV _{DD0} < 1.8 V			2	MHz
TRDIOD0, TRDIOD1,		LS (low-speed main) mode	1.8 V ≤ EVDD0 ≤ 5.5 V			4	MHz
TRGIOA, TRGIOB			1.6 V ≤ EV _{DD0} < 1.8 V			2	MHz
output frequency		LV (low-voltage main) mode	1.6 V ≤ EVDD0 ≤ 5.5 V			2	MHz
PCLBUZ0, PCLBUZ1 output	fPCL	HS (high-speed main) mode	4.0 V ≤ EVDD0 ≤ 5.5 V			16	MHz
frequency			2.7 V ≤ EV _{DD0} < 4.0 V			8	MHz
			1.8 V ≤ EVDD0 < 2.7 V			4	MHz
			1.6 V ≤ EVDD0 < 1.8 V			2	MHz
		LS (low-speed main) mode	1.8 V ≤ EVDD0 ≤ 5.5 V			4	MHz
			1.6 V ≤ EVDD0 < 1.8 V			2	MHz
		LV (low-voltage main) mode	1.8 V ≤ EVDD0 ≤ 5.5 V			4	MHz
			1.6 V ≤ EV _{DD0} < 1.8 V			2	MHz
Interrupt input high-level	tinth,	INTP0	1.6 V ≤ V _{DD} ≤ 5.5 V	1			μs
width, low-level width	tintl	INTP1 to INTP11	1.6 V ≤ EVDD0 ≤ 5.5 V	1			μs
Key interrupt input low-level	tkr	KR0 to KR7	1.8 V ≤ EVDD0 ≤ 5.5 V	250			ns
width			1.6 V ≤ EV _{DD0} < 1.8 V	1			μs
RESET low-level width	trsl		1	10			μs

Minimum Instruction Execution Time during Main System Clock Operation

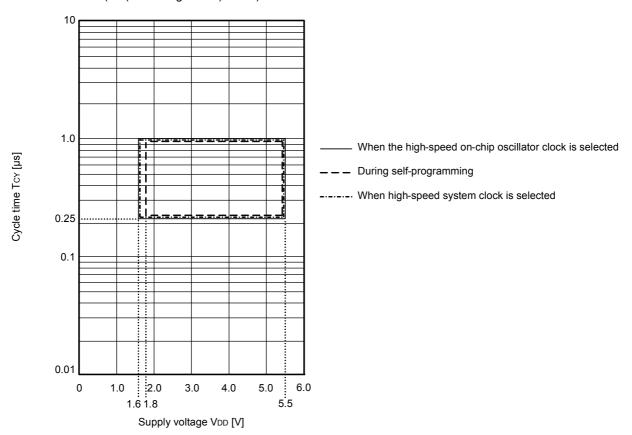
Tcy vs Vdd (HS (high-speed main) mode)



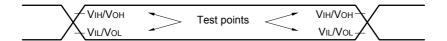
Tcy vs Vdd (LS (low-speed main) mode)



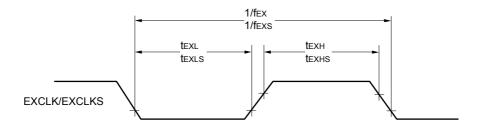
TCY vs VDD (LV (low-voltage main) mode)



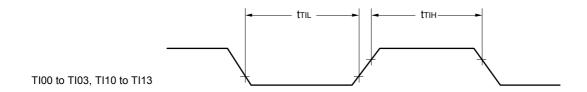
AC Timing Test Points

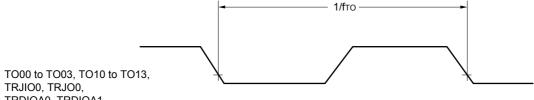


External System Clock Timing



TI/TO Timing



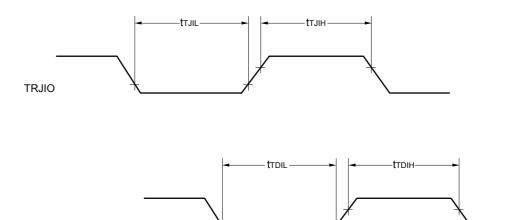


TRDIOA0, TRDIOA1,

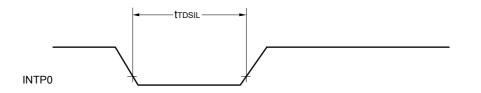
TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1,

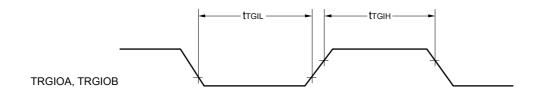
TRDIOD0, TRDIOD1,

TRGIOA, TRGIOB

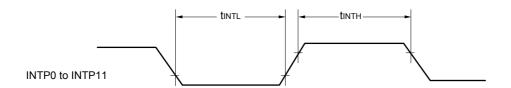


TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1

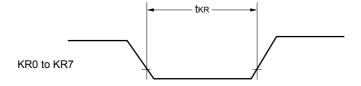




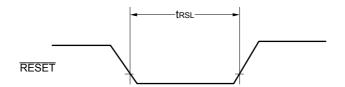
Interrupt Request Input Timing



Key Interrupt Input Timing

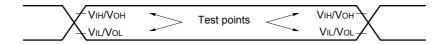


RESET Input Timing



2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

 $(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le EVDD0 \le 5.5 \text{ V}, \text{Vss} = EVss0 = 0 \text{ V})$

Parameter	Symbol	Conditions		Conditions HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-v	Unit					
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.					
Transfer rate		2.4	4 V ≤ EVDD0 ≤ 5.5 V		fMCK/6 Note 2		fмск/6		fмск/6	bps				
Note 1			Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		5.3		1.3		0.6	Mbps				
		1.	8 V ≤ EVDD0 ≤ 5.5 V		fmck/6 Note 2		fмск/6		fмск/6	bps				
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		5.3		1.3		0.6	Mbps				
		1.	7 V ≤ EVDD0 ≤ 5.5 V		fMCK/6 Note 2		fmck/6 Note 2		fмск/6	bps				
							Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		5.3		1.3		0.6	Mbps
		1.0	6 V ≤ EVDD0 ≤ 5.5 V		_		fmck/6 Note 2		fмск/6	bps				
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		_		1.3		0.6	Mbps				

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

Note 2. The following conditions are required for low voltage interface when EVDD0 < VDD.

 $2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V: MAX. } 2.6 \text{ Mbps}$

 $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.4 \text{ V}$: MAX. 1.3 Mbps

 $1.6~V \le EV_{DD0} < 1.8~V$: MAX. 0.6~Mbps

Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

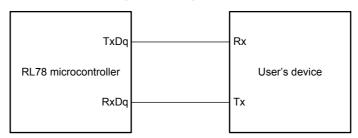
HS (high-speed main) mode: 32 MHz (2.7 V \leq VDD \leq 5.5 V)

16 MHz (2.4 V \leq VDD \leq 5.5 V)

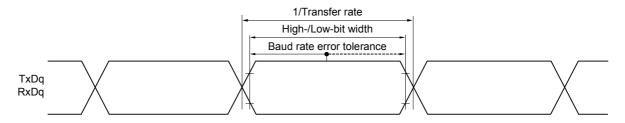
LS (low-speed main) mode: 8 MHz (1.8 V \leq VDD \leq 5.5 V) LV (low-voltage main) mode: 4 MHz (1.6 V \leq VDD \leq 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1, 3, 5, 7)

Remark 2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10, 11))

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(TA = -40 to +85°C, 2.7 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 2/fcLk	4.0 V ≤ EVDD0 ≤ 5.5 V	62.5		250		500		ns
			2.7 V ≤ EVDD0 ≤ 5.5 V	83.3		250		500		ns
SCKp high-/low-level	tкн1,	4.0 V ≤ EV _{DD0}	≤ 5.5 V	tkcy1/2 - 7		tkcy1/2 - 50		tксү1/2 - 50		ns
width	t _{KL1}	2.7 V ≤ EVDD0	≤ 5.5 V	tkcy1/2 - 10		tkcy1/2 - 50		tkcy1/2 - 50		ns
SIp setup time (to SCKp↑)	tsıĸ1	4.0 V ≤ EV _{DD0}	≤ 5.5 V	23		110		110		ns
Note 1		2.7 V ≤ EVDD0	≤ 5.5 V	33		110		110		ns
SIp hold time (from SCKp↑) Note 2	tksi1	2.7 V ≤ EVDD0	2.7 V ≤ EV _{DD0} ≤ 5.5 V			10		10		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 20 pF Note	4		10		10		10	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- Remark 1. This value is valid only when CSI00's peripheral I/O redirect function is not used.
- Remark 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 1)
- Remark 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00))

(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) (TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol	Conditions		HS (high-s main) mo	•	LS (low-speed mode	d main)	LV (low-vol main) mo	•	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	2.7 V ≤ EVDD0 ≤ 5.5 V	125		500		1000		ns
			2.4 V ≤ EVDD0 ≤ 5.5 V	250		500		1000		ns
			1.8 V ≤ EV _{DD0} ≤ 5.5 V	500		500		1000		ns
			1.7 V ≤ EVDD0 ≤ 5.5 V	1000		1000		1000		ns
			1.6 V ≤ EVDD0 ≤ 5.5 V	_		1000		1000		ns
SCKp high-/low-level	tĸнı,	4.0 V ≤ EV _{DD0}	≤ 5.5 V	tkcy1/2 - 12		tkcy1/2 - 50		tkcy1/2 - 50		ns
width	t _{KL1}	2.7 V ≤ EV _{DD0}	≤ 5.5 V	tkcy1/2 - 18		tkcy1/2 - 50		tkcy1/2 - 50		ns
		2.4 V ≤ EVDD0	≤ 5.5 V	tkcy1/2 - 38		tkcy1/2 - 50		tkcy1/2 - 50		ns
		1.8 V ≤ EVDD0	≤ 5.5 V	tkcy1/2 - 50		tkcy1/2 - 50		tkcy1/2 - 50		ns
		1.7 V ≤ EVDD0	≤ 5.5 V	tkcy1/2 - 100		tkcy1/2 - 100		tkcy1/2 - 100		ns
		1.6 V ≤ EVDD0	≤ 5.5 V	_		tkcy1/2 - 100		tkcy1/2 - 100		ns
SIp setup time	tsıĸ1	4.0 V ≤ EV _{DD0}	≤ 5.5 V	44		110		110		ns
(to SCKp↑) Note 1		2.7 V ≤ EV _{DD0}	≤ 5.5 V	44		110		110		ns
		2.4 V ≤ EVDD0	≤ 5.5 V	75		110		110		ns
		1.8 V ≤ EVDD0	≤ 5.5 V	110		110		110		ns
		1.7 V ≤ EVDD0	≤ 5.5 V	220		220		220		ns
		1.6 V ≤ EVDD0	≤ 5.5 V	_		220		220		ns
SIp hold time	tksıı	1.7 V ≤ EVDD0	≤ 5.5 V	19		19		19		ns
(from SCKp↑) Note 2		1.6 V ≤ EVDD0	≤ 5.5 V	_		19		19		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	1.7 V ≤ EV _{DD0} C = 30 pF Note			25		25		25	ns
1000		1.6 V ≤ EVDD0 C = 30 pF Note			_		25		25	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remark 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3, 5, 7)
- Remark 2. fMcK: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol	Cond	ditions	HS (high-spee	d main)	LS (low-speed mode	d main)	LV (low-voltag mode	e main)	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle	tkcy2	4.0 V ≤ EV _{DD0} ≤ 5.5 V	20 MHz < fmck	8/fмск		_		_		ns
time Note 5			fмcк ≤ 20 MHz	6/fмск		6/fмск		6/fмск		ns
		2.7 V ≤ EV _{DD0} ≤ 5.5 V	16 MHz < fmck	8/fмск		_		_		ns
			fмcк ≤ 16 MHz	6/fмск		6/fмск		6/fмск		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V		6/fмск and 500		6/fмск and 500		6/fмск and 500		ns
		1.8 V ≤ EVDD0 ≤ 5.5 V		6/fмск and 750		6/fмск and 750		6/fмск and 750		ns
	1.7 V ≤ EV _{DD0} ≤ 5.5 V			6/fмск and 1500		6/fмск and 1500		6/fмск and 1500		ns
		1.6 V ≤ EVDD0 ≤ 5.5 V		_		6/fмск and 1500		6/fмск and 1500		ns
SCKp high-/	tĸн2,	4.0 V ≤ EV _{DD0} ≤ 5.5 V		tkcy2/2 - 7		tkcy2/2 - 7		tkcy2/2 - 7		ns
low-level width	tKL2	2.7 V ≤ EV _{DD0} ≤ 5.5 V		tkcy2/2 - 8		tkcy2/2 - 8		tkcy2/2 - 8		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		tkcy2/2 - 18		tkcy2/2 - 18		tkcy2/2 - 18		ns
		1.7 V ≤ EV _{DD0} ≤ 5.5 V		tkcy2/2 - 66		tkcy2/2 - 66		tkcy2/2 - 66		ns
		1.6 V ≤ EV _{DD0} ≤ 5.5 V		_		tkcy2/2 - 66		tkcy2/2 - 66		ns
SIp setup time	tsık2	2.7 V ≤ EV _{DD0} ≤ 5.5 V		1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
(to SCKp↑) Note 1		1.8 V ≤ EV _{DD0} ≤ 5.5 V		1/fмск + 30		1/fмск + 30		1/fмск + 30		ns
		1.7 V ≤ EV _{DD0} ≤ 5.5 V		1/fмск + 40		1/fмск + 40		1/fмск + 40		ns
		1.6 V ≤ EV _{DD0} ≤ 5.5 V		_		1/fмск + 40		1/fмск + 40		ns
SIp hold time	tks12	1.8 V ≤ EV _{DD0} ≤ 5.5 V		1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
(from SCKp↑) Note 2		1.7 V ≤ EV _{DD0} ≤ 5.5 V		1/fмск + 250		1/fмск + 250		1/fмск + 250		ns
		1.6 V ≤ EV _{DD0} ≤ 5.5 V		_		1/fмск + 250		1/fмск + 250		ns
Delay time from SCKp↓ to	tkso2	C = 30 pF Note 4	2.7 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск + 44		2/fмск + 110		2/fмск + 110	ns
SOp output Note 3			2.4 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск + 75		2/fмск + 110		2/fмск + 110	ns
			1.8 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск + 100		2/fмск + 110		2/fмск + 110	ns
			1.7 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск + 220		2/fмск + 220		2/fмск + 220	ns
			1.6 V ≤ EV _{DD0} ≤ 5.5 V		_		2/fмск + 220		2/fмск + 220	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SOp output lines.
- **Note 5.** The maximum transfer rate when using the SNOOZE mode is 1 Mbps.
- Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3, 5, 7)

n: Channel number (mn = 00 to 03, 10, 11))

Remark 2. fmck: Serial array unit operation clock frequency

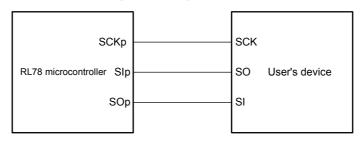
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

Parameter	Symbol		Conditions	HS (high-speed mode	d main)	LS (low-speed mode	main)	LV (low-voltage mode	e main)	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SSI00 setup time	tssik	DAPmn = 0	2.7 V ≤ EVDD0 ≤ 5.5 V	120		120		120		ns
			1.8 V ≤ EV _{DD0} ≤ 5.5 V	200		200		200		ns
			1.7 V ≤ EV _{DD0} ≤ 5.5 V	400		400		400		ns
			1.6 V ≤ EVDD0 ≤ 5.5 V	_		400		400		ns
		DAPmn = 1	2.7 V ≤ EV _{DD0} ≤ 5.5 V	1/fмск + 120		1/fмск + 120		1/fмск + 120		ns
			1.8 V ≤ EV _{DD0} ≤ 5.5 V	1/fмск + 200		1/fмск + 200		1/fмск + 200		ns
			1.7 V ≤ EV _{DD0} ≤ 5.5 V	1/fмск + 400		1/fмск + 400		1/fмск + 400		ns
			1.6 V ≤ EVDD0 ≤ 5.5 V	_		1/fмск + 400		1/fмск + 400		ns
SSI00 hold time	tkssi	DAPmn = 0	2.7 V ≤ EV _{DD0} ≤ 5.5 V	1/fмск + 120		1/fмск + 120		1/fмск + 120		ns
			1.8 V ≤ EV _{DD0} ≤ 5.5 V	1/fмск + 200		1/fмск + 200		1/fмск + 200		ns
			1.7 V ≤ EV _{DD0} ≤ 5.5 V	1/fмск + 400		1/fмск + 400		1/fмск + 400		ns
			1.6 V ≤ EV _{DD0} ≤ 5.5 V	_		1/fмск + 400		1/fмск + 400		ns
		DAPmn = 1	2.7 V ≤ EV _{DD0} ≤ 5.5 V	120		120		120		ns
			1.8 V ≤ EV _{DD0} ≤ 5.5 V	200		200		200		ns
			1.7 V ≤ EV _{DD0} ≤ 5.5 V	400		400		400		ns
			1.6 V ≤ EVDD0 ≤ 5.5 V	_		400		400		ns

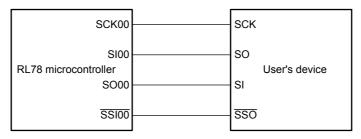
Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM number (g = 3, 5)

CSI mode connection diagram (during communication at same potential)



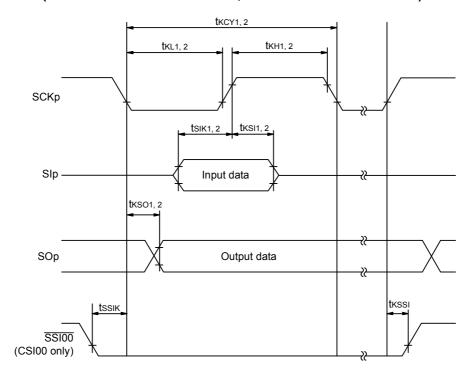
CSI mode connection diagram (during communication at same potential) (Slave Transmission of slave select input function (CSI00))



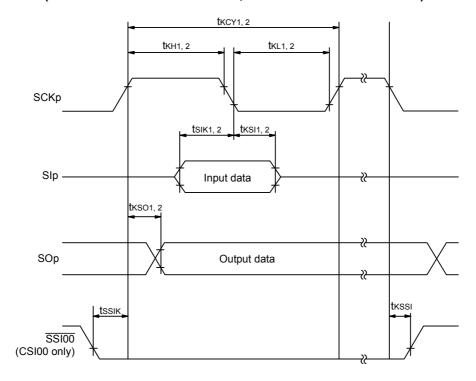
Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21)

Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)

CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21)

Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)

(5) During communication at same potential (simplified I²C mode)

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

(1/2)

Parameter	Symbol	Conditions		speed main) ode	-	peed main) ode		oltage main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fscL	$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$		1000 Note 1		400 Note 1		400 Note 1	kHz
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 3 \text{ k}\Omega$		400 Note 1		400 Note 1		400 Note 1	kHz
		$1.8 \text{ V} \leq \text{EV}_{\text{DDO}} < 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 5 \text{ k}\Omega$		300 Note 1		300 Note 1		300 Note 1	kHz
		$1.7~V \leq EV_{DD0} < 1.8~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$		250 Note 1		250 Note 1		250 Note 1	kHz
		$1.6~V \leq EV_{DD0} < 1.8~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$		_		250 Note 1		250 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	475		1150		1150		ns
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $C_{\text{b}} = 100 \text{ pF, R}_{\text{b}} = 3 \text{ k}\Omega$	1150		1150		1150		ns
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF, R}_{\text{b}} = 5 \text{ k}\Omega$	1550		1550		1550		ns
		$1.7~V \leq EV_{DD0} < 1.8~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	1850		1850		1850		ns
		$1.6~V \leq EV_{DD0} < 1.8~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	_		1850		1850		ns
Hold time when SCLr = "H"	thigh	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	475		1150		1150		ns
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $C_{\text{b}} = 100 \text{ pF, R}_{\text{b}} = 3 \text{ k}\Omega$	1150		1150		1150		ns
		$1.8~V \leq EV_{DD0} < 2.7~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	1550		1550		1550		ns
		$1.7~V \leq EV_{DD0} < 1.8~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	1850		1850		1850		ns
		$1.6~V \leq EV_{DD0} < 1.8~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	_		1850		1850		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

(5) During communication at same potential (simplified I²C mode)

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

(2/2)

Parameter	Symbol	Conditions	HS (high-speed main) mode		LS (low-speed mode	nain)	LV (low-voltage r mode	main)	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu: dat	$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	1/fmcK + 85 Note 2		1/fмск + 145 Note 2		1/fмск + 145 Note 2		ns
		1.8 V \leq EV _{DD0} \leq 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1/fmck + 145 Note 2		1/fmck + 145 Note 2		1/fmck + 145 Note 2		ns
		$1.8~V \leq EV_{DD0} < 2.7~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	1/fmck + 230 Note 2		1/fмск + 230 Note 2		1/fмск + 230 Note 2		ns
		$1.7~V \leq EV_{DD0} < 1.8~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	1/fmck + 290 Note 2		1/fmck + 290 Note 2		1/fmck + 290 Note 2		ns
		$1.6 \ V \leq EV_{DD0} < 1.8 \ V,$ $C_b = 100 \ pF, \ R_b = 5 \ k\Omega$	_		1/fmck + 290 Note 2		1/fmck + 290 Note 2		ns
Data hold time (transmission)	thd: dat	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	0	305	0	305	0	305	ns
		1.8 V \leq EV _{DD0} \leq 5.5 V, C _b = 100 pF, R _b = 3 kΩ	0	355	0	355	0	355	ns
		$1.8~V \leq EV_{DD0} < 2.7~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	0	405	0	405	0	405	ns
		$1.7 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	0	405	0	405	0	405	ns
		$1.6 \ V \le EV_{DD0} < 1.8 \ V,$ $C_b = 100 \ pF, \ R_b = 5 \ k\Omega$	_		0	405	0	405	ns

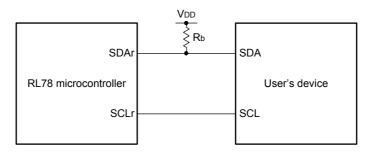
Note 1. The value must also be equal to or less than fmck/4.

Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

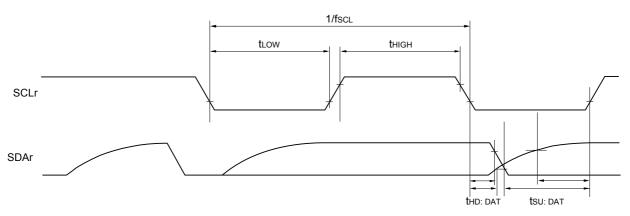
Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



 $\textbf{Remark 1.} \ \ R_b[\Omega]: \ Communication \ line \ (SDAr) \ pull-up \ resistance, \ C_b[F]: \ Communication \ line \ (SDAr, SCLr) \ load \ capacitance$

Remark 2. r: IIC number (r = 00, 01, 10, 11, 20, 21), g: PIM number (g = 0, 1, 3, 5, 7), h: POM number (h = 0, 1, 3, 5, 7)

Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),

n: Channel number (n = 0 to 3), mn = 00 to 03, 10, 11)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(TA = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

Parameter	Symbol		Conditions	٠ ٠	-speed main) node	,	speed main) node	,	voltage main) mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		reception	$4.0 \text{ V} \le \text{EV}_{DD0} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V}$		f _{MCK} /6 Note 1		f _{MCK} /6 Note 1		f _{MCK} /6 Note 1	bps
			Theoretical value of the maximum transfer rate fmck = fclk Note 4		5.3		1.3		0.6	Mbps
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$		f _{MCK} /6 Note 1		f _{MCK} /6 Note 1		f _{MCK} /6 Note 1	bps
			Theoretical value of the maximum transfer rate folk Note 4		5.3		1.3		0.6	Mbps
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$		fмск/6 Notes 1, 2, 3		fмск/6 Notes 1, 2		fмск/6 Notes 1, 2	bps
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 4		5.3		1.3		0.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

Note 2. Use it with $EVDD0 \ge V_b$.

Note 3. The following conditions are required for low voltage interface when EVDDO < VDD.

 $2.4~V \leq EV_{DD0} < 2.7~V;$ MAX. 2.6~Mbps

 $1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.4 \text{ V}$: MAX. 1.3 Mbps

Note 4. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLk) are:

HS (high-speed main) mode: 32 MHz (2.7 V \leq VDD \leq 5.5 V)

16 MHz (2.4 V \leq VDD \leq 5.5 V)

LS (low-speed main) mode: 8 MHz (1.8 V \leq VDD \leq 5.5 V) LV (low-voltage main) mode: 4 MHz (1.6 V \leq VDD \leq 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Remark 1. Vb [V]: Communication line voltage

Remark 2. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1, 5, 7)

Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10, 11)

Remark 4. UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(TA = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

(2/2)

Parameter	Symbol		Conditions	` •	-speed main) node	,	speed main) node	,	roltage main) node	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		transmission	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{Vb} \le 4.0 \text{ V}$		Note 1		Note 1		Note 1	bps
			Theoretical value of the maximum transfer rate $C_b = 50$ pF, $R_b = 1.4$ k Ω , $V_b = 2.7$ V		2.8 Note 2		2.8 Note 2		2.8 Note 2	Mbps
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V}$		Note 3		Note 3		Note 3	bps
			Theoretical value of the maximum transfer rate $C_b = 50$ pF, $R_b = 2.7$ k Ω , $V_b = 2.3$ V		1.2 Note 4		1.2 Note 4		1.2 Note 4	Mbps
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$		Notes 5, 6		Notes 5, 6		Notes 5, 6	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 k Ω , V_b = 1.6 V		0.43 Note 7		0.43 Note 7		0.43 Note 7	Mbps

Note 1. The smaller maximum transfer rate derived by using fMck/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when $4.0 \text{ V} \le \text{EV}_{DD0} \le 5.5 \text{ V}$ and $2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V}$

$$\begin{array}{l} \text{Maximum transfer rate} = \frac{1}{ \left\{ -C_b \times R_b \times \ln \left(1 - \frac{2.2}{V_b} \right) \right\} \times 3} \\ \\ \text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \left\{ -C_b \times R_b \times \ln \left(1 - \frac{2.2}{V_b} \right) \right\}}{\left(\frac{1}{\text{Transfer rate}} \right) \times \text{Number of transferred bits}} \\ \end{array}$$

- Note 2. This value as an example is calculated when the conditions described in the "Conditions" column are met.

 Refer to **Note 1** above to calculate the maximum transfer rate under conditions of the customer.
- **Note 3.** The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

$$\begin{array}{c} 1 \\ \hline \\ \{-C_b \times R_b \times \ln{(1-\frac{2.0}{V_b}\)}\} \times 3 \end{array} \\ \hline \\ Baud \ rate \ error \ (theoretical \ value) = \\ \hline \\ \left(\begin{array}{c} \frac{1}{Transfer \ rate} \times 2 \end{array} - \left\{ -C_b \times R_b \times \ln{(1-\frac{2.0}{V_b}\)} \right\} \\ \hline \\ \left(\begin{array}{c} \frac{1}{Transfer \ rate} \end{array} \right) \times \text{Number of transferred bits} \end{array}$$

Expression for calculating the transfer rate when 2.7 V \leq EVDD0 < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

- Note 4. This value as an example is calculated when the conditions described in the "Conditions" column are met.

 Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.
- Note 5. Use it with $EV_{DD0} \ge V_b$.



^{*} This value is the theoretical value of the relative difference between the transmission and reception sides.

^{*} This value is the theoretical value of the relative difference between the transmission and reception sides.

Note 6. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate

Expression for calculating the transfer rate when 1.8 V \leq EVDD0 < 3.3 V and 1.6 V \leq Vb \leq 2.0 V

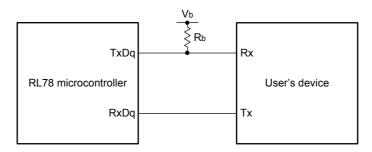
$$\frac{1}{ \left\{ -C_b \times R_b \times \ln \left(1 - \frac{1.5}{V_b} \right) \right\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

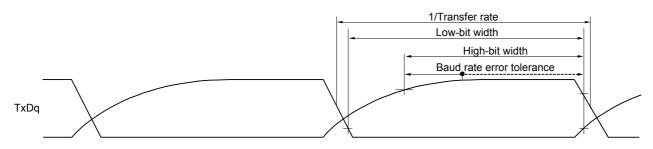
- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **Note 7.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 6** above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

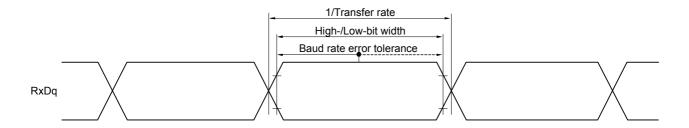
(Remarks are listed on the next page.)

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





- **Remark 1.** Rb[Ω]: Communication line (TxDq) pull-up resistance,
 - Сь[F]: Communication line (TxDq) load capacitance, Vь[V]: Communication line voltage
- **Remark 2.** q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1, 5, 7)
- $\textbf{Remark 3.} \ \, \textbf{fmck: Serial array unit operation clock frequency}$
 - (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 - m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))
- Remark 4. UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(TA = -40 to +85°C, 2.7 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

Parameter	Symbol		Conditions	HS (high-s main) mo		LS (low-speed mode	,	LV (low-vo main) mo	•	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 2/fcLK	$ \begin{aligned} 4.0 & \ V \le EV_{DD0} \le 5.5 \ V, \\ 2.7 & \ V \le V_b \le 4.0 \ V, \\ C_b = 20 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	200		1150		1150		ns
			$\begin{split} 2.7 \ V &\leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V &\leq V_{b} \leq 2.7 \ V, \\ C_{b} &= 20 \ pF, \ R_{b} = 2.7 \ k \Omega \end{split}$	300		1150		1150		ns
SCKp high-level width	tкнı	$4.0 \text{ V} \le \text{EV}_{DDG}$ $2.7 \text{ V} \le \text{V}_{b} \le 2$ $C_{b} = 20 \text{ pF, Rb}$	4.0 V,	tксү1/2 - 50		tксү1/2 - 50		tксү1/2 - 50		ns
		$2.7 \text{ V} \le \text{EV}_{DD0}$ $2.3 \text{ V} \le \text{V}_{b} \le 2$ $C_{b} = 20 \text{ pF, Rb}$	2.7 V,	tксү1/2 - 120		tkcy1/2 - 120		tkcy1/2 - 120		ns
SCKp low-level width	tKL1	$4.0 \text{ V} \leq \text{EV}_{\text{DDO}}$ $2.7 \text{ V} \leq \text{V}_{\text{b}} \leq$ $C_{\text{b}} = 20 \text{ pF, Rb}$	4.0 V,	tксү1/2 - 7		tксү1/2 - 50		tксү1/2 - 50		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}}$ $2.3 \text{ V} \leq \text{V}_{\text{b}} \leq$ $C_{\text{b}} = 20 \text{ pF, Rb}$	2.7 V,	tксү1/2 - 10		tксү1/2 - 50		tксү1/2 - 50		ns
SIp setup time (to SCKp↑) Note 1	tsıĸ1	$4.0 \text{ V} \leq \text{EV}_{\text{DDO}}$ $2.7 \text{ V} \leq \text{V}_{\text{b}} \leq$ $C_{\text{b}} = 20 \text{ pF, Rb}$	4.0 V,	58		479		479		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}}$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le \text{C}_{\text{b}} = 20 \text{ pF, Rb}$	2.7 V,	121		479		479		ns
SIp hold time (from SCKp↑) Note 1	tksi1	$4.0 \text{ V} \leq \text{EV}_{\text{DDO}}$ $2.7 \text{ V} \leq \text{V}_{\text{b}} \leq$ $C_{\text{b}} = 20 \text{ pF, Rb}$	4.0 V,	10		10		10		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DDO}}$ $2.3 \text{ V} \leq \text{V}_{\text{b}} \leq$ $C_{\text{b}} = 20 \text{ pF, Rb}$	2.7 V,	10		10		10		ns
Delay time from SCKp↓ to SOp out- put Note 1	tkso1	$4.0 \text{ V} \leq \text{EV}_{\text{DDO}}$ $2.7 \text{ V} \leq \text{V}_{\text{b}} \leq$ $C_{\text{b}} = 20 \text{ pF, Rb}$	4.0 V,		60		60		60	ns
		$2.7 \text{ V} \leq \text{EVDD0}$ $2.3 \text{ V} \leq \text{V}_b \leq$ $C_b = 20 \text{ pF, Rb}$	2.7 V,		130		130		130	ns

(Notes, Caution, and Remarks are listed on the next page.)

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(TA = -40 to +85°C, 2.7 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

(2/2)

Parameter	Symbol	Conditions		peed main) ode	,	peed main) ode	,	ltage main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) ^{Note 2}	tsıĸ1	$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 20 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	23		110		110		ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 20 \text{ pF}, \text{R}_{\text{b}} = 2.7 \text{ k}\Omega $	33		110		110		ns
SIp hold time (from SCKp↓) ^{Note 2}	tksı1	$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 20 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	10		10		10		ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 20 \text{ pF}, \text{R}_{\text{b}} = 2.7 \text{ k}\Omega $	10		10		10		ns
Delay time from SCKp↑ to SOp output Note 2	tkso1	$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 20 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $		10		10		10	ns
		$ \begin{aligned} 2.7 & \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 & \ V \leq V_b \leq 2.7 \ V, \\ C_b = 20 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $		10		10		10	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
- Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

- Remark 1. $Rb[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 3, 5)
- Remark 3. fmck: Serial array unit operation clock frequency

 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number

 (mn = 00))
- Remark 4. This value is valid only when CSI00's peripheral I/O redirect function is not used.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

(TA = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

(1/3)

Parameter	Symbol	Conditions		HS (high-s main) mo		LS (low-speed mode	,	LV (low-vo main) mo	•	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$ \begin{aligned} 4.0 \ V &\leq EV_{DDO} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	300		1150		1150		ns
			$ \begin{aligned} 2.7 & \text{ V} \leq \text{EV}_{\text{DDO}} < 4.0 \text{ V}, \\ 2.3 & \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{C}_{\text{b}} &= 30 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega \end{aligned} $	500		1150		1150		ns
			$\begin{split} 1.8 \ V & \leq EV_{DDO} < 3.3 \ V, \\ 1.6 \ V & \leq V_b \leq 2.0 \ V \ \text{Note}, \\ C_b & = 30 \ \text{pF}, \ R_b = 5.5 \ k\Omega \end{split}$	1150		1150		1150		ns
SCKp high-level width	tкнı	$4.0 \text{ V} \le \text{EVDD0}$ $2.7 \text{ V} \le \text{Vb} \le 4$ $C_b = 30 \text{ pF, Rb}$	0 V,	tксү1/2 - 75		tксү1/2 - 75		tксү1/2 - 75		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}}$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2$ $C_{\text{b}} = 30 \text{ pF}, \text{Rb}$	7 V,	tксү1/2 - 170		tксү1/2 - 170		tксү1/2 - 170		ns
		1.8 V ≤ EVDD0 1.6 V ≤ Vb ≤ 2 Cb = 30 pF, Rb	0 V Note,	tксү1/2 - 458		tксү1/2 - 458		tkcy1/2 - 458		ns
SCKp low-level width	tKL1	$4.0 \text{ V} \le \text{EVDD0}$ $2.7 \text{ V} \le \text{Vb} \le 4$ $C_b = 30 \text{ pF}, \text{ Rb}$	0 V,	tксү1/2 - 12		tксү1/2 - 50		tксү1/2 - 50		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}}$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2$ $C_{\text{b}} = 30 \text{ pF}, \text{ Rb}$	7 V,	tkcy1/2 - 18		tксү1/2 - 50		tксү1/2 - 50		ns
		1.8 V ≤ EVDD0 1.6 V ≤ Vb ≤ 2 Cb = 30 pF, Rb	0 V Note,	tkcy1/2 - 50		tксү1/2 - 50		tксү1/2 - 50		ns

Note Use it with $EVDD0 \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

(TA = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

(2/3)

Parameter	Symbol	Conditions	, ,	speed main) ode	,	peed main) ode	,	oltage main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	tsıĸ1	$ \begin{aligned} 4.0 \ & V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ & V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	81		479		479		ns
		$\label{eq:section} \begin{split} 2.7 \ & V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ & V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	177		479		479		ns
		$\begin{array}{l} 1.8 \; \text{V} \leq \text{EV}_{\text{DD0}} < 3.3 \; \text{V}, \\ 1.6 \; \text{V} \leq \text{V}_{\text{b}} \leq 2.0 \; \text{V} \; \text{Note 2}, \\ \text{Cb} = 30 \; \text{pF}, \; \text{Rb} = 5.5 \; \text{k}\Omega \end{array}$	479		479		479		ns
SIp hold time (from SCKp↑) Note 1	tksii	$ \begin{aligned} 4.0 & \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ \text{C}_{\text{b}} & = 30 \text{ pF}, \text{ R}_{\text{b}} = 1.4 \text{ k}\Omega \end{aligned} $	19		19		19		ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{Cb} = 30 \text{ pF}, \text{Rb} = 2.7 \text{ k}\Omega $	19		19		19		ns
		$\begin{split} 1.8 \ V &\leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V \ ^{Note \ 2}, \\ C_b &= 30 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$	19		19		19		ns
Delay time from SCKp↓ to SOp output Note 1	tkso1	$ \begin{aligned} 4.0 & \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ \text{Cb} & = 30 \text{ pF}, \text{ Rb} = 1.4 \text{ k}\Omega \end{aligned} $		100		100		100	ns
		$ \begin{aligned} 2.7 & \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 & \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{Cb} & = 30 \text{ pF}, \text{ Rb} = 2.7 \text{ k}\Omega \end{aligned} $		195		195		195	ns
		$\begin{split} &1.8 \; \text{V} \leq \text{EV}_{\text{DD0}} < 3.3 \; \text{V}, \\ &1.6 \; \text{V} \leq \text{V}_{\text{b}} \leq 2.0 \; \text{V} \; \text{Note 2}, \\ &\text{C}_{\text{b}} = 30 \; \text{pF}, \; \text{R}_{\text{b}} = 5.5 \; \text{k} \Omega \end{split}$		483		483		483	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

Note 2. Use it with $EVDD0 \ge V_b$.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

(TA = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

(3/3)

Parameter	Symbol	Conditions	, ,	peed main) ode		peed main) ode	,	Itage main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) Note 1	tsıĸ1	$ \begin{aligned} 4.0 \ & V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ & V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	44		110		110		ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{Cb} = 30 \text{ pF, Rb} = 2.7 \text{ k}\Omega $	44		110		110		ns
		$\begin{array}{l} 1.8 \; \text{V} \leq \text{EV}_{\text{DD0}} < 3.3 \; \text{V}, \\ 1.6 \; \text{V} \leq \text{V}_{\text{b}} \leq 2.0 \; \text{V} \; \text{Note 2}, \\ \text{C}_{\text{b}} = 30 \; \text{pF}, \; \text{R}_{\text{b}} = 5.5 \; \text{k}\Omega \end{array}$	110		110		110		ns
SIp hold time (from SCKp↓) Note 1	tksi1	$ \begin{aligned} 4.0 & \ V \le EV_{DD0} \le 5.5 \ V, \\ 2.7 & \ V \le V_b \le 4.0 \ V, \\ C_b & = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	19		19		19		ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{Cb} = 30 \text{ pF, Rb} = 2.7 \text{ k}\Omega $	19		19		19		ns
		$\begin{aligned} &1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} \text{ Note 2}, \\ &C_{\text{b}} = 30 \text{ pF}, \text{ Rb} = 5.5 \text{ k}\Omega \end{aligned}$	19		19		19		ns
Delay time from SCKp↑ to SOp output Note 1	tkso1	$ \begin{aligned} 4.0 & \ V \le EV_{DD0} \le 5.5 \ V, \\ 2.7 & \ V \le V_b \le 4.0 \ V, \\ C_b & = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $		25		25		25	ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 30 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega $		25		25		25	ns
		$\begin{split} &1.8 \; \text{V} \leq \text{EV}_{\text{DD0}} < 3.3 \; \text{V}, \\ &1.6 \; \text{V} \leq \text{V}_{\text{b}} \leq 2.0 \; \text{V} \; \text{Note 2}, \\ &\text{Cb} = 30 \; \text{pF}, \; \text{Rb} = 5.5 \; \text{k}\Omega \end{split}$		25		25		25	ns

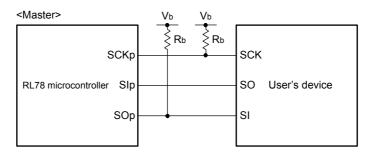
Note 1. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

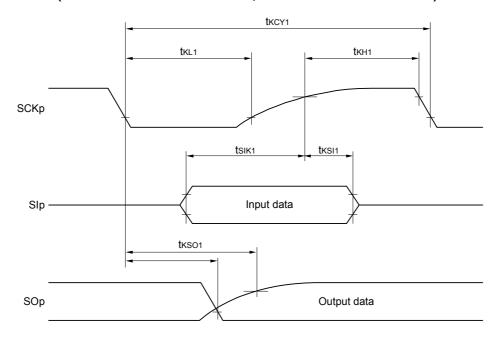
Note 2. Use it with $EV_{DD0} \ge V_b$.

CSI mode connection diagram (during communication at different potential)

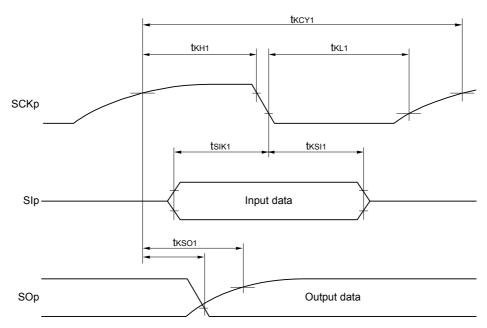


- Remark 1. $Rb[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** p: CSI number (p = 00, 01, 10, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3, 5, 7)
- Remark 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00))
- Remark 4. CSI01 of 48-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 01, 10, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3, 5, 7)

Remark 2. CSI01 of 48-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

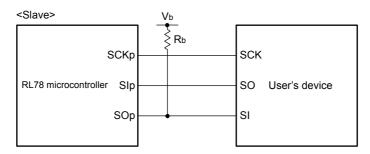
(TA = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

Parameter	Symbol	Cor	nditions	, ,	h-speed mode	,	/-speed mode	LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy2	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$	24 MHz < fmck	14/fмск		_		_		ns
Note 1		$2.7~V \leq V_b \leq 4.0~V$	20 MHz < fмcк ≤ 24 MHz	12/fмск		_		_		ns
			8 MHz < fмcк ≤ 20 MHz	10/fмск		_		_		ns
			4 MHz < fмcк ≤ 8 MHz	8/fмск		16/fмск		_		ns
			fмcк ≤ 4 MHz	6/fмск		10/fмск		10/fмск		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$	24 MHz < fmck	20/fмск		_		_		ns
		$2.3~V \leq V_b \leq 2.7~V$	20 MHz < fмcк ≤ 24 MHz	16/fмск		_		_		ns
			16 MHz < fмcк ≤ 20 MHz	14/fмск		_		_		ns
			8 MHz < fмcк ≤ 16 MHz	12/fмск		_		_		ns
			4 MHz < fмcк ≤ 8 MHz	8/fмск		16/fмск		_		ns
			fмcк ≤ 4 MHz	6/fмск		10/fмск		10/fмск		ns
		1.8 V ≤ EVDD0 < 3.3 V,	24 MHz < fmck	48/fмск		_		_		ns
		1.6 V ≤ V _b ≤ 2.0 V Note 2	20 MHz < fмcк ≤ 24 MHz	36/fмск		_		_		ns
		Note 2	16 MHz < fмcк ≤ 20 MHz	32/fмск		_		_		ns
			8 MHz < fмcк ≤ 16 MHz	26/fмск		_		_		ns
			4 MHz < fмcк ≤ 8 MHz	16/fмск		16/fмск		_		ns
			fмck ≤ 4 MHz	10/fмск		10/fмск		10/fмск		ns
SCKp high-/ low-level width	tĸH2, tĸL2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2	2.7 V ≤ V _b ≤ 4.0 V	tксү2/2 - 12		tксү2/2 - 50		tксү2/2 - 50		ns
		2.7 V ≤ EVDD0 < 4.0 V, 2	$2.3~V \leq V_b \leq 2.7~V$	tkcy2/2 - 18		tkcy2/2 - 50		tксү2/2 - 50		ns
		1.8 V ≤ EVDD0 < 3.3 V,	$1.6~V \le V_b \le 2.0~V~\text{Note 2}$	tkcy2/2 - 50		tkcy2/2 - 50		tксү2/2 - 50		ns
SIp setup time (to SCKp↑) Note 3	tsık2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2	$2.7 \text{ V} \le \text{Vb} \le 4.0 \text{ V}$	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		2.7 V ≤ EVDD0 ≤ 4.0 V, 2	$2.3~V \leq V_b \leq 2.7~V$	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		1.8 V ≤ EVDD0 ≤ 3.3 V,	$1.6 \text{ V} \leq \text{V}_b \leq 2.0 \text{ V Note 2}$	1/fмск + 30		1/fмск + 30		1/fмск + 30		ns
SIp hold time (from SCKp↑) Note 4	tksi2			1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
Delay time from SCKp↓ to SOp	tkso2	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}, \Omega$ $C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$			2/fмск + 120		2/fмск + 573		2/fмск + 573	ns
output Note 5		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \Omega$ C _b = 30 pF, R _b = 2.7 k Ω			2/fмск + 214		2/fмск + 573		2/fмск + 573	ns
		1.8 V ≤ EVDD0 < 3.3 V, C _b = 30 pF, Rv = 5.5 kΩ	$1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V}^{\text{Note 2}},$		2/fмск + 573		2/fмcк + 573		2/fмск + 573	ns

(Notes, Cautions, and Remarks are listed on the next page.)

- Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
- Note 2. Use it with $EVDD0 \ge V_b$.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and SCKp pin, and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

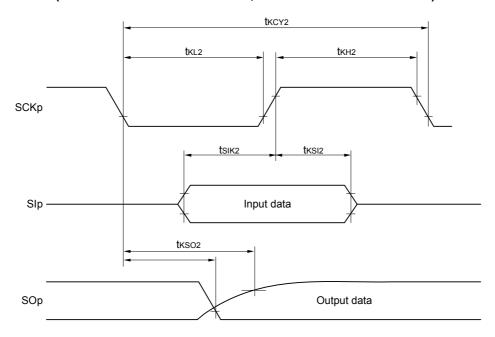
CSI mode connection diagram (during communication at different potential)



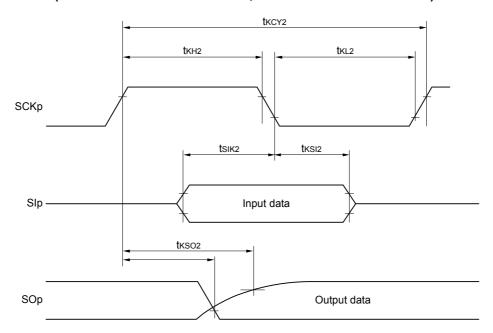
- **Remark 1.** Rb[Ω]: Communication line (SOp) pull-up resistance, Cb[F]: Communication line (SOp) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** p: CSI number (p = 00, 01, 10, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3, 5, 7)
- Remark 3. fMcK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01, 02, 10))
- Remark 4. CSI01 of 48-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

Also, communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.

CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 01, 10, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3, 5, 7)

Remark 2. CSI01 of 48-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

Also, communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

(TA = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

Parameter	Symbol	Conditions	, ,	speed main) node		speed main) node	LV (low-voltage main) mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	1
SCLr clock frequency	fscL	$ \begin{aligned} 4.0 & \ V \le EV_{DD0} \le 5.5 \ V, \\ 2.7 & \ V \le V_b \le 4.0 \ V, \\ C_b & = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $		1000 Note 1		300 Note 1		300 Note 1	kHz
		$\label{eq:substitute} \begin{split} 2.7 \ & V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ & V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$		1000 Note 1		300 Note 1		300 Note 1	kHz
		$ \begin{aligned} &4.0 \; \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \; \text{V}, \\ &2.7 \; \text{V} \leq \text{V}_{\text{b}} \leq 4.0 \; \text{V}, \\ &\text{C}_{\text{b}} = 100 \; \text{pF}, \; \text{R}_{\text{b}} = 2.8 \; \text{k} \Omega \end{aligned} $		400 Note 1		300 Note 1		300 Note 1	kHz
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 100 \text{ pF}, \text{R}_{\text{b}} = 2.7 \text{ k}\Omega $		400 Note 1		300 Note 1		300 Note 1	kHz
		$\begin{split} &1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} \text{ Note 2}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ Rb} = 5.5 \text{ k}\Omega \end{split}$		300 Note 1		300 Note 1		300 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$ \begin{aligned} 4.0 & \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} & = 50 \text{ pF}, \text{ Rb} = 2.7 \text{ k}\Omega \end{aligned} $	475		1550		1550		ns
		$ \begin{aligned} &2.7 \; \text{V} \leq \text{EV}_{\text{DD0}} < 4.0 \; \text{V}, \\ &2.3 \; \text{V} \leq \text{V}_{\text{b}} \leq 2.7 \; \text{V}, \\ &C_{\text{b}} = 50 \; \text{pF}, \; R_{\text{b}} = 2.7 \; \text{k}\Omega \end{aligned} $	475		1550		1550		ns
		$ \begin{aligned} &4.0 \; \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \; \text{V}, \\ &2.7 \; \text{V} \leq \text{V}_{\text{b}} \leq 4.0 \; \text{V}, \\ &\text{C}_{\text{b}} = 100 \; \text{pF}, \; \text{R}_{\text{b}} = 2.8 \; \text{k} \Omega \end{aligned} $	1150		1550		1550		ns
		$ 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega $	1150		1550		1550		ns
		$\begin{split} 1.8 \ V &\leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V \ ^{Note \ 2}, \\ C_b &= 100 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$	1550		1550		1550		ns
Hold time when SCLr = "H"	tніgн	$\begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$	245		610		610		ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 50 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega $	200		610		610		ns
		$ 4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ \text{C}_{\text{b}} = 100 \text{ pF}, \text{R}_{\text{b}} = 2.8 \text{ k}\Omega $	675		610		610		ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 100 \text{ pF}, \text{R}_{\text{b}} = 2.7 \text{ k}\Omega $	600		610		610		ns
		$\begin{aligned} &1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} \text{ Note 2}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ Rb} = 5.5 \text{ k}\Omega \end{aligned}$	610		610		610		ns

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

(TA = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

(2/2)

Parameter	Symbol	Conditions	HS (high-speed r	main)	LS (low-speed m	nain)	LV (low-voltage r mode	main)	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $	1/fmck + 135 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		ns
		$ \begin{aligned} &2.7 \text{ V} \leq \text{EV}_{\text{DDO}} < 4.0 \text{ V}, \\ &2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ &C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega \end{aligned} $	1/fmck + 135 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		ns
		$ \begin{aligned} &4.0 \text{ V} \leq \text{EV}_{\text{DDO}} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned} $	1/fmck + 190 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		ns
		$ \begin{aligned} 2.7 & \ V \leq EV_{DDO} < 4.0 \ V, \\ 2.3 & \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $	1/fmck + 190 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		ns
		$ \begin{aligned} &1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} &\text{Note 2}, \\ &C_{\text{b}} = 100 \text{ pF}, &R_{\text{b}} = 5.5 \text{ k}\Omega \end{aligned} $	1/fmck + 190 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		ns
Data hold time (transmission)	thd:dat	$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $	0	305	0	305	0	305	ns
		$ \begin{aligned} &2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ &2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ &C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega \end{aligned} $	0	305	0	305	0	305	ns
		$ \begin{aligned} &4.0 \; \text{V} \leq \text{EV} \text{DDO} \leq 5.5 \; \text{V}, \\ &2.7 \; \text{V} \leq \text{V}_{\text{b}} \leq 4.0 \; \text{V}, \\ &\text{C}_{\text{b}} = 100 \; \text{pF}, \; \text{R}_{\text{b}} = 2.8 \; \text{k} \Omega \end{aligned} $	0	355	0	355	0	355	ns
		$ \begin{aligned} &2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ &2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ Rb} = 2.7 \text{ k}\Omega \end{aligned} $	0	355	0	355	0	355	ns
		$\begin{split} &1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} \stackrel{\text{Note 2}}{\sim}, \\ &C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 5.5 \text{ k}\Omega \end{split}$	0	405	0	405	0	405	ns

Note 1. The value must also be equal to or less than fMCK/4.

Caution Select the TTL input buffer and the N-ch open drain output (Vod tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics

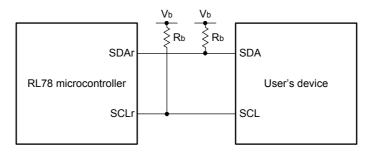
with TTL input buffer selected.

(Remarks are listed on the next page.)

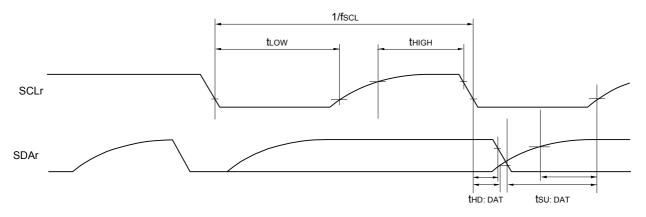
Note 2. Use it with $EVDD0 \ge V_b$.

Note 3. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Remark 1. $Rb[\Omega]$: Communication line (SDAr, SCLr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance, Vb[V]: Communication line voltage

Remark 2. r: IIC number (r = 00, 01, 10, 11, 20), g: PIM, POM number (g = 0, 1, 3, 5, 7)

Remark 3. fmck: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),
n: Channel number (n = 0, 2), mn = 00, 01, 02, 10)

2.5.2 Serial interface IICA

(1) I²C standard mode

(TA = -40 to +85°C, 1.6 V \leq EVDD0 $\,\leq$ VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol	C	Conditions	` •	peed main) ode	, ,	peed main) ode	LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock	fscL	Standard mode:	2.7 V ≤ EVDD0 ≤ 5.5 V	0	100	0	100	0	100	kHz
frequency		fclk ≥ 1 MHz	1.8 V ≤ EVDD0 ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.7 V ≤ EVDD0 ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.6 V ≤ EVDD0 ≤ 5.5 V	-	_	0	100	0	100	kHz
Setup time of	tsu: sta	2.7 V ≤ EVDD0 ≤	5.5 V	4.7		4.7		4.7		μs
restart condition		1.8 V ≤ EVDD0 ≤	5.5 V	4.7		4.7		4.7		μs
		1.7 V ≤ EVDD0 ≤	5.5 V	4.7		4.7		4.7		μs
		1.6 V ≤ EVDD0 ≤	5.5 V	-	_	4.7		4.7		μs
Hold time Note 1	thd: Sta	2.7 V ≤ EVDD0 ≤	5.5 V	4.0		4.0		4.0		μs
		1.8 V ≤ EVDD0 ≤	5.5 V	4.0		4.0		4.0		μs
		1.7 V ≤ EVDD0 ≤	5.5 V	4.0		4.0		4.0		μs
		1.6 V ≤ EVDD0 ≤	5.5 V	-	_	4.0		4.0		μs
Hold time when	tLOW	2.7 V ≤ EVDD0 ≤	5.5 V	4.7		4.7		4.7		μs
SCLA0 = "L"		1.8 V ≤ EVDD0 ≤	5.5 V	4.7		4.7		4.7		μs
		1.7 V ≤ EVDD0 ≤	5.5 V	4.7		4.7		4.7		μs
		1.6 V ≤ EVDD0 ≤	5.5 V	-	_	4.7		4.7		μs
Hold time when	tніgн	2.7 V ≤ EVDD0 ≤	5.5 V	4.0		4.0		4.0		μs
SCLA0 = "H"		1.8 V ≤ EVDD0 ≤	5.5 V	4.0		4.0		4.0		μs
		1.7 V ≤ EVDD0 ≤	5.5 V	4.0		4.0		4.0		μs
		1.6 V ≤ EVDD0 ≤	5.5 V	-	_	4.0		4.0		μs

 $(\textbf{Notes},\,\textbf{Caution},\, \text{and}\,\, \textbf{Remark}$ are listed on the next page.)

(1) I²C standard mode

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

(2/2)

Parameter	Symbol	Conditions	, ,	peed main) ode	, ,	peed main) ode	,	ltage main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu: DAT	2.7 V ≤ EVDD0 ≤ 5.5 V	250		250		250		ns
		1.8 V ≤ EVDD0 ≤ 5.5 V	250		250		250		ns
		1.7 V ≤ EVDD0 ≤ 5.5 V	250		250		250		ns
		1.6 V ≤ EVDD0 ≤ 5.5 V	-	_	250		250		ns
Data hold time (transmission)	thd: dat	2.7 V ≤ EVDD0 ≤ 5.5 V	0	3.45	0	3.45	0	3.45	μs
Note 2		1.8 V ≤ EVDD0 ≤ 5.5 V	0	3.45	0	3.45	0	3.45	μs
		1.7 V ≤ EVDD0 ≤ 5.5 V	0	3.45	0	3.45	0	3.45	μs
		1.6 V ≤ EVDD0 ≤ 5.5 V	-	_	0	3.45	0	3.45	μs
Setup time of stop condition	tsu: sto	2.7 V ≤ EVDD0 ≤ 5.5 V	4.0		4.0		4.0		μs
		1.8 V ≤ EVDD0 ≤ 5.5 V	4.0		4.0		4.0		μs
		1.7 V ≤ EVDD0 ≤ 5.5 V	4.0		4.0		4.0		μs
		1.6 V ≤ EVDD0 ≤ 5.5 V	-	_	4.0		4.0		μs
Bus-free time	tBUF	2.7 V ≤ EVDD0 ≤ 5.5 V	4.7		4.7		4.7		μs
		1.8 V ≤ EVDD0 ≤ 5.5 V	4.7		4.7		4.7		μs
		1.7 V ≤ EVDD0 ≤ 5.5 V	4.7		4.7		4.7		μs
		1.6 V ≤ EVDD0 ≤ 5.5 V	-	_	4.7		4.7		μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

Note 2. The maximum value (MAX.) of thD: DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: C_b = 400 pF, R_b = 2.7 $k\Omega$

(2) I2C fast mode

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

Parameter	Symbol	Conditions		` `	h-speed mode	d LS (low-speed main) mode		`	-voltage mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode:	2.7 V ≤ EVDD0 ≤ 5.5 V	0	400	0	400	0	400	kHz
		fc∟k ≥ 3.5 MHz	1.8 V ≤ EVDD0 ≤ 5.5 V	0	400	0	400	0	400	kHz
Setup time of restart condi-	tsu: sta	2.7 V ≤ EV _{DD0} ≤	5.5 V	0.6		0.6		0.6		μs
tion		1.8 V ≤ EV _{DD0} ≤	5.5 V	0.6		0.6		0.6		μs
Hold time Note 1	thd: STA	2.7 V ≤ EV _{DD0} ≤	5.5 V	0.6		0.6		0.6		μs
		1.8 V ≤ EV _{DD0} ≤	5.5 V	0.6		0.6		0.6		μs
Hold time when SCLA0 = "L"	tLOW	2.7 V ≤ EV _{DD0} ≤	5.5 V	1.3		1.3		1.3		μs
		1.8 V ≤ EV _{DD0} ≤	5.5 V	1.3		1.3		1.3		μs
Hold time when SCLA0 = "H"	thigh	2.7 V ≤ EVDD0 ≤	5.5 V	0.6		0.6		0.6		μs
		1.8 V ≤ EV _{DD0} ≤	5.5 V	0.6		0.6		0.6		μs
Data setup time (reception)	tsu: dat	2.7 V ≤ EVDD0 ≤	5.5 V	100		100		100		ns
		1.8 V ≤ EV _{DD0} ≤	5.5 V	100		100		100		ns
Data hold time (transmission)	thd: dat	2.7 V ≤ EV _{DD0} ≤	5.5 V	0	0.9	0	0.9	0	0.9	μs
Note 2		1.8 V ≤ EV _{DD0} ≤	5.5 V	0	0.9	0	0.9	0	0.9	μs
Setup time of stop condition	tsu: sto	2.7 V ≤ EVDD0 ≤	5.5 V	0.6		0.6		0.6		μs
		1.8 V ≤ EV _{DD0} ≤	5.5 V	0.6		0.6		0.6		μs
Bus-free time	tbuf	2.7 V ≤ EV _{DD0} ≤	5.5 V	1.3		1.3		1.3		μs
		1.8 V ≤ EV _{DD0} ≤	5.5 V	1.3		1.3		1.3		μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

Note 2. The maximum value (MAX.) of thd: DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: C_b = 320 pF, R_b = 1.1 k Ω

(3) I²C fast mode plus

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

Parameter	Symbol	Conditions			, • .		LS (low-speed main) mode		LV (low-voltage main) mode	
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode plus: fclk ≥ 10 MHz	2.7 V ≤ EVDD0 ≤ 5.5 V	0	1000	_		_		kHz
Setup time of restart condition	tsu: sta	2.7 V ≤ EVDD0 ≤ 5.	5 V	0.26		-	_	_		μs
Hold time Note 1	thd: STA	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	0.26		_		_		μs
Hold time when SCLA0 = "L"	tLOW	2.7 V ≤ EV _{DD0} ≤ 5.	.5 V	0.5		_		_		μs
Hold time when SCLA0 = "H"	tніgн	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	0.26		_		_	_	μs
Data setup time (reception)	tsu: dat	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	50		_		_	_	ns
Data hold time (transmission) Note 2	thd: dat	2.7 V ≤ EVDD0 ≤ 5.	2.7 V ≤ EVDD0 ≤ 5.5 V		0.45	-	_	_	_	μs
Setup time of stop condition	tsu: sto	2.7 V ≤ EVDD0 ≤ 5.5 V		0.26			_	-	_	μs
Bus-free time	tBUF	2.7 V ≤ EVDD0 ≤ 5.5 V		0.5		_		_	_	μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

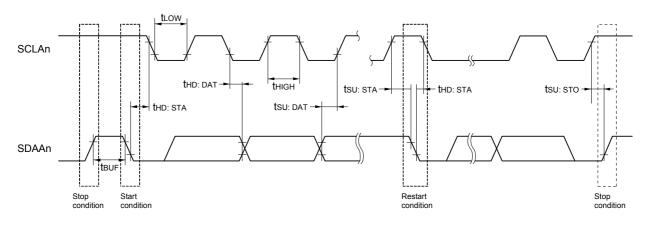
Note 2. The maximum value (MAX.) of thD: DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

 $\label{eq:Remark} \textbf{Remark} \qquad \text{The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.}$

Fast mode plus: C_b = 120 pF, R_b = 1.1 k Ω

IICA serial transfer timing



Remark n = 0, 1

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage Input channel	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = V _{DD} Reference voltage (-) = V _{SS}	Reference voltage (+) = V _{BGR} Reference voltage (-)= AV _{REFM}
ANI0 to ANI7	Refer to 2.6.1 (1).	Refer to 2.6.1 (3).	Refer to 2.6.1 (4).
ANI16 to ANI24	Refer to 2.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 2.6.1 (1) .		_

(1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI2 to ANI7, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Condition	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V		1.2	±3.5	LSB
		AV _{REFP} = V _{DD} Note 3	1.6 V ≤ AVREFP ≤ 5.5 V Note 4		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	$3.6 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	2.125		39	μs
		Target pin: ANI2 to ANI14	2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
			1.6 V ≤ V _{DD} ≤ 5.5 V	57		95	μs
		10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.375		39	μs
		Target pin: Internal reference voltage,	2.7 V ≤ V _{DD} ≤ 5.5 V	3.5625		39	μs
		and temperature sensor output voltage (HS (high-speed main) mode)	2.4 V ≤ VDD ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±0.25	%FSR
		AV _{REFP} = V _{DD} Note 3	1.6 V ≤ AVREFP ≤ 5.5 V Note 4			±0.50	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±0.25	%FSR
		AV _{REFP} = V _{DD} Note 3	1.6 V ≤ AVREFP ≤ 5.5 V Note 4			±0.50	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±2.5	LSB
		AVREFP = VDD Note 3	1.6 V ≤ AVREFP ≤ 5.5 V Note 4			±5.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±1.5	LSB
		AV _{REFP} = V _{DD} Note 3	1.6 V ≤ AVREFP ≤ 5.5 V Note 4			±2.0	LSB
Analog input voltage	Vain	ANI2 to ANI7		0		AVREFP	V
		Internal reference voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed m	V _{BGR} Note 5			V	
		Temperature sensor output voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed m	V _{TMPS25} Note 5			V	

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. When AVREFP < VDD, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AVREFP = VDD. Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AVREFP = VDD. Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when AVREFP = VDD.

Note 4. Values when the conversion time is set to 57 μs (min.) and 95 μs (max.).

Note 5. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.



(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI24

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, 1.6 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Cond	itions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V		1.2	±5.0	LSB
		EVDD0 ≤ AVREFP = VDD Notes 3, 4	1.6 V ≤ AVREFP ≤ 5.5 V Note 5		1.2	±8.5	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.125		39	μs
		Target ANI pin: ANI16 to ANI24	2.7 V ≤ VDD ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ VDD ≤ 5.5 V	17		39	μs
			1.6 V ≤ VDD ≤ 5.5 V	57		95	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±0.35	%FSR
		EV _{DD0} ≤ AV _{REFP} = V _{DD} Notes 3, 4	1.6 V ≤ AVREFP ≤ 5.5 V Note 5			±0.60	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±0.35	%FSR
		EVDD0 ≤ AVREFP = VDD Notes 3, 4	1.6 V ≤ AVREFP ≤ 5.5 V Note 5			±0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±3.5	LSB
		EVDD0 ≤ AVREFP = VDD Notes 3, 4	1.6 V ≤ AVREFP ≤ 5.5 V Note 5			±6.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±2.0	LSB
		EVDD0 ≤ AVREFP = VDD Notes 3, 4	1.6 V ≤ AVREFP ≤ 5.5 V Note 5			±2.5	LSB
Analog input voltage	VAIN	ANI16 to ANI24		0		AVREFP and EVDD0	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. When $EVDD0 \le AVREFP \le VDD$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AVREFP = VDD. Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AVREFP = VDD. Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when AVREFP = VDD.

Note 4. When AVREFP \leq EVDD0 \leq VDD, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when AVREFP = VDD. Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when AVREFP = VDD. Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when AVREFP = VDD.

Note 5. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin: ANI0 to ANI17, ANI16 to ANI24, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V, Reference voltage (+) = VDD, Reference voltage (-) = Vss)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V		1.2	±7.0	LSB
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3		1.2	±10.5	LSB
Conversion time	tconv	10-bit resolution	$3.6 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	2.125		39	μs
		Target pin: ANI0 to ANI7, ANI16 to ANI24	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	3.1875		39	μs
			1.8 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
			1.6 V ≤ V _{DD} ≤ 5.5 V	57		95	μs
		10-bit resolution	3.6 V ≤ V _{DD} ≤ 5.5 V	2.375		39	μs
		Target pin: internal reference voltage, and temperature sensor output voltage	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	3.5625		39	μs
		(HS (high-speed main) mode)	$2.4~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±0.85	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±0.85	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±4.0	LSB
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±6.5	LSB
Differential linearity error	DLE	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±2.0	LSB
Note 1			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±2.5	LSB
Analog input voltage	Vain	ANI0 to ANI7		0		VDD	V
		ANI16 to ANI24		0		EV _{DD0}	٧
		Internal reference voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)			V _{BGR} Note 4		
		Temperature sensor output voltage (2.4 V \leq VDD \leq 5.5 V, HS (high-speed main) r	V _{TMPS25} Note 4			V	

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

Note 4. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2 to ANI7, ANI16 to ANI24

(TA = -40 to +85°C, 2.4 V \leq VDD \leq 5.5 V, 1.6 V \leq EVDD0 \leq VDD, Vss = EVss0 = 0 V, Reference voltage (+) = VBGR Note 3, Reference voltage (-) = AVREFM = 0 V Note 4, HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES				8		bit
Conversion time	tconv	8-bit resolution	2.4 V ≤ VDD ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	Ezs	8-bit resolution	$2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}$			±0.60	% FSR
Integral linearity error Note 1	ILE	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}$			±1.0	LSB
Analog input voltage	Vain			0		V _{BGR} Note 3	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

Note 4. When reference voltage (-) = Vss, the MAX. values are as follows.

Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (-) = AVREFM. Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (-) = AVREFM. Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

2.6.2 Temperature sensor characteristics/internal reference voltage characteristic

(TA = -40 to +85°C, 2.4 V \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, Ta = +25°C		1.05		V
Internal reference voltage	VBGR	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μs

2.6.3 D/A converter characteristics

(Ta = -40 to +85°C, 1.6 V \leq EVsso \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES					8	bit
Overall error	AINL	Rload = 4 MΩ	1.8 V ≤ V _{DD} ≤ 5.5 V			±2.5	LSB
		Rload = 8 MΩ	$1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$			±2.5	LSB
Settling time	tset	Cload = 20 pF	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$			3	μs
			1.6 V ≤ V _{DD} < 2.7 V			6	μs

2.6.4 Comparator

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Cor	nditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOCMP				±5	±40	mV
Input voltage range	VICMP		0		V _{DD}	V	
Internal reference	ΔVIREF	CmRVM register value : 7	FH to 80H (m = 0, 1)			±2	LSB
voltage deviation		Other than above			±1	LSB	
Response Time	tcr, tcf	Input amplitude±100mV			70	150	ns
Operation stabilization	tсмр	CMPn = 0→1	V _{DD} = 3.3 to 5.5 V			1	μs
time ^{Note 1}			V _{DD} = 2.7 to 3.3 V			3	μs
Reference voltage stabilization wait time	tvr	CVRE: 0→1 ^{Note 2}				20	μs
Operation current	ICMPDD	Separately, it is defined as	the operation current of perip	heral function	ons.		

- **Note 1.** Time taken until the comparator satisfies the DC/AC characteristics after the comparator operation enable signal is switched (CMPnEN = $0 \rightarrow 1$).
- **Note 2.** Enable comparator output (CnOE bit = 1; n = 0 to 1) after enabling operation of the internal reference voltage generator (by setting the CVREm bit to 1; m = 0 to 1) and waiting for the operation stabilization time to elapse.

2.6.5 PGA

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Со	nditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOPGA					±10	mV
Input voltage range	VIPGA			0		0.9 × V _{DD} / Gain	V
Output voltage range	VIOHPGA			$0.93 \times V_{DD}$			٧
	VIOLPGA					$0.07 \times V_{DD}$	V
Gain error		x4, x8				±1	%
	x16		6			±1.5	%
		x32				±2	%
Slew rate	SRRPGA	Rising	4.0 V ≤ V _{DD} ≤ 5.5 V	3.5			V/µs
		When Vin= 0.1Vpb/gain to 0.9Vpb/gain. 10 to 90% of output voltage amplitude	(Other than x32)				
			4.0 V ≤ V _{DD} ≤ 5.5 V (x32)	3.0			
			2.7 V ≤ V _{DD} ≤ 4.0V	0.5			
	SRFPGA	Falling	4.0 V ≤ V _{DD} ≤ 5.5 V	3.5			
		When Vin= 0.1Vpb/gain to 0.9Vpb/gain.	(Other than x32)				
		90 to 10% of output	4.0 V ≤ V _{DD} ≤ 5.5 V (x32)	3.0			
		voltage amplitude	2.7 V ≤ V _{DD} ≤ 4.0V	0.5			
Reference voltage	t PGA	x4, x8				5	μs
stabilization wait time- Note 1		x16, x32				10	μs
Operation current	IPGADD	Separately, it is defined a	Separately, it is defined as the operation current of peripheral fu				

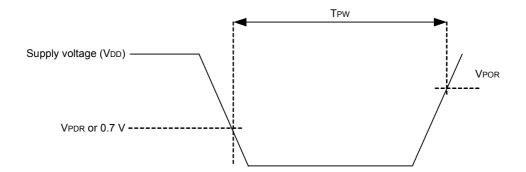
Note 1. Time required until a state is entered where the DC and AC specifications of the PGA are satisfied after the PGA operation has been enabled (PGAEN = 1).

2.6.6 POR circuit characteristics

$(TA = -40 \text{ to } +85^{\circ}C, Vss = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power on/down reset threshold	VPOR	Voltage threshold on VDD rising	1.47	1.51	1.55	V
	VPDR	Voltage threshold on VDD falling Note 1	1.46	1.50	1.54	V
Minimum pulse width Note 2	Tpw		300			μs

- **Note 1.** However, when the operating voltage falls while the LVD is off, enter STOP mode, or enable the reset status using the external reset pin before the voltage falls below the operating voltage range shown in **2.4 AC Characteristics**.
- Note 2. Minimum time required for a POR reset when VDD exceeds below VPDR. This is also the minimum time required for a POR reset from when VDD exceeds below 0.7 V to when VDD exceeds VPOR while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



2.6.7 LVD circuit characteristics

(1) Reset Mode and Interrupt Mode

(Ta = -40 to +85°C, VPDR \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Voltage	Supply voltage level	VLVD0	Rising edge	3.98	4.06	4.14	V
detection			Falling edge	3.90	3.98	4.06	V
threshold		VLVD1	Rising edge	3.68	3.75	3.82	V
			Falling edge	3.60	3.67	3.74	V
		VLVD2	Rising edge	3.07	3.13	3.19	V
		Falling edge	3.00	3.06	3.12	V	
		VLVD3	Rising edge	2.96	3.02	3.08	V
			Falling edge	2.90	2.96	3.02	V
		VLVD4	Rising edge	2.86	2.92	2.97	V
			Falling edge	2.80	2.86	2.91	V
		VLVD5	Rising edge	2.76	2.81	2.87	V
		Falling edge	2.70	2.75	2.81	V	
		VLVD6	Rising edge	2.66	2.71	2.76	V
		Falling edge	2.60	2.65	2.70	V	
		VLVD7	Rising edge	2.56	2.61	2.66	V
			Falling edge	2.50	2.55	2.60	V
		VLVD8	Rising edge	2.45	2.50	2.55	V
			Falling edge	2.40	2.45	2.50	V
		VLVD9	Rising edge	2.05	2.09	2.13	V
			Falling edge	2.00	2.04	2.08	V
		VLVD10	Rising edge	1.94	1.98	2.02	V
			Falling edge	1.90	1.94	1.98	V
		VLVD11	Rising edge	1.84	1.88	1.91	V
			Falling edge	1.80	1.84	1.87	V
		VLVD12	Rising edge	1.74	1.77	1.81	V
			Falling edge	1.70	1.73	1.77	V
		VLVD13	Rising edge	1.64	1.67	1.70	V
			Falling edge	1.60	1.63	1.66	V
Minimum puls	se width	tLW		300			μs
Detection del	ay time					300	μs

(2) Interrupt & Reset Mode

(TA = -40 to +85°C, VPDR \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol		Cond	itions	MIN.	TYP.	MAX.	Unit
Voltage detection	VLVDA0	VPOC2,	VPOC1, VPOC0 = 0, 0, 0, fal	ling reset voltage	1.60	1.63	1.66	V
threshold	VLVDA1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
				Falling interrupt voltage	1.70	1.73	1.77	V
	VLVDA2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
				Falling interrupt voltage	1.80	1.84	1.87	V
	VLVDA3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDB0	VPOC2,	VPOC1, VPOC0 = 0, 0, 1, fal	ling reset voltage	1.80	1.84	1.87	V
	VLVDB1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
				Falling interrupt voltage	1.90	1.94	1.98	V
	VLVDB2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
				Falling interrupt voltage	2.00	2.04	2.08	V
	VLVDB3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
				Falling interrupt voltage	3.00	3.06	3.12	V
	VLVDC0	VPOC2,	VPOC1, VPOC0 = 0, 1, 0, fal	ling reset voltage	2.40	2.45	2.50	V
	VLVDC1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
				Falling interrupt voltage	2.50	2.55	2.60	V
	VLVDC2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
				Falling interrupt voltage	2.60	2.65	2.70	V
	VLVDC3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	V
				Falling interrupt voltage	3.60	3.67	3.74	V
	VLVDD0	VPOC2,	VPOC1, VPOC0 = 0, 1, 1, fal	ling reset voltage	2.70	2.75	2.81	V
	VLVDD1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDD2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
				Falling interrupt voltage	2.90	2.96	3.02	V
	VLVDD3	1	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
				Falling interrupt voltage	3.90	3.98	4.06	V

2.6.8 Power supply voltage rising slope characteristics

$(TA = -40 \text{ to } +85^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

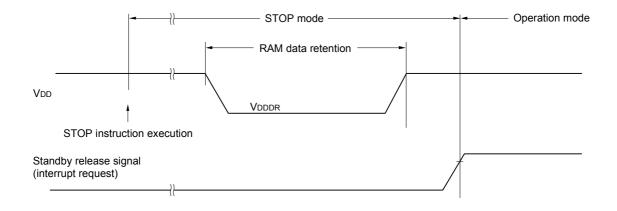
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 2.4 AC Characteristics.

2.7 RAM Data Retention Characteristics

$(TA = -40 \text{ to } +85^{\circ}\text{C}, Vss = 0V))$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.46 Notes 1, 2		5.5	V

- **Note 1.** The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.
- Note 2. Enter STOP mode before the supply voltage falls below the recommended operating voltage.



2.8 Flash Memory Programming Characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
System clock frequency	fclk	1.8 V ≤ VDD ≤ 5.5 V	1.8 V ≤ VDD ≤ 5.5 V			32	MHz
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years	TA = 85°C	1,000			Times
Number of data flash rewrites		Retained for 1 year	TA = 25°C		1,000,000		
Notes 1, 2, 3		Retained for 5 years	Ta = 85°C	100,000			
		Retained for 20 years	Ta = 85°C	10,000			

- Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
- Note 2. When using flash memory programmer and Renesas Electronics self-programming library
- **Note 3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

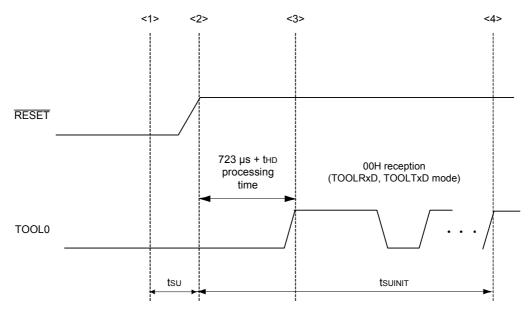
(TA = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming			1,000,000	bps

2.10 Timing of Entry to Flash Memory Programming Modes

(TA = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory)	thD	POR and LVD reset must end before the external reset ends.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the external reset ends).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

tsuinit. The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.

tsu:How long from when the TOOL0 pin is placed at the low level until a pin reset ends thd:Ho:How long to keep the TOOL0 pin at the low level from when the external resets end (excluding the processing time of the firmware to control the flash memory)

3. ELECTRICAL SPECIFICATIONS (G: TA = -40 to +105°C)

This chapter describes the following electrical specifications.

Target products G: Industrial applications TA = −40 to +105°C

R5F11BxxGxx

- Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
- Caution 2. With products not provided with an EVDD0, or EVsso pin, replace EVDD0 with VDD, or replace EVsso with Vss.
- Caution 3. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G1F User's Manual.
- Caution 4. Please contact Renesas Electronics sales office for derating of operation under TA = +85 to +105°C.

 Derating is the systematic reduction of load for the sake of improved reliability.
- Remark When the products "G: Industrial applications" is used in the range of TA = -40 to +85°C, see 2. ELECTRICAL SPECIFICATIONS (TA = -40 to +85°C).

Operation of products rated "G: Industrial applications (TA = -40 to + 105°C)" at ambient operating temperatures above 85°C differs from that of products rated "A: Consumer applications" in the ways listed below.

Parameter	A: Consumer applications	G: Industrial applications
Operating ambient temperature	TA = -40 to +85°C	T _A = -40 to +105°C
Operating mode Operating voltage range	HS (high-speed main) mode: $2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V@1 MHz to } 32 \text{ MHz}$ $2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V@1 MHz to } 16 \text{ MHz}$ LS (low-speed main) mode: $1.8 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V@1 MHz to } 8 \text{ MHz}$ LV (low-voltage main) mode: $2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V@1 MHz to } 4 \text{ MHz}$	HS (high-speed main) mode only: $2.7~V \le V_{DD} \le 5.5~V@1~MHz~to~32~MHz$ $2.4~V \le V_{DD} \le 5.5~V@1~MHz~to~16~MHz$
High-speed on-chip oscillator clock accuracy	1.8 V ≤ V _{DD} ≤ 5.5 V: ±1.0% @ T _A = -20 to +85°C ±1.5% @ T _A = -40 to -20°C 2.4 V ≤ V _{DD} < 1.8 V: ±5.0% @ T _A = -20 to +85°C ±5.5% @ T _A = -40 to -20°C	2.4 V ≤ VDD ≤ 5.5 V: ±2.0% @ TA = +85 to +105°C ±1.0% @ TA = -20 to +85°C ±1.5% @ TA = -40 to -20°C
Serial array unit	UART CSI: fcLk/2 (16 Mbps supported), fcLk/4 Simplified I ² C communication	UART CSI: fcLk/4 Simplified I ² C communication
IICA	Standard mode Fast mode Fast mode plus	Standard mode Fast mode
Voltage detector	• Rising: 1.67 V to 4.06 V (14 stages) • Falling: 1.63 V to 3.98 V (14 stages)	• Rising: 2.61 V to 4.06 V (8 stages) • Falling: 2.55 V to 3.98 V (8 stages)

Remark The electrical characteristics of products rated "G: Industrial applications (TA = -40 to + 105°C)" at ambient operating temperatures above 85°C differ from those of products "A: Consumer applications". For details, refer to **3.1** to **3.10**.

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings

(1/2)

Symbols	Conditions	D-ti	
-	Conditions	Ratings	Unit
VDD		-0.5 to +6.5	V
EV _{DD0}		-0.5 to +6.5	V
VIREGC	REGC	-0.3 to +2.8	V
		and -0.3 to V _{DD} +0.3 Note 1	
VI1	P00 to P06, P10 to P17, P30, P31,	-0.3 to EVDD0 +0.3	V
	P40 to P43, P50 to P55, P70 to P77, P120,	and -0.3 to V _{DD} +0.3 Note 2	
Mo		0.2 to 1.6 E	V
V12	P60 to P63 (N-cri open-drain)	-0.3 (0 +0.5	V
VI3	P20 to P27, P121 to P124, P137,	-0.3 to V _{DD} +0.3 Note 2	V
	EXCLK, EXCLKS, RESET		
Vo1	P00 to P06, P10 to P17, P30, P31,	-0.3 to EVDD0 +0.3	V
	P40 to P43, P50 to P55, P60 to P63,	and -0.3 to V _{DD} +0.3 Note 2	
	P70 to P77, P120, P130, P140, P141,		
	P146, P147		
Vo2	P20 to P27	-0.3 to V _{DD} +0.3 Note 2	V
VAI1	ANI16 to ANI24	-0.3 to EVDD0 +0.3	.,
		and -0.3 to AVREF(+) +0.3 Notes 2, 3	V
VAI2	ANI0 to ANI7	-0.3 to V _{DD} +0.3	V
		and -0.3 to AVREF(+) +0.3 Notes 2, 3	V
	EVDD0 VIREGC VI1 VI2 VI3 VO1 VO2 VAI1	EVDD0 VIREGC REGC VI1 P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147 VI2 P60 to P63 (N-ch open-drain) VI3 P20 to P27, P121 to P124, P137, EXCLK, EXCLKS, RESET V01 P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P60 to P63, P70 to P77, P120, P130, P140, P141, P146, P147 Vo2 P20 to P27 VAI1 ANI16 to ANI24	EVDDO REGC REGC REGC -0.3 to +6.5 VIREGC REGC -0.3 to +2.8 and -0.3 to VDD +0.3 Note 1 VI1 P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147 VI2 P60 to P63 (N-ch open-drain) -0.3 to +6.5 VI3 P20 to P27, P121 to P124, P137, EXCLK, EXCLKS, RESET VO1 P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P60 to P63, P70 to P77, P120, P130, P141, P146, P147 Vo2 P20 to P27 -0.3 to VDD +0.3 Note 2 VAI1 ANI16 to ANI24 -0.3 to VDD +0.3 Note 2 -0.3 to EVDDO +0.3 and -0.3 to AVREF(+) +0.3 Notes 2, 3 -0.3 to VDD +0.3 Notes 2, 3 -0.3 to VDD +0.3

- Note 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
- Note 2. Must be 6.5 V or lower.
- Note 3. Do not exceed AVREF (+) + 0.3 V in case of A/D conversion target pin.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter.

 That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
- Remark 2. AVREF (+): + side reference voltage of the A/D converter.
- Remark 3. Vss: Reference voltage

Absolute Maximum Ratings

(2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P130, P140, P141, P146, P147	-40	mA
		Total of all	P00 to P04, P40 to P43,P120, P130, P140, P141	-70	mA
		pins -170 mA	P05, P06, P10 to P17, P30, P31, P50 to P55, P70 to P77, P146, P147	-100	mA
	Іон2	Per pin	P20 to P27	-0.5	mA
		Total of all pins		-2	mA
Output current, low	loL1	Per pin	P00 to P06, P10 to P17, P30, P31, P40-P43, P50 to P55, P60 to P63, P70 to P77, P120, P130, P140, P141, P146, P147	40	mA
		Total of all	P00 to P04, P40 to P47, P120, P130, P140, P141	70	mA
		pins 170 mA	P05, P06, P10 to P17, P30, P31, P50 to P55, P70 to P77, P146, P147	100	mA
	lOL2	Per pin	P20 to P27	1	mA
		Total of all pins		5	mA
Operating ambient tem-	ТА	In normal c	pperation mode	-40 to +105	°C
perature		In flash me	mory programming mode		
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

3.2 Oscillator Characteristics

3.2.1 X1, XT1 characteristics

(Ta = -40 to +105°C, 2.4 V \leq EVDD0 = VDD \leq 5.5 V, Vss = 0 V)

Resonator	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) Note	Ceramic resonator/	$2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	1.0		20.0	MHz
	crystal resonator	2.4 V ≤ V _{DD} < 2.7 V	1.0		16.0	
XT1 clock oscillation frequency (fxT) Note	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time.

Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user.

Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to 5.4 System Clock Oscillator in the RL78/G1F User's Manual.

3.2.2 On-chip oscillator characteristics

(TA = -40 to +105°C, 2.4 V \leq EVDD0 = VDD \leq 5.5 V, Vss = 0 V)

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency	fıн	2.7 V ≤ VDD ≤ 5.5 V	1		32	MHz
Notes 1, 2		2.4 V ≤ V _{DD} < 2.7 V	1		16	MHz
High-speed on-chip oscillator clock frequency		T _A = +85 to +105°C	-2		2	%
accuracy		T _A = -20 to +85°C	-1		1	%
		T _A = -40 to -20°C	-1.5		1.5	%
Low-speed on-chip oscillator clock frequency	fıL			15		kHz
Low-speed on-chip oscillator clock frequency			-15		+15	%
accuracy						

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 4 of the option byte (000C2H/010C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.

3.3 DC Characteristics

3.3.1 Pin characteristics

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EVDD0} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	Іон1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P55, P70 to P77, P120, P130, P140, P141, P146, P147				-3.0 Note 2	mA
		Total of P00 to P04, P40 to P43,	4.0 V ≤ EVDD0 ≤ 5.5 V			-30.0	mA
		P120, P130, P140, P141	2.7 V ≤ EVDD0 < 4.0 V			-10.0	mA
		(When duty ≤ 70% Note 3)	2.4 V ≤ EVDD0 < 2.7 V			-5.0	mA
			$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$			-30.0	mA
		P30, P31, P50 to P53,	2.7 V ≤ EV _{DD0} < 4.0 V			-19.0	mA
		P70 to P77, P146, P147 (When duty ≤ 70% Note 3)	1.8 V ≤ EVDD0 < 2.7 V			-10.0	mA
		Total of all pins (When duty ≤ 70% Note 3)				-60.0	mA
	Іон2	Per pin for P20 to P27				-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% Note ³)	2.4 V ≤ VDD ≤ 5.5 V			-1.5	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from the EVDDO, VDD pins to an output pin.

Note 3. Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

```
• Total output current of pins = (IOH \times 0.7)/(n \times 0.01)

<Example> Where n = 80% and IOH = -10.0 mA

Total output current of pins = (-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7 mA
```

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43, P50 to P55, P71, P74 do not output high level in N-ch open-drain mode.

Note 2. Do not exceed the total current value.

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

(2/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	IOL1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77,P120, P130, P140, P141, P146, P147				8.5 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		Total of P00 to P04, P40 to P43,	4.0 V ≤ EVDD0 ≤ 5.5 V			40.0	mA
		P120, P130, P140, P141	2.7 V ≤ EVDD0 < 4.0 V			15.0	mA
		(When duty ≤ 70% Note 3)	2.4 V ≤ EVDD0 < 1.8 V			9.0	mA
		Total of P05, P06, P10 to P17,	4.0 V ≤ EVDD0 ≤ 5.5 V			40.0	mA
		P30, P31, P50 to P55, P60 to	2.7 V ≤ EVDD0 < 4.0 V			35.0	mA
		P63, P70 to P77, P146, P147 (When duty ≤ 70% Note 3)	2.4 V ≤ EVDD0 < 1.8 V			20.0	mA
		Total of all pins (When duty ≤ 70% Note 3)				80.0	mA
	lOL2	Per pin for P20 to P27				0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	2.4 V ≤ VDD ≤ 5.5 V			5.0	mA

- Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso and Vss pins.
- Note 2. Do not exceed the total current value.
- **Note 3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (IoL × 0.7)/(n × 0.01)

<Example> Where n = 80% and IoL = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

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Items	Symbol	Conditions	Conditions			MAX.	Unit
Input voltage, high	VIH1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	Normal input buffer	0.8 EVDD0		EV _{DD0}	V
	V _{IH2}	P01, P03, P04, P10, P14 to P17, P30, P43, P50, P53 to P55,	TTL input buffer 4.0 V ≤ EVDD0 ≤ 5.5 V	2.2		EV _{DD0}	V
			TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	2.0		EV _{DD0}	V
			TTL input buffer 2.4 V ≤ EVDD0 < 3.3 V	1.5		EV _{DD0}	V
	VIH3	P20 to P27 (when P20 is used as	0.7 VDD		Vdd	V	
	VIH4	P60 to P63	0.7 EVDD0		6.0	V	
	V _{IH5}	P121 to P123, P137, EXCLK, EX P20 is used as INTP11 pin)	CLKS, RESET (when	0.8 VDD		VDD	V
Input voltage, low	VIL1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	Normal input buffer	0		0.2 EVDD0	V
	VIL2	P01, P03, P04, P10, P14 to P17, P30, P43, P50, P53 to P55,	TTL input buffer 4.0 V ≤ EVDD0 ≤ 5.5 V	0		0.8	V
			TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	0		0.5	V
			TTL input buffer 2.4 V ≤ EVDD0 < 3.3 V	0		0.32	V
	VIL3	P20 to P27 (when P20 is used as	a port pin)	0		0.3 VDD	V
	VIL4	P60 to P63		0		0.3 EVDD0	V
	VIL5	P121 to P124, P137, EXCLK, EX P20 is used as INTP11 pin)	CLKS, RESET (when	0		0.2 VDD	V

Caution The maximum value of VIH of pins P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43, P50 to P55, P71, P74 is EVDD0, even in the N-ch open-drain mode.

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

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Items	Symbol	Condition	าร	MIN.	TYP.	MAX.	Unit
Output voltage, high	VOH1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55,	4.0 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -3.0 mA	EVDD0 - 0.7			V
		P70 to P77, P120, P130, P140, P141, P146, P147	2.7 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -2.0 mA	EVDD0 - 0.6			V
			2.4 V ≤ EV _{DD0} < 5.5 V, IOH1 = -1.5 mA	EVDD0 - 0.5			V
	VOH2	P20 to P27	$2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V},$ $IOH2 = -100 \mu\text{A}$	VDD - 0.5			V
Output voltage, low	VOL1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55,	4.0 V ≤ EVDD0 ≤ 5.5 V, IOL1 = 8.5 mA			0.7	V
	D444 D440 D447	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $\text{IoL1} = 3.0 \text{ mA}$			0.6	V	
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $\text{IoL1} = 1.5 \text{ mA}$			0.4	V
			$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $\text{IoL1} = 0.6 \text{ mA}$			0.4	V
	VOL2	P20 to P27	$2.4~V \leq V_{DD} \leq 5.5~V,$ $I_{OL2} = 400~\mu A$			0.4	V
	VOL3	P60 to P63	4.0 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 15.0 mA			2.0	V
			4.0 V ≤ EVDD0 ≤ 5.5 V, lol3 = 5.0 mA			0.4	V
			2.7 V ≤ EVDD0 ≤ 5.5 V, lol3 = 3.0 mA			0.4	V
			2.4 V ≤ EVDD0 ≤ 5.5 V, loL3 = 2.0 mA			0.4	V

Caution P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43, P50 to P55, P71, P74 do not output high level in N-ch opendrain mode.

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

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Items	Symbol	Conditi	ons		MIN.	TYP.	MAX.	Unit
Input leakage cur- rent, high	ILIH1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	VI = EVDD0				1	μА
	ILIH2	P20 to P27, P137, RESET	VI = VDD				1	μΑ
	Ішн3	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VDD	In input port or external clock input			1	μА
				In resonator con- nection			10	μΑ
Input leakage current, low	ILIL1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	VI = EVsso				-1	μА
	ILIL2	P20 to P27, P137, RESET	Vı = Vss				-1	μΑ
	ILIL3	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VSS	In input port or external clock input			-1	μА
				In resonator con- nection			-10	μΑ
On-chip pull-up resistance	Ru	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	Vı = EVsso	, In input port	10	20	100	kΩ

3.3.2 Supply current characteristics

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

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Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operat-	HS (high-speed main)	fHOCO = 64 MHz,	Basic	V _{DD} = 5.0 V		2.4		mA
current		ing mode	mode Note 5	fih = 32 MHz Note 3	operation	V _{DD} = 3.0 V		2.4		
Note 1				fHOCO = 32 MHz,	Basic	V _{DD} = 5.0 V		2.1		
				fih = 32 MHz Note 3	operation	V _{DD} = 3.0 V		2.1		
			HS (high-speed main)	fHOCO = 64 MHz,	Normal	V _{DD} = 5.0 V		5.2	9.3	mA
			mode Note 5	fih = 32 MHz Note 3	operation	V _{DD} = 3.0 V		5.2	9.3	
				fHOCO = 32 MHz,	Normal	V _{DD} = 5.0 V		4.8	8.7	
				fih = 32 MHz Note 3	operation	V _{DD} = 3.0 V		4.8	8.7	
				fносо = 48 MHz,	Normal	V _{DD} = 5.0 V		4.1	7.3	
				fih = 24 MHz Note 3	operation	V _{DD} = 3.0 V		4.1	7.3	
				fHOCO = 24 MHz,	Normal	V _{DD} = 5.0 V		3.8	6.7	
				fih = 24 MHz Note 3	operation	V _{DD} = 3.0 V		3.8	6.7	
				fHOCO = 16 MHz,	Normal	V _{DD} = 5.0 V		2.8	4.9	
				fih = 16 MHz Note 3	operation	V _{DD} = 3.0 V		2.8	4.9	
			HS (high-speed main)	f _{MX} = 20 MHz Note 2,	Normal	Square wave input		3.3	5.7	mA
		mode Note 5	V _{DD} = 5.0 V	operation	Resonator connection		3.5	5.8		
			V _{DD} = 3.0 V	Normal	Square wave input		3.3	5.7		
				f _{MX} = 10 MHz Note 2,	operation	Resonator connection		3.5	5.8	
					Normal	Square wave input		2.0	3.4	
					operation	Resonator connection		2.1	3.5	
				fmx = 10 MHz Note 2,	Normal	Square wave input		2.0	3.4	
				V _{DD} = 3.0 V	operation	Resonator connection		2.1	3.5	
			Subsystem clock	fsuB = 32.768 kHz Note 4	Normal	Square wave input		4.7	6.1	μΑ
			operation	Ta = -40°C	operation	Resonator connection		4.7	6.1	
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		4.7	6.1	
				T _A = +25°C	operation	Resonator connection		4.7	6.1	
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		4.8	6.7	
				T _A = +50°C	operation	Resonator connection		4.8	6.7	
		fsuB = 32.768 kHz Note 4 Normal	Normal	Square wave input		4.8	7.5			
		T _A = +70°C	operation	Resonator connection		4.8	7.5			
			fsuB = 32.768 kHz Note 4	Normal	Square wave input		5.4	8.9		
			T _A = +85°C	operation	Resonator connection		5.4	8.9		
		fsuB = 32.768 kHz Note 4	Normal	Square wave input		7.2	21.0			
				T _A = +105°C	operation	Resonator connection		7.3	21.1	

(Notes and Remarks are listed on the next page.)

- Note 1. Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing data flash rewrite.
- Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 3. When high-speed system clock and subsystem clock are stopped.
- Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer
- **Note 5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below. HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}_{@}1 \text{ MHz}$ to 32 MHz $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}_{@}1 \text{ MHz}$ to 16 MHz
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency (64 MHz max.)

 Remark 3. fil: High-speed on-chip oscillator clock frequency (32 MHz max.)

 Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

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Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply current	IDD2	HALT mode	HS (high-speed main)	fHOCO = 64 MHz,	V _{DD} = 5.0 V		0.80	4.36	mA
Note 1	Note 2		mode Note 7	fiH = 32 MHz Note 4	V _{DD} = 3.0 V		0.80	4.36	
				fHOCO = 32 MHz,	V _{DD} = 5.0 V		0.54	3.67	
				fih = 32 MHz Note 4	V _{DD} = 3.0 V		0.54	3.67	
				fHOCO = 48 MHz,	V _{DD} = 5.0 V		0.62	3.42	
				fih = 24 MHz Note 4	V _{DD} = 3.0 V		0.62	3.42	
				fHOCO = 24 MHz,	V _{DD} = 5.0 V		0.44	2.85	
				fiH = 24 MHz Note 4	V _{DD} = 3.0 V		0.44	2.85	
				fHOCO = 16 MHz,	V _{DD} = 5.0 V		0.40	2.08	
				fih = 16 MHz Note 4	V _{DD} = 3.0 V		0.40	2.08	
			HS (high-speed main)	f _{MX} = 20 MHz Note 3,	Square wave input		0.28	2.45	mA
			mode Note 7	V _{DD} = 5.0 V	Resonator connection		0.49	2.57	
				f _{MX} = 20 MHz Note 3,	Square wave input		0.28	2.45	
				V _{DD} = 3.0 V	Resonator connection		0.49	2.57	
				fmx = 10 MHz Note 3,	Square wave input		0.19	1.28	
				V _{DD} = 5.0 V	Resonator connection		0.30	1.36	
				fmx = 10 MHz Note 3,	Square wave input		0.19	1.28	
		ļ	V _{DD} = 3.0 V	Resonator connection		0.30	1.36		
			Subsystem clock	fsuB = 32.768 kHz Note 5,	Square wave input		0.25	0.57	μΑ
			operation	TA = -40°C	Resonator connection		0.44	0.76	
				T 125°C	Square wave input		0.30	0.57	
					Resonator connection		0.49	0.76	
				fsuB = 32.768 kHz Note 5,	UB = 32.768 kHz Note 5, Square wave input		0.36	1.17	1
				T _A = +50°C	Resonator connection		0.59	1.36	
				fsuB = 32.768 kHz Note 5,	Square wave input		0.49	1.97	
				T _A = +70°C	Resonator connection		0.72	2.16	
				fsuB = 32.768 kHz Note 5,	Square wave input		0.97	3.37	
				T _A = +85°C	Resonator connection		1.16	3.56	
				fsuB = 32.768 kHz Note 5,	Square wave input		3.20	17.10	
				T _A = +105°C	Resonator connection		3.40	17.50	
	I _{DD3}	STOP mode	T _A = -40°C		<u> </u>		0.18	0.51	μА
	Note 6	Note 8	T _A = +25°C			İ	0.24	0.51	
		T _A = +50°C			İ	0.29	1.10		
		T _A = +70°C				0.41	1.90	-	
			T _A = +85°C				0.90	3.30	-
			T _A = +105°C				3.10	17.00	

(Notes and Remarks are listed on the next page.)

- Note 1. Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing data flash rewrite.
- Note 2. During HALT instruction execution by flash memory.
- Note 3. When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 4. When high-speed system clock and subsystem clock are stopped.
- Note 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
- Note 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below. HS (high-speed main) mode: $2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V} \text{@}1 \text{ MHz}$ to 32 MHz

 $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @1 \text{ MHz to } 16 \text{ MHz}$

- Note 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency (64 MHz max.)
 Remark 3. filh: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EVDD0} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = 0 \text{ V})$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscilla- tor operating current	I _{FIL} Note 1				0.2		μΑ
RTC operating current	I _{RTC} Notes 1, 2, 3				0.02		μΑ
12-bit interval timer operat- ing current	IT Notes 1, 2, 4				0.02		μА
Watchdog timer operating current	I _{WDT} Notes 1, 2, 5	fı∟ = 15 kHz			0.22		μА
A/D converter operating current	I _{ADC} Notes 1, 6	When conversion at maximum speed	Normal mode, AV _{REFP} = V _{DD} = 5.0 V		1.3	1.7	mA
			Low voltage mode, AVREFP = VDD = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	IADREF Note 1				75		μΑ
Temperature sensor operating current	ITMPS Note 1				75		μΑ
D/A converter operating current	IDAC Notes 1, 11	Per D/A converter channel				1.5	mA
PGA operating current		Operation			480	700	μΑ
Comparator operating cur- rent	ICMP Notes 1, 12	Operation (per comparator chan- nel, constant current for compara-	When the internal reference voltage is not in use		50	100	μА
		tor included)	When the internal reference voltage is in use		60	110	μΑ
LVD operating current	I _{LVD} Notes 1, 7				0.08		μΑ
Self-programming operating current	IFSP Notes 1, 9				2.50	12.2	mA
BGO operating current	I _{BGO} Notes 1, 8				2.50	12.2	mA
SNOOZE operating current	I _{SNOZ} Note 1	ADC operation	The mode is performed Note 10		0.50	1.10	mA
			The A/D conversion operations are performed, Low voltage mode, AVREFP = VDD = 3.0 V		1.20	2.04	
		CSI/UART operation			0.70	1.54	
		DTC operation			3.10		

- Note 1. Current flowing to VDD.
- Note 2. When high speed on-chip oscillator and high-speed system clock are stopped.
- Note 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
- Note 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator).

 The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
- Note 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- Note 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- **Note 8.** Current flowing during programming of the data flash.
- Note 9. Current flowing during self-programming.
- Note 10. For shift time to the SNOOZE mode, see 26.3.3 SNOOZE mode in the RL78/G1F User's Manual.



- **Note 11.** Current flowing only to the D/A converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IDAC when the D/A converter operates in an operation mode or the HALT mode.
- Note 12. Current flowing only to the comparator circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2, or IDD3 and ICMP when the comparator circuit is in operation.
- Remark 1. fil: Low-speed on-chip oscillator clock frequency
- Remark 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 3. fclk: CPU/peripheral hardware clock frequency
- Remark 4. Temperature condition of the TYP. value is TA = 25°C

3.4 AC Characteristics

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (min-	Tcy	Main system	HS (high-speed main)	$2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V}$	0.03125		1	μs
imum instruction exe- cution time)		clock (fmain) operation	mode	2.4 V ≤ VDD < 2.7 V	0.0625		1	μs
		Subsystem clo	ock (fsub) operation	$2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}$	28.5	30.5	31.3	μs
		In the self-	HS (high-speed main)	$2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V}$	0.03125		1	μs
		program- ming mode	mode	2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
External system clock	fex	2.7 V ≤ V _{DD} ≤	5.5 V		1.0		20.0	MHz
frequency		2.4 V ≤ V _{DD} ≤	2.7 V		1.0		16.0	MHz
	fexs				32		35	kHz
External system clock	texH,	2.7 V ≤ V _{DD} ≤	5.5 V		24			ns
input high-level width,	texL	2.4 V ≤ V _{DD} ≤	2.7 V		30			ns
low-level width	texhs,				13.7			μs
TI00 to TI03 input high-level width, low- level width	ttih, ttil				1/fMCK + 10 Note			ns
Timer RJ input cycle	fc	TRJIO		2.7 V ≤ EVDD0 ≤ 5.5 V	100			ns
				2.4 V ≤ EVDD0 < 2.7 V	300			ns
Timer RJ input high-	tтлін,	TRJIO		2.7 V ≤ EVDD0 ≤ 5.5 V	40			ns
level width, low-level width	t⊤JIL			2.4 V ≤ EVDD0 < 2.7 V	120			ns

Note The following conditions are required for low voltage interface when EVDD0 < VDD

2.4 V ≤ EV_{DD0} < 2.7 V: MIN. 125 ns

Remark fMCK: Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel

number (n = 0 to 3))

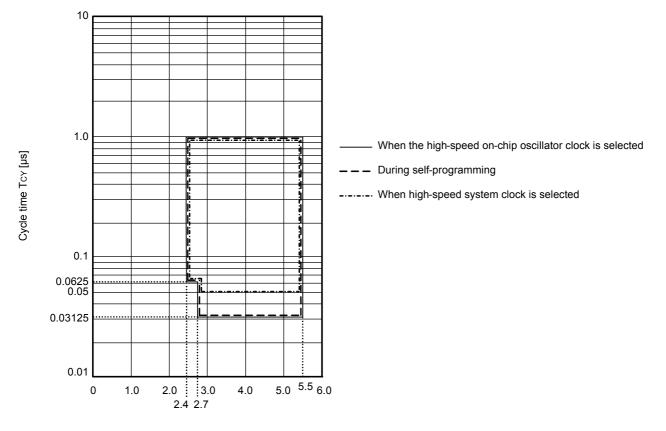
(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

(2/2)

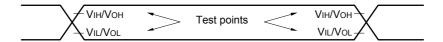
							-
Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Timer RD input high-level width, low-level width	ttdih, ttdil	TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1		3/fclk			ns
Timer RD forced cutoff signal	ttdsil	P130/INTP0 2MHz < fclk ≤ 32 MHz		1			μs
input low-level width			fclk ≤ 2 MHz	1/fcLK + 1			
Timer RG input high-level width, low-level width	tтgін, tтgіL	TRGIOA, TRGIOB		2.5/fclk			ns
TO00 to TO03,	fто	HS (high-speed main) mode	4.0 V ≤ EVDD0 ≤ 5.5 V			16	MHz
TRJIO0, TRJO0,			2.7 V ≤ EV _{DD0} < 4.0 V			8	MHz
TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1, TRGIOA, TRGIOB output frequency			2.4 V ≤ EVDD0 < 2.7 V			4	MHz
PCLBUZ0, PCLBUZ1 output	fPCL	HS (high-speed main) mode	4.0 V ≤ EVDD0 ≤ 5.5 V			16	MHz
frequency			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}$			8	MHz
			2.4 V ≤ EVDD0 < 2.7 V			4	MHz
Interrupt input high-level	tinth,	INTP0	$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	1			μs
width, low-level width	tintl	INTP1 to INTP11	2.4 V ≤ EVDD0 ≤ 5.5 V	1			μs
Key interrupt input low-level width	tkr	KR0 to KR7	2.4 V ≤ EVDD0 ≤ 5.5 V	250			ns
RESET low-level width	trsl			10			μs

Minimum Instruction Execution Time during Main System Clock Operation

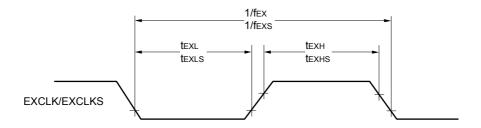
Tcy vs Vdd (HS (high-speed main) mode)



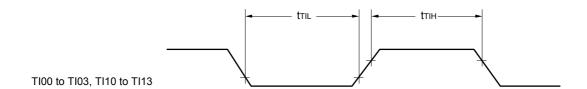
AC Timing Test Points

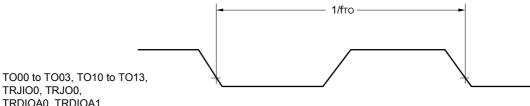


External System Clock Timing



TI/TO Timing

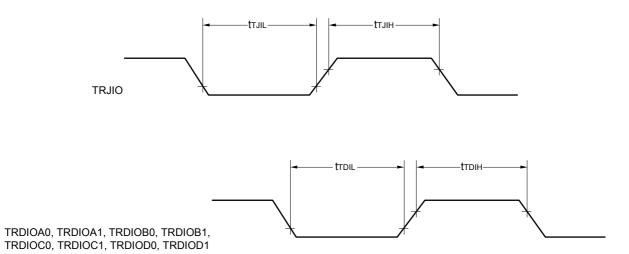


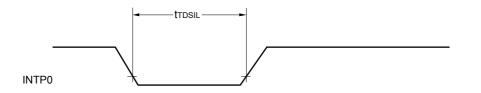


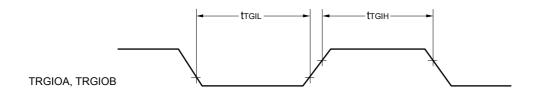
TRDIOA0, TRDIOA1,

TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1,

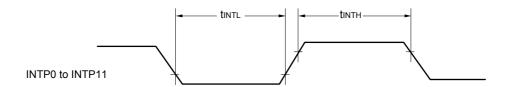
TRDIOD0, TRDIOD1, TRGIOA, TRGIOB



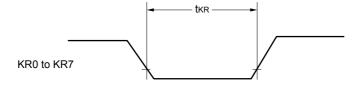




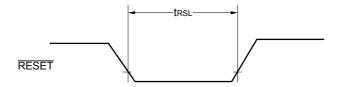
Interrupt Request Input Timing



Key Interrupt Input Timing

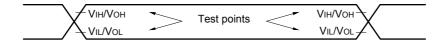


RESET Input Timing



3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		
			MIN.	MAX.	
Transfer rate	Transfer rate 2.4 V ≤ EVDD0 ≤ 5.5 V			fMCK/12 Note 2	bps
Note 1		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		2.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

Note 2. The following conditions are required for low voltage interface when EVDD0 < VDD.

 $2.4~V \leq EV_{DD0} < 2.7~V;~MAX.1.3~Mbps$

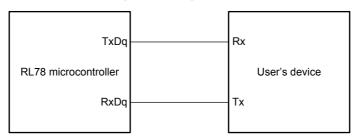
Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 32 MHz (2.7 V \leq VDD \leq 5.5 V)

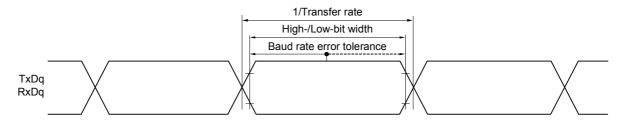
16 MHz (2.4 V \leq VDD \leq 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1, 3, 5, 7)

Remark 2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10, 11))

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) (TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol	Conditions		HS (high-speed	HS (high-speed main) mode	
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 2/fclk	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	250		ns
			2.4 V ≤ EVDD0 ≤ 5.5 V	500		ns
SCKp high-/low-level width	tĸнı,	4.0 V ≤ EVDD0 ≤ 5.5 V		tkcy1/2 - 24		ns
	tkL1	2.7 V ≤ EVDD0 ≤ 5.5 V		tkcy1/2 - 36		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V		tkcy1/2 - 76		
SIp setup time (to SCKp↑) Note 1	tsıĸ1	4.0 V ≤ EVDD0 ≤ 5.5 V		66		ns
		2.7 V ≤ EVDD0 ≤ 5.5 V		66		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V		113		
SIp hold time (from SCKp↑) Note 2	tksi1	2.7 V ≤ EVDD0 ≤ 5.5 V		38		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 20 pF Note 4			50	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remark 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3, 5, 7)
- Remark 2. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00 to 03, 10, 11))

(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVSS0 = 0 V)

Parameter	Symbol	Conditions		HS (high-spee	HS (high-speed main) mode	
				MIN.	MAX.	
SCKp cycle time Note 5	tKCY2	4.0 V ≤ EV _{DD0} ≤ 5.5 V	20 MHz < fmck	16/fмск		ns
			fмcк ≤ 20 MHz	12/fмск		ns
		2.7 V ≤ EV _{DD0} ≤ 5.5 V	16 MHz < fмcк	16/fмск		ns
			fмcκ ≤ 16 MHz	12/fмск		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V	12/fмcк and 1000		ns	
SCKp high-/ low-level width	tkH2, tkL2	4.0 V ≤ EVDD0 ≤ 5.5 V		tксү2/2 - 14		ns
		2.7 V ≤ EV _{DD0} ≤ 5.5 V	tксү2/2 - 16		ns	
		2.4 V ≤ EV _{DD0} ≤ 5.5 V	1/fмск + 36		ns	
SIp setup time tsik2 (to SCKp†) Note 1		2.7 V ≤ EV _{DD0} ≤ 5.5 V	1/fмcк + 40		ns	
		2.4 V ≤ EVDD0 ≤ 5.5 V	1/fмcк + 60		ns	
SIp hold time (from SCKp↑) Note 2	tksı2			1/fмск + 62		ns
Delay time from	tkso2	C = 30 pF Note 4	2.7 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск + 66	ns
SCKp↓ to SOp output Note 3			2.4 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск + 113	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SOp output lines.
- **Note 5.** The maximum transfer rate when using the SNOOZE mode is 1 Mbps.
- Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remark 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21), m: Unit number (m = 0, 1),
 - n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3, 5, 7)
- Remark 2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10, 11))

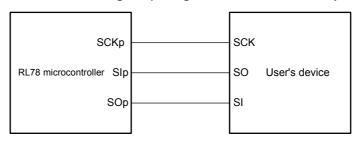
(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVSS0 = 0 V)(2/2)

Parameter	Symbol	Conditions		HS (high-speed ma	Unit	
				MIN.	MAX.	
SSI00 setup time	100 setup time tssik	DAPmn = 0	2.7 V ≤ EVDD0 ≤ 5.5 V	240		ns
			2.4 V ≤ EVDD0 ≤ 5.5 V	400		ns
		DAPmn = 1	2.7 V ≤ EVDD0 ≤ 5.5 V	1/fмск + 240		ns
			2.4 V ≤ EVDD0 ≤ 5.5 V	1/fмск + 400		ns
SSI00 hold time	SI00 hold time tkssi	tkssi DAPmn = 0	2.7 V ≤ EVDD0 ≤ 5.5 V	1/fмск + 240		ns
			2.4 V ≤ EVDD0 ≤ 5.5 V	1/fмск + 400		ns
		l l	2.7 V ≤ EVDD0 ≤ 5.5 V	240		ns
			2.4 V ≤ EVDD0 ≤ 5.5 V	400		ns

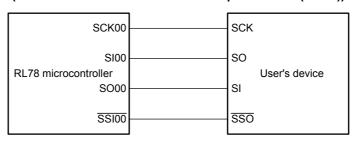
Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM number (g = 3, 5)

CSI mode connection diagram (during communication at same potential)



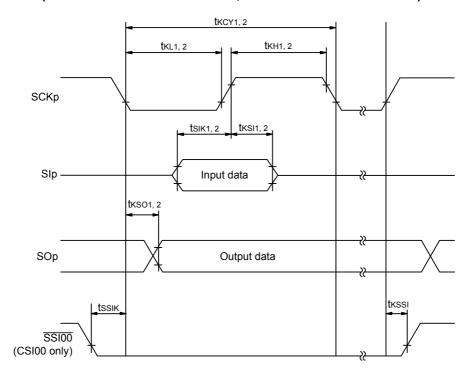
CSI mode connection diagram (during communication at same potential) (Slave Transmission of slave select input function (CSI00))



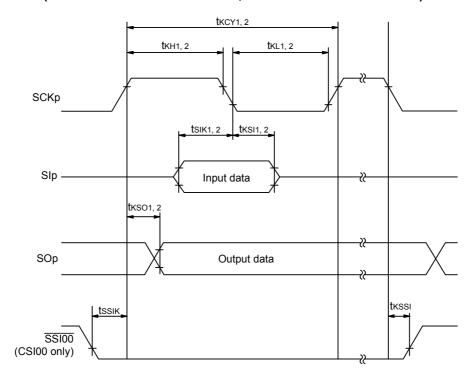
Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21)

Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)

CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21)

Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)

(4) During communication at same potential (simplified I²C mode)

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

Parameter	Symbol	Conditions	HS (high-speed	HS (high-speed main) mode		
			MIN.	MAX.	1	
SCLr clock frequency	fscL	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$		400 Note 1	kHz	
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 3 \text{ k}Ω$		100 Note 1	kHz	
Hold time when SCLr = "L"	tLOW	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	1200		ns	
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 3 \text{ k}Ω$	4600		ns	
Hold time when SCLr = "H"	tніGн	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	1200		ns	
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 3 \text{ k}Ω$	4600		ns	
Data setup time (reception)	tsu: dat	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	1/f _{MCK} + 220 Note 2		ns	
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 3 \text{ k}Ω$	1/f _{MCK} + 580 Note 2		ns	
Data hold time (transmission)	thd: dat	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	0	770	ns	
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$	0	1420	ns	

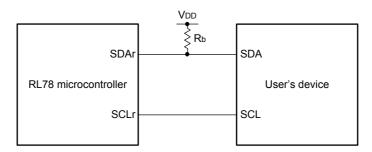
Note 1. The value must also be equal to or less than fmck/4.

Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

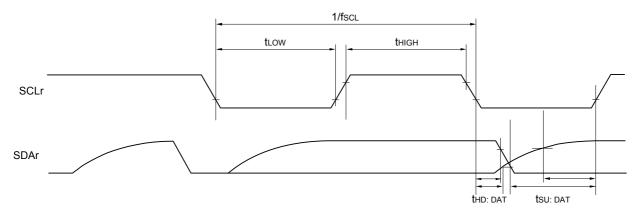
Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



 $\textbf{Remark 1.} \ \ R_b[\Omega]: \ Communication \ line \ (SDAr) \ pull-up \ resistance, \ C_b[F]: \ Communication \ line \ (SDAr, SCLr) \ load \ capacitance$

Remark 2. r: IIC number (r = 00, 01, 10, 11, 20, 21), g: PIM number (g = 0, 1, 3, 5, 7), h: POM number (h = 0, 1, 3, 5, 7)

Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),

n: Channel number (n = 0 to 3), mn = 00 to 03, 10, 11)

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

(1/2)

Parameter	Symbol		Conditions	HS (high-speed main) mode		Unit	
				MIN.	MAX.]	
Transfer rate	sfer rate reception		$0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$		f _{MCK} /12 Note 1	bps	
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		2.6	Mbps	
			$7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$		f _{MCK} /12 Note 1	bps	
			Theoretical value of the maximum transfer rate fmck = fclk Note 3		2.6	Mbps	
			$V \le EV_{DD0} < 3.3 \text{ V},$ $V \le V_b \le 2.0 \text{ V}$		fмск/12 Notes 1, 2	bps	
			Theoretical value of the maximum transfer rate fmck = fclk Note 3		1.3	Mbps	

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

Note 2. The following conditions are required for low voltage interface when EVDD0 < VDD.

 $2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V: MAX. } 2.6 \text{ Mbps}$

 $1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.4 \text{ V}$: MAX. 1.3 Mbps

Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 32 MHz (2.7 V \leq VDD \leq 5.5 V)

16 MHz (2.4 V \leq VDD \leq 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

- Remark 1. Vb [V]: Communication line voltage
- Remark 2. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1, 5, 7)
- Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10, 11)

Remark 4. UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

(2/2)

Parameter	Symbol	Conditions		HS (high-s	HS (high-speed main) mode	
					MAX.	
Transfer rate		transmission	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$		Note 1	bps
		Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF, } R_b = 1.4 \text{ k}\Omega,$ $V_b = 2.7 \text{ V}$		2.6 Note 2	Mbps	
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$		Note 3	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF, } R_b = 2.7 \text{ k}\Omega,$ $V_b = 2.3 \text{ V}$		1.2 Note 4	Mbps
			$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$		Note 5	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF, } R_b = 5.5 \text{ k}\Omega,$ $V_b = 1.6 \text{ V}$		0.43 Note 6	Mbps

Note 1. The smaller maximum transfer rate derived by using fмck/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when 4.0 V ≤ EVDD0 ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$

$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
Baud rate error (theoretical value) =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 100 \, [\%]}$$

- Note 2. This value as an example is calculated when the conditions described in the "Conditions" column are met.

 Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- **Note 3.** The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EVDD0 < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

Note 4. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.

^{*} This value is the theoretical value of the relative difference between the transmission and reception sides.

^{*} This value is the theoretical value of the relative difference between the transmission and reception sides.

Note 5. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate

Expression for calculating the transfer rate when 2.4 V \leq EVDD0 < 3.3 V and 1.6 V \leq Vb \leq 2.0 V

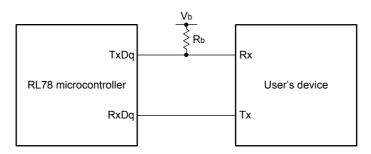
Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

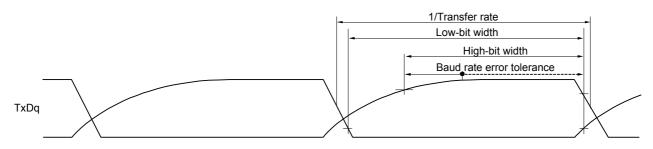
- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **Note 6.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 5** above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

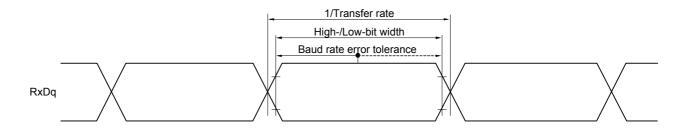
(Remarks are listed on the next page.)

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





- **Remark 1.** Rb[Ω]: Communication line (TxDq) pull-up resistance,
 - Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1, 5, 7)
- Remark 3. fmck: Serial array unit operation clock frequency
 - (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 - m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))
- Remark 4. UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is 1.

(6) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol	C	Conditions	HS (high-speed	I main) mode	Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$ 4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ \text{C}_{\text{b}} = 30 \text{ pF}, \text{R}_{\text{b}} = 1.4 \text{ k}\Omega $	600		ns
			$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, \text{Rb} = 2.7 \text{ k}\Omega$	1000		ns
			$2.4 \text{ V} \leq \text{EV}_{\text{DDO}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \text{ Rb} = 5.5 \text{ k}\Omega$	2300		ns
SCKp high-level width tkH1		$4.0 \text{ V} \le \text{EV}_{\text{DDO}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $\text{C}_{\text{b}} = 30 \text{ pF}, \text{R}_{\text{b}} = 1.4 \text{ k}\Omega$		tксү1/2 - 150		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0$ $2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7$,	tксү1/2 - 340		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3$ $1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 5.5$,	tксү1/2 - 916		ns
SCKp low-level width	tKL1	$2.7 \text{ V} \le V_b \le 4.0 \text{ V},$	4.0 V \leq EV _{DD0} \leq 5.5 V, 2.7 V \leq V _b \leq 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ			ns
2	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0$ $2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7$,	tkcy1/2 - 36		ns	
	$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 5.5 \text{ k}\Omega$		tксү1/2 - 100		ns	

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

 $(\mbox{\bf Remarks}$ are listed two pages after the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

(TA = -40 to +105°C, 1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

(2/3)

Parameter	Symbol	Conditions	HS (high-spee	ed main) mode	Unit
			MIN.	MAX.	
SIp setup time (to SCKp↑) Note	tsıĸ1	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	162		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	354		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DDO}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \text{ Rb} = 5.5 \text{ k}\Omega$	958		ns
SIp hold time (from SCKp↑) Note	tksıı	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	38		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	38		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 5.5 \text{ k}\Omega$	38		ns
Delay time from SCKp↓ to SOp output Note	tkso1	$4.0 \text{ V} \le \text{EV}_{\text{DDO}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 1.4 \text{ k}\Omega$		200	ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$		390	ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DDO}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \text{ Rb} = 5.5 \text{ k}\Omega$		966	ns

Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

(TA = -40 to +105°C, 1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

(3/3)

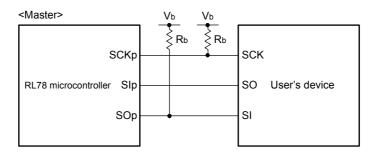
Parameter	Symbol	Conditions	HS (high-spee	ed main) mode	Unit
			MIN.	MAX.	
SIp setup time (to SCKp↓) Note	tsıĸ1	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	88		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	88		ns
		$2.4 \ V \le EV_{DDO} < 3.3 \ V,$ $1.6 \ V \le V_b \le 2.0 \ V,$ $C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega$	220		ns
SIp hold time (from SCKp↓) Note	tksıı	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	38		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	38		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 5.5 \text{ k}\Omega$	38		ns
Delay time from SCKp↑ to SOp output Note	tkso1	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$		50	ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$		50	ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 5.5 \text{ k}\Omega$		50	ns

Note When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

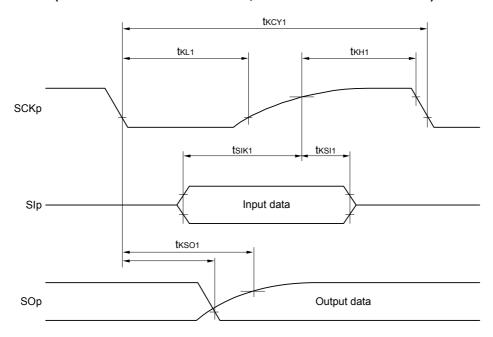
(Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential

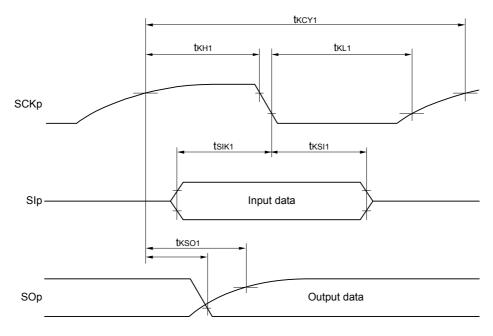


- Remark 1. $Rb[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** p: CSI number (p = 00, 01, 10, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3, 5, 7)
- Remark 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00))
- Remark 4. CSI01 of 48-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



- **Remark 1.** p: CSI number (p = 00, 01, 10, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3, 5, 7)
- Remark 2. CSI01 of 48-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.
- Remark 3. Remark 3. Remark 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 2), mn = 00, 01, 02, 10)

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

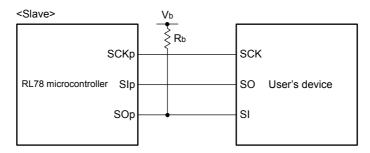
(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

Parameter	Symbol	Cor	HS (high-spee	ed main) mode	Unit	
				MIN.	MAX.	
SCKp cycle time Note 1	tkcy2	4.0 V ≤ EV _{DD0} ≤ 5.5 V,	24 MHz < fmck	28/fмск		ns
		$2.7~V \leq V_b \leq 4.0~V$	20 MHz < fмcк ≤ 24 MHz	24/fмск		ns
			8 MHz < fмcк ≤ 20 MHz	20/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	16/fмск		ns
			fмcκ ≤ 4 MHz	12/fмск		ns
		$2.7~V \leq EV_{DD0} < 4.0~V,$	24 MHz < fmck	40/fмск		ns
		$2.3~V \leq V_b \leq 2.7~V$	20 MHz < fмcк ≤ 24 MHz	32/fмск		ns
			16 MHz < fмcк ≤ 20 MHz	28/fмск		ns
			8 MHz < fмcк ≤ 16 MHz	24/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	16/fмск		ns
			fмcκ ≤ 4 MHz	12/fмск		ns
		2.4 V ≤ EVDD0 < 3.3 V,	24 MHz < fmck	96/fмск		ns ns
		$1.6 \text{ V} \le \text{Vb} \le 2.0 \text{ V}$	20 MHz < fмcк ≤ 24 MHz	72/fмск		
			16 MHz < fмcκ ≤ 20 MHz	64/fмск		
			8 MHz < fмск ≤ 16 MHz	52/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	32/fмск		ns
			fмcκ ≤ 4 MHz	20/fмск		ns
SCKp high-/low-level	tkH2, tkL2	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.	7 V ≤ V _b ≤ 4.0 V	tkcy2/2 - 24		ns
width		2.7 V ≤ EVDD0 < 4.0 V, 2.	3 V ≤ V _b ≤ 2.7 V	tkcy2/2 - 36		ns
		2.4 V ≤ EVDD0 < 3.3 V, 1.	6 V ≤ V _b ≤ 2.0 V	tkcy2/2 - 100		ns
SIp setup time	tsık2	2.7 V ≤ EVDD0 < 4.0 V, 2.	3 V ≤ V _b ≤ 2.7 V	1/fмск + 40		ns
(to SCKp↑) Note 2		2.4 V ≤ EVDD0 < 3.3 V, 1.	6 V ≤ V _b ≤ 2.0 V	1/fмск + 60		ns
SIp hold time (from SCKp↑) Note 3	tksi2			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output Note 4	tKSO2	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}, 2.$ Cb = 30 pF, Rb = 1.4 kΩ	$7 \text{ V} \le V_b \le 4.0 \text{ V},$		2/fмcк + 240	ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.0 $ C _b = 30 pF, R _b = 2.7 k Ω	$3~V \leq V_b \leq 2.7~V,$		2/fмск + 428	ns
		$2.4 \text{ V} \le \text{EVDD0} < 3.3 \text{ V}, 1.$ C _b = 30 pF, R _V = 5.5 kΩ	6 V ≤ V _b ≤ 2.0 V,		2/fмск + 1146	ns

(Notes and Remarks are listed on the next page.)

- Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 5. Select the TTL input buffer for the SIp pin and SCKp pin, and the N-ch open drain output (VDD tolerance (for the 48, 32, 24-pin products)/EVDD tolerance (for the 64, 36-pin products)) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

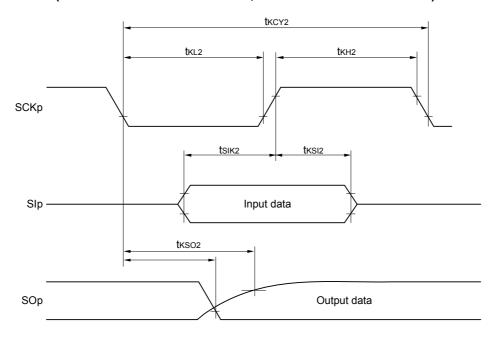
CSI mode connection diagram (during communication at different potential)



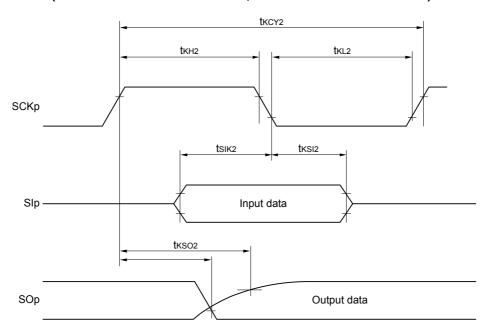
- **Remark 1.** Rb[Ω]: Communication line (SOp) pull-up resistance, Cb[F]: Communication line (SOp) load capacitance,
 - V_b[V]: Communication line voltage
- **Remark 2.** p: CSI number (p = 00, 01, 10, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3, 5, 7)
- Remark 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00, 01, 02, 10))
- Remark 4. CSI01 of 48-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

Also, communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.

CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 01, 10, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3, 5, 7)

Remark 2. CSI01 of 48-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

Also, communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

(1/2)

Parameter	Symbol	Conditions	HS (high-spe	eed main) mode	Unit
			MIN.	MIN. MAX.	
SCLr clock frequency	fscL	$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $		400 Note 1	kHz
		$\begin{split} 2.7 & \ V \le EV_{DD0} < 4.0 \ V, \\ 2.3 & \ V \le V_b \le 2.7 \ V, \\ C_b = 50 & \ pF, \ R_b = 2.7 \ k\Omega \end{split}$		400 Note 1	kHz
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $		100 Note 1	kHz
		$ \begin{aligned} 2.7 & \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 & \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $		100 Note 1	kHz
		$ 2.4 \text{ V} \leq \text{EV}_{\text{DDO}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 5.5 \text{ k}\Omega $		100 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $	1200		ns
		$\begin{split} 2.7 & \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 & \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 & \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	1200		ns
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $	4600		ns
		$\begin{aligned} 2.7 & \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 & \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega \end{aligned}$	4600		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DDO}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 5.5 \text{ k}\Omega$	4650		ns
Hold time when SCLr = "H"	thigh	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	620		ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DDO}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega $	500		ns
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $	2700		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	2400		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5.5 \text{ k}\Omega$	1830		ns

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

(2/2)

Parameter	Symbol	Conditions	HS (high-speed m	ain) mode	Unit
			MIN.	MAX.	
Data setup time (reception)	tsu:dat	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, \text{R}_{\text{b}} = 2.7 \text{ k}\Omega$	1/fmck + 340 Note 2		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	1/fmck + 340 Note 2		ns
		$\begin{aligned} &4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned}$	1/fmck + 760 Note 2		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	1/fmck + 760 Note 2		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ \text{C}_{\text{b}} = 100 \text{ pF}, \text{R}_{\text{b}} = 5.5 \text{ k}\Omega$	1/fmck + 570 Note 2		ns
Data hold time (transmission)	thd:dat	$ 4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ \text{C}_{\text{b}} = 50 \text{ pF}, \text{R}_{\text{b}} = 2.7 \text{ k}\Omega $	0	770	ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	0	770	ns
		$\begin{aligned} 4.0 & \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} &= 100 \text{ pF}, \text{ R}_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned}$	0	1420	ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	0	1420	ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 5.5 \text{ k}\Omega$	0	1215	ns

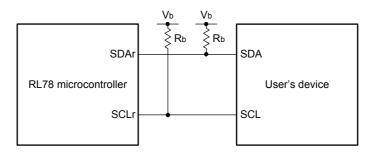
Note 1. The value must also be equal to or less than fmck/4.

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

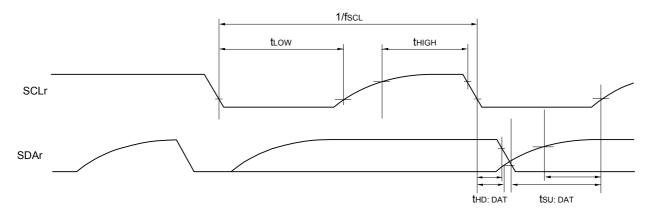
(Remarks are listed on the next page.)

Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- Remark 1. $Rb[\Omega]$: Communication line (SDAr, SCLr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** r: IIC number (r = 00, 01, 10, 11, 20), g: PIM, POM number (g = 0, 1, 3, 5, 7)
- Remark 3. fmck: Serial array unit operation clock frequency

 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),

 n: Channel number (n = 0, 2), mn = 00, 01, 02, 10)

3.5.2 Serial interface IICA

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

Parameter	Symbol	Conditions	HS	(high-sp	eed main) r	node	Unit
			Standard mod		Fast	mode	
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode: fcLk ≥ 3.5 MHz	_	_	0	400	kHz
		Standard mode: fclk ≥ 1 MHz	0	100	_	_	kHz
Setup time of restart condition	tsu: sta		4.7		0.6		μs
Hold time Note 1	thd: STA		4.0		0.6		μs
Hold time when SCLA0 = "L"	tLOW		4.7		1.3		μs
Hold time when SCLA0 = "H"	thigh		4.0		0.6		μs
Data setup time (reception)	tsu: dat		250		100		ns
Data hold time (transmission) Note 2	thd: dat		0	3.45	0	0.9	μs
Setup time of stop condition	tsu: sto		4.0		0.6		μs
Bus-free time	tBUF		4.7		1.3		μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

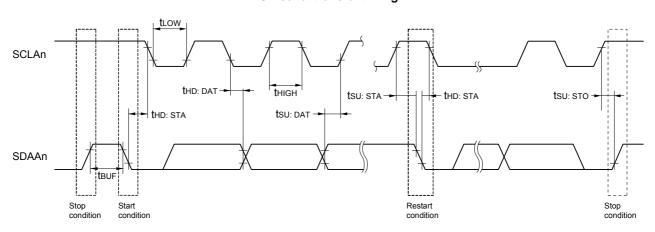
Note 2. The maximum value (MAX.) of thd: DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ Fast mode: $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

IICA serial transfer timing



Remark n = 0, 1

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage Input channel	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = V _{DD} Reference voltage (-) = V _{SS}	Reference voltage (+) = V _{BGR} Reference voltage (-)= AV _{REFM}
ANI0 to ANI7	Refer to 3.6.1 (1).	Refer to 3.6.1 (3).	Refer to 3.6.1 (4).
ANI16 to ANI24	Refer to 3.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 3.6.1 (1) .		_

(1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI2 to ANI7, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution AVREFP = VDD Note 3	2.4 V ≤ AVREFP ≤ 5.5 V		1.2	±3.5	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
		Target pin: ANI2 to ANI14	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	3.1875		39	μs
			$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
		10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μs
		Target pin: Internal reference voltage, and temperature sensor output volt-	$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$	3.5625		39	μs
		age (HS (high-speed main) mode)	$2.4~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	17			μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution AVREFP = VDD Note 3	2.4 V ≤ AVREFP ≤ 5.5 V			±0.25	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution AVREFP = VDD Note 3	2.4 V ≤ AVREFP ≤ 5.5 V			±0.25	%FSR
Integral linearity error Note 1	ILE	10-bit resolution AVREFP = VDD Note 3	2.4 V ≤ AVREFP ≤ 5.5 V			±2.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution AVREFP = VDD Note 3	2.4 V ≤ AVREFP ≤ 5.5 V			±1.5	LSB
Analog input voltage	Vain	ANI2 to ANI7		0		AVREFP	V
		Internal reference voltage output (2.4 V ≤ VDD ≤ 5.5 V, HS (high-speed n	ternal reference voltage output .4 V ≤ VDD ≤ 5.5 V, HS (high-speed main) mode)		V _{BGR} Note 4		V
		Temperature sensor output voltage (2.4 V ≤ VDD ≤ 5.5 V, HS (high-speed n	nain) mode)	V _{TMPS25} Note 4			V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. When AVREFP < VDD, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AVREFP = VDD. Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AVREFP = VDD. Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when AVREFP = VDD.

Note 4. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI24

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, 2.4 V \leq AVREFP \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Cond	itions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution EV _{DD0} ≤ AV _{REFP} = V _{DD} Notes 3, 4	2.4 V ≤ AVREFP ≤ 5.5 V		1.2	±5.0	LSB
Conversion time	tconv	10-bit resolution	$3.6 \text{ V} \leq \text{VdD} \leq 5.5 \text{ V}$	2.125		39	μs
		Target ANI pin: ANI16 to ANI20	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	3.1875		39	μs
			2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution EV _{DD0} ≤ AV _{REFP} = V _{DD} Notes 3, 4	2.4 V ≤ AVREFP ≤ 5.5 V			±0.35	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution EV _{DD0} ≤ AV _{REFP} = V _{DD} Notes 3, 4	2.4 V ≤ AVREFP ≤ 5.5 V			±0.35	%FSR
Integral linearity error Note 1	ILE	10-bit resolution EV _{DD0} ≤ AV _{REFP} = V _{DD} Notes 3, 4	2.4 V ≤ AVREFP ≤ 5.5 V			±3.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution EV _{DD0} ≤ AV _{REFP} = V _{DD} Notes 3, 4	2.4 V ≤ AVREFP ≤ 5.5 V			±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI24		0		AVREFP and EVDD0	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. When $EVDD0 \le AVREFP \le VDD$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AVREFP = VDD. Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AVREFP = VDD. Integral linearity error/ Differential linearity error: Add $\pm 0.5\%$ LSB to the MAX. value when AVREFP = VDD.

Note 4. When $AV_{REFP} < EV_{DD0} \le V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when AVREFP = VDD. Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when AVREFP = VDD. Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when AVREFP = VDD.

(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin: ANI0 to ANI7, ANI16 to ANI24, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V, Reference voltage (+) = VDD, Reference voltage (-) = Vss)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ V _{DD} ≤ 5.5 V	2.125		39	μs
		Target pin: ANI0 to ANI14, ANI16 to ANI20	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	3.1875		39	μs
			2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
		10-bit resolution	3.6 V ≤ V _{DD} ≤ 5.5 V	2.375		39	μs
		Target pin: internal reference voltage, and temperature sensor output voltage	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	3.5625		39	μs
			$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	2.4 V ≤ VDD ≤ 5.5 V			±2.0	LSB
Analog input voltage	Vain	ANI0 to ANI7	1	0		VDD	V
		ANI16 to ANI24	to ANI24			EV _{DD0}	٧
		Internal reference voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) r	rnal reference voltage V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)			3	V
	Temperature sensor output voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)				V _{TMPS25} Note 3		

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2 to ANI7, ANI16 to ANI24

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, 2.4 V \leq EVDD0 \leq VDD, VSS = EVSS0 = 0 V, Reference voltage (+) = VBGR Note 3, Reference voltage (-) = AVREFM = 0 V Note 4, HS (high-speed main) mode)

Parameter	Symbol	Co	MIN.	TYP.	MAX.	Unit	
Resolution	RES				8		bit
Conversion time	tconv	8-bit resolution	2.4 V ≤ VDD ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	Ezs	8-bit resolution	2.4 V ≤ VDD ≤ 5.5 V			±0.60	% FSR
Integral linearity error Note 1	ILE	8-bit resolution	$2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	2.4 V ≤ VDD ≤ 5.5 V			±1.0	LSB
Analog input voltage	Vain			0		V _{BGR} Note 3	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

Note 4. When reference voltage (-) = Vss, the MAX. values are as follows.

Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (-) = AVREFM. Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (-) = AVREFM. Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

3.6.2 Temperature sensor characteristics/internal reference voltage characteristic

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, Ta = +25°C		1.05		V
Internal reference voltage	VBGR	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μs

3.6.3 D/A converter characteristics

(TA = -40 to +105°C, 2.4 V \leq EVsso \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

Parameter	Symbol	Cor	MIN.	TYP.	MAX.	Unit	
Resolution	RES					8	bit
Overall error	AINL	Rload = 4 M Ω	$2.4~\text{V} \leq \text{VDD} \leq 5.5~\text{V}$			±2.5	LSB
		Rload = 8 MΩ	$2.4~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±2.5	LSB
Settling time	tset	Cload = 20 pF	$2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$			3	μs
			2.4 V ≤ V _{DD} < 2.7 V			6	μs

3.6.4 Comparator

(TA = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Con	ditions	MIN.	TYP.	MAX.	Unit		
Input offset voltage	VIOCMP				±5	±40	mV		
Input voltage range	VICMP			0		V _{DD}	V		
Internal reference	ΔVIREF	CmRVM register value : 7	FH to 80H (m = 0, 1)			±2	LSB		
voltage deviation		Other than above				±1	LSB		
Response Time	tcr, tcf	Input amplitude±100mV	nput amplitude±100mV			150	ns		
Operation stabilization	tсмр	CMPn = 0→1	V _{DD} = 3.3 to 5.5 V			1	μs		
time ^{Note 1}			V _{DD} = 2.7 to 3.3 V			3	μs		
Reference voltage stabilization wait time	tvr	CVRE: 0→1 ^{Note 2}				20	μs		
Operation current	Ісмрор	Separately, it is defined as	tely, it is defined as the operation current of peripheral functions.						

- **Note 1.** Time taken until the comparator satisfies the DC/AC characteristics after the comparator operation enable signal is switched (CMPnEN = $0 \rightarrow 1$).
- **Note 2.** Enable comparator output (CnOE bit = 1; n = 0 to 1) after enabling operation of the internal reference voltage generator (by setting the CVREm bit to 1; m = 0 to 1) and waiting for the operation stabilization time to elapse.

3.6.5 PGA

(TA = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Co	nditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOPGA					±10	mV
Input voltage range	VIPGA			0		0.9 × V _{DD} / Gain	V
Output voltage range	VIOHPGA			$0.93 \times V_{DD}$			V
	VIOLPGA					$0.07 \times V_{DD}$	V
Gain error						±1	%
x16		x16				±1.5	%
		x32			±2	%	
Slew rate	SRRPGA	Rising When Vin= 0.1Vpb/gain to 0.9Vpb/gain. 10 to 90% of output voltage amplitude	4.0 V ≤ V _{DD} ≤ 5.5 V (Other than x32)	3.5			V/µs
			4.0 V ≤ V _{DD} ≤ 5.5 V (x32)	3.0			
			2.7 V ≤ V _{DD} ≤ 4.0V	0.5			
	SRFPGA	Falling When Vin= 0.1Vpp/gain	4.0 V ≤ V _{DD} ≤ 5.5 V (Other than x32)	3.5			
		to 0.9Vpp/gain.	4.0 V ≤ V _{DD} ≤ 5.5 V (x32)	3.0			
		voltage amplitude	2.7 V ≤ V _{DD} ≤ 4.0V	0.5			
Reference voltage	t PGA	x4, x8	•			5	μs
stabilization wait time- Note 1		x16, x32				10	μs
Operation current	IPGADD	Separately, it is defined a	as the operation current of per	ipheral function	ons.	•	

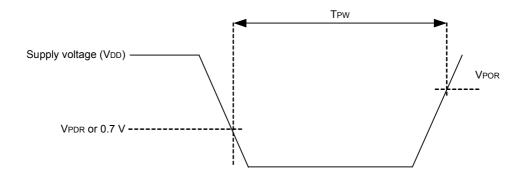
Note 1. Time required until a state is entered where the DC and AC specifications of the PGA are satisfied after the PGA operation has been enabled (PGAEN = 1).

3.6.6 POR circuit characteristics

$(TA = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power on/down reset threshold	VPOR	Voltage threshold on VDD rising	1.45	1.51	1.55	V
	VPDR	Voltage threshold on VDD falling Note 1	1.44	1.50	1.54	V
Minimum pulse width Note 2	Tpw		300			μs

- Note 1. However, when the operating voltage falls while the LVD is off, enter STOP mode, or enable the reset status using the external reset pin before the voltage falls below the operating voltage range shown in 3.4 AC Characteristics.
- Note 2. Minimum time required for a POR reset when VDD exceeds below VPDR. This is also the minimum time required for a POR reset from when VDD exceeds below 0.7 V to when VDD exceeds VPOR while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



3.6.7 LVD circuit characteristics

(1) Reset Mode and Interrupt Mode

(Ta = -40 to +105°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

Pa	rameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Voltage detection	Supply voltage level	VLVD0	Rising edge	3.90	4.06	4.22	V
threshold			Falling edge	3.83	3.98	4.13	V
		VLVD1	Rising edge	3.60	3.75	3.90	V
			Falling edge	3.53	3.67	3.81	V
		VLVD2	Rising edge	3.01	3.13	3.25	V
			Falling edge	2.94	3.06	3.18	V
	VLVD3	Rising edge	2.90	3.02	3.14	V	
			Falling edge	2.85	2.96	3.07	V
		VLVD4	Rising edge	2.81	2.92	3.03	V
			Falling edge	2.75	2.86	2.97	V
		VLVD5	Rising edge	2.70	2.81	2.92	V
			Falling edge	2.64	2.75	2.86	V
		VLVD6	Rising edge	2.61	2.71	2.81	V
			Falling edge	2.55	2.65	2.75	V
		VLVD7	Rising edge	2.51	2.61	2.71	V
			Falling edge	2.45	2.55	2.65	V
Minimum pulse wid	ith	tLW		300			μs
Detection delay tim	ne					300	μs

(2) Interrupt & Reset Mode

(Ta = -40 to +105°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Cond	itions	MIN.	TYP.	MAX.	Unit
Voltage detection	VLVDD0	VPOC2, VPOC1, VPOC0 = 0, 1, 1, fal	/Poc2, VPoc1, VPoc0 = 0, 1, 1, falling reset voltage				V
threshold	VLVDD1	LVIS1, LVIS0 = 1, 0	LVIS1, LVIS0 = 1, 0 Rising release reset voltage				
			Falling interrupt voltage	2.75	2.86	2.97	V
	VLVDD2	LVIS1, LVIS0 = 0, 1	S1, LVIS0 = 0, 1 Rising release reset voltage		3.02	3.14	V
			Falling interrupt voltage	2.85	2.96	3.07	V
	VLVDD3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.90	4.06	4.22	V
			Falling interrupt voltage	3.83	3.98	4.13	V

3.6.8 Power supply voltage rising slope characteristics

$(TA = -40 \text{ to } +105^{\circ}\text{C}, Vss = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 3.4 AC Characteristics.

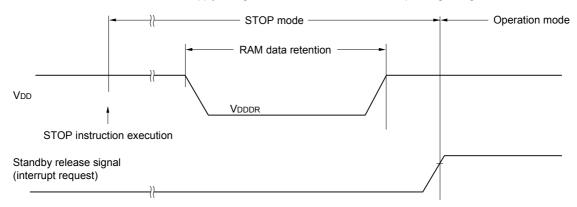
3.7 RAM Data Retention Characteristics

$(TA = -40 \text{ to } +105^{\circ}C, Vss = 0V)$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.44 Notes 1, 2		5.5	V

Note 1. The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.

Note 2. Enter STOP mode before the supply voltage falls below the recommended operating voltage.



3.8 Flash Memory Programming Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fclk	$2.4~V \leq V_{DD} \leq 5.5~V$	1		32	MHz

(Ta = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years	TA = 85°C	1,000			Times
Number of data flash rewrites		Retained for 1 year	Ta = 25°C		1,000,000		
Notes 1, 2, 3		Retained for 5 years	Ta = 85°C	100,000			
		Retained for 20 years	Ta = 85°C	10,000			

- Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
- Note 2. When using flash memory programmer and Renesas Electronics self-programming library
- **Note 3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

3.9 Dedicated Flash Memory Programmer Communication (UART)

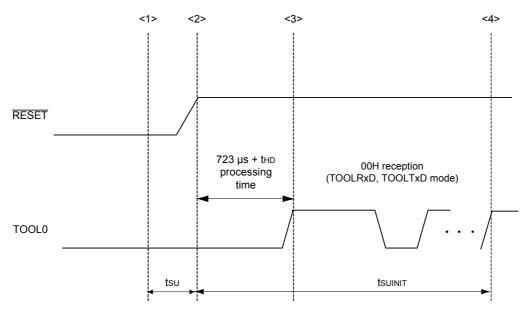
(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

3.10 Timing of Entry to Flash Memory Programming Modes

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory)	thD	POR and LVD reset must end before the external reset ends.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the external reset ends).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit. The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.

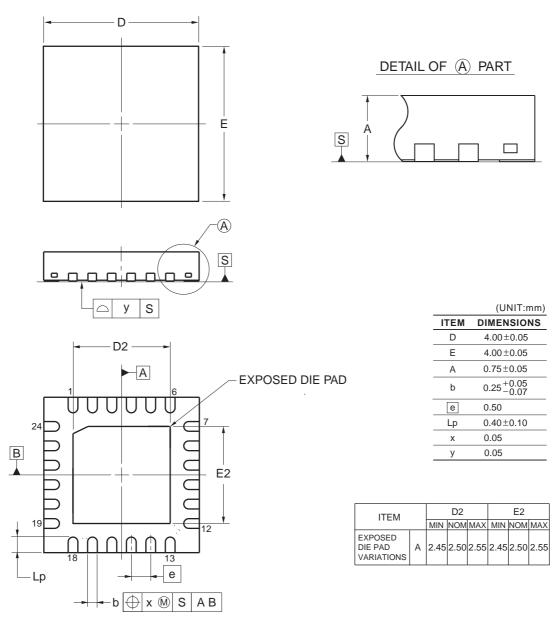
tsu: How long from when the TOOL0 pin is placed at the low level until a pin reset ends
thd: How long to keep the TOOL0 pin at the low level from when the external resets end
(excluding the processing time of the firmware to control the flash memory)

4. PACKAGE DRAWINGS

4.1 24-pin products

R5F11B7CANA, R5F11B7EANA, R5F11B7CGNA, R5F11B7EGNA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-HWQFN24-4x4-0.50	PWQN0024KE-A	P24K8-50-CAB-1	0.04

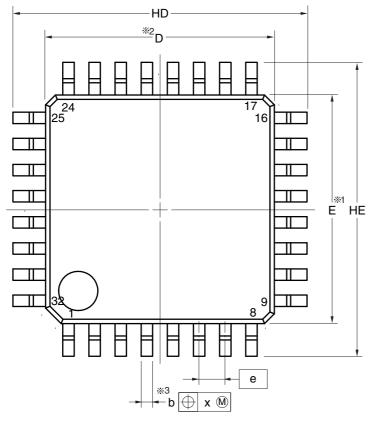


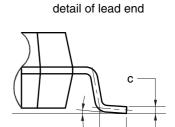
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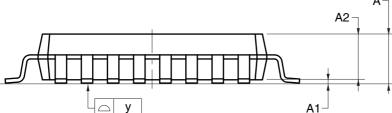
4.2 32-pin products

R5F11BBCAFP, R5F11BBEAFP, R5F11BBCGFP, R5F11BBEGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP32-7x7-0.80	PLQP0032GB-A	P32GA-80-GBT-1	0.2







(UNIT:mm)

	(UNIT:mm)
ITEM	DIMENSIONS
D	7.00±0.10
Е	7.00±0.10
HD	9.00±0.20
HE	9.00±0.20
Α	1.70 MAX.
A1	0.10±0.10
A2	1.40
b	$0.37 {\pm} 0.05$
С	0.145±0.055
L	0.50±0.20
θ	0° to 8°
е	0.80
х	0.20
у	0.10

NOTE

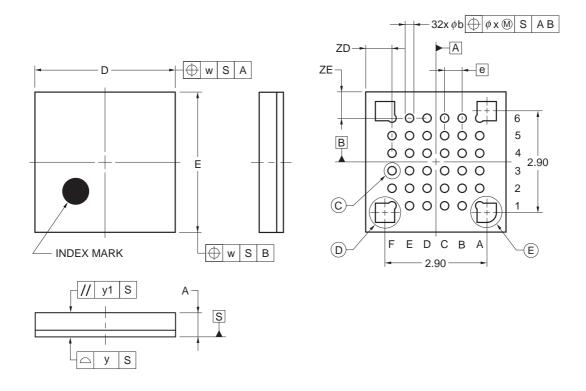
- 1.Dimensions "%1" and "%2" do not include mold flash.
- 2.Dimension " $\mbox{\%}3$ " does not include trim offset.

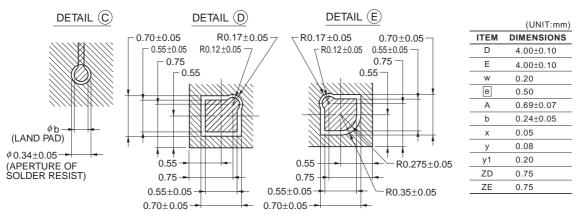
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4.3 36-pin products

R5F11BCCALA, R5F11BCEALA, R5F11BCCGLA, R5F11BCEGLA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA36-4x4-0.50	PWLG0036KA-A	P36FC-50-AA4-2	0.023

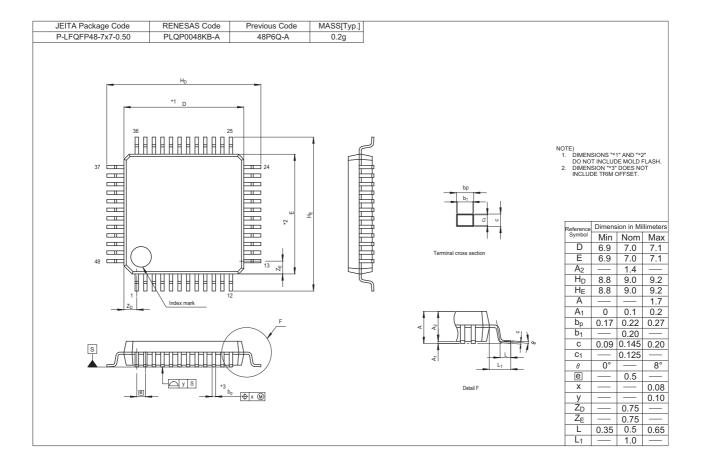




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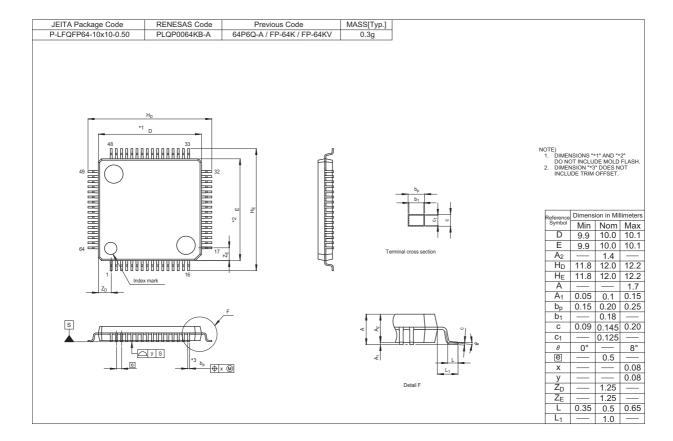
4.4 48-pin products

R5F11BGCAFB, R5F11BGEAFB, R5F11BGCGFB, R5F11BGEGFB



4.5 64-pin products

R5F11BLCAFB, R5F11BLEAFB, R5F11BLCGFB, R5F11BLEGFB



RF\	/ISI	ON	HIST	TORY
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RL78/G1F Datasheet

Rev.	Date	Description		
Nev.	Date	Page	Summary	
0.10		_	First Edition issued	
0.50	Jan 14, 2015	3	Modification of description in Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G1F	
		10	Addition of description in 1.4 Pin Identification	
		11	Modification of description in 1.5 Block Diagram	
		12, 13	Modification of description in 1.6 Outline of Functions	
		14	Addition of target products to the beginning	
		17	Modification of 2.2.2 On-chip oscillator characteristics	
		18	Addition of note 4 in 2.3.1 Pin characteristics	
		23, 25, 27	Modification of 2.3.2 Supply current characteristics	
		73	Modification of 2.6.4 Comparator	
		73	Modification of 2.6.5 PGA	
		77	Renamed to 2.7 RAM Data Retention Characteristics	
		79	Addition of target products to the beginning	
		83	Modification of 3.2.2 On-chip oscillator characteristics	
		87	Modification of "Output voltage, low"	
		89, 91, 93	Modification of 3.3.2 Supply current characteristics	
		130	Modification of 3.6.4 Comparator	
		130	Modification of 3.6.5 PGA	
		133	Renamed to 3.7 RAM Data Retention Characteristics	
1.00	Jan 14, 2015	All	Modification of the unit symbol (PWMOP into PWMOPA)	
		1	Modification of descriptions in 1.1 Features	
		10	Modification of 1.4 Pin Identification	
		13	Modification of 1.6 Outline of Functions	
		73	Modification of 2.6.5 PGA	
		130	Modification of 3.6.5 PGA	
1.10	Aug 12, 2016	5	Addition of product name (RL78/G1F) and description (Top View) in 1.3.1 24-pin products	
		6	Addition of product name (RL78/G1F) and description (Top View) in 1.3.2 32-pin products	
		8	Addition of product name (RL78/G1F) and description (Top View) in 1.3.4 48-pin products	
		9	Addition of product name (RL78/G1F) and description (Top View) in 1.3.5 64-pin products	

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NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE: Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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 R5F11BBCAFP#50
 R5F11BLEAFB#30
 R5F11BGCAFB#30

 R5F11BBEAFP#30
 R5F11BGEAFB#30
 R5F11BGCAFB#50
 R5F11B7CANA#W0
 R5F11B7CANA#W0
 R5F11B7CANA#W0

 R5F11BLEGFB#30
 R5F11BLEGFB#50
 R5F11BGCGFB#50
 R5F11BGEGFB#30
 R5F11BGEGFB#50

 R5F11BLCAFB#50
 R5F11BLCGFB#30
 R5F11BLCGFB#50
 R5F11BCCGLA#U0
 R5F11BCCGLA#W0

 R5F11BCEALA#W0
 R5F11BCEGLA#U0
 R5F11BCGGFB#30
 R5F11BBCGFP#30
 R5F11BBCGFP#30

 R5F11B7CANA#20
 R5F11B7CANA#40
 R5F11BBCGFP#10
 R5F11BBEAFP#10
 R5F11BLEAFB#10

 R5F11B7EANA#20
 R5F11B7CANA#40
 R5F11BBCGFP#10
 R5F11BBEAFP#10
 R5F11BLEAFB#10